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Final Technical Peport 30 Oct 95 MDA972-93-G-0001

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# APPLICATION SPECIFIC ELECTRONIC MODULE (ASEM) MERCHANT FOUNDRY

# FINAL TECHNICAL REPORT

02AT-001

CLEARED FOR OPEN PUBLICATION

October 30, 1995

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DIRECTORATE FOR FREEDOM OF INTURMATION AND SECURITY REVIEW (DASD-PA) DEPARTMENT OF DEFENSE

Sponsored By

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The commercial part of Motorola's ASEM Foundry is the responsibility of GSTG's Diversified Technologies Division (DTD) and is a joint venture with Motorola's Semiconductor Products Sector (SPS). SPS is responsible for the marketing support of the Foundry and support of devices for use in the Foundry. It should be noted that the Foundry is not bound to use Motorola devices exclusively, but rather use Motorola devices to the maximum extent possible consistent with function and cost considerations. DTD provides the lead for the Foundry and is responsible for performance of the MCM development including design, part selection, layout and test. A copy of the business plan as presented at the formation of the joint venture is included as Appendix A.

Manufacturing of the MCMs for both commercial and Government products is the responsibility of the Microelectronics Factory (MEF) within GSTG. The MEF is responsible for the development and maintenance of all required manufacturing processes and equipment for the successful build of MCMs. In addition the MEF is also responsible for the development and maintenance of the design rules as they pertain to the manufacturing process and for the development and maintenance of qualified personnel.

The Government portion of the Foundry is the responsibility of GSTG's Government Electronics Division (GED). GED is responsible for the design, part selection, layout and test of ASEMs. Each ASEM opportunity is addressed as a separate project beginning with the identification of an opportunity and continuing through the delivery of finished modules. This portion of the Foundry is fully compliant with all Government requirements and as a result, is responsible for seeing that the MEF is also compliant to the Government's requirements. Additionally, the Government Foundry is responsible for maintenance of the design kits, the layout systems and the test systems necessary for the support of the ASEM Foundry at GSTG.

Staff functions of GSTG also support the Foundry in the areas of quality assurance, material acquisition and tracking, management systems and

corporate technology transfer.

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## 3.0 <u>Technical Results</u>

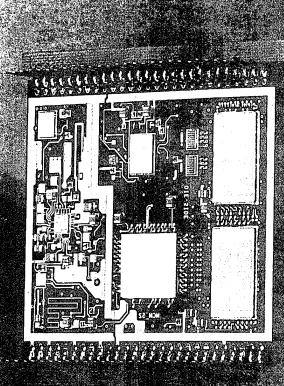
The Government portion of the Foundry was the first in operation and during the period of this contract, aggressively pursued over 30 MCM opportunities for Government applications. Notably, the Foundry was key to the development of the PRC 112-GPS where an MCM solution allowed insertion of a GPS receiver into the PRC-112. In addition, the Foundry supported the development of the MCM GPS Receiver with Mayo Clinic that resulted in the smallest GPS receiver, a credit that stood until mid-95. A photo of the GPS MCM Receiver is shown in Figure 2. The following highlights the technical results of the contract.

## 3.1 Epoxy Encapsulation

During this contract, Motorola, as part of the cost sharing thrust in support of the ASEM Foundry, completed the insertion of the Liquid Epoxy Encapsulation (glob top) of die technology and supporting processes for MCM manufacturing. Due to recent innovations in formulation chemistry, Liquid Epoxy Encapsulation has been gaining in use for mechanical and environmental protection of Integrated Circuits, Hybrids & Multichip Modules. Liquid encapsulants offer advantages in non-recurring costs such as tooling and capital equipment. Presently these encapsulation materials are being used primarily for digital and low frequency applications. Motorola, anticipating the need for this technology in RF and mixed signal applications in order to maintain cost efficiency, has completed testing to extend the use of this liquid encapsulant to frequencies up to 1.5 Ghz.

Very little information was available about the effect of encapsulating tuned RF circuits with an epoxy coating. There was much conjecture among the RF design community about the detuning that could occur due to the change in dielectric constant from near 1 in free air, where the device is initially tested, to a dielectric constant of 4 or more after epoxy encapsulation. Accurate modeling of the encapsulation effects was difficult because the results depend on the assumptions.

In an attempt to quantify changes in RF circuit performance due to encapsulation, Motorola tested several RF hybrid device types ranging in center frequency from 900 MHz to 1.5 GHz. RF performance of a typical device was measured before and after encapsulation. Additionally, tests were run to check for the effects of moisture penetration into the epoxy\_encapsulant due to 85°C/85%RH exposure. Power out, Gain, Return Loss and Efficiency were the device parameters of interest. A summary of the testing is presented in Appendix B.



Results of the testing indicate that the encapsulant has minimal effect on most RF parameters. Gain, Power Out and Efficiency were typically less than 10% change from pre to post encapsulation. Return loss was effected more dramatically with the magnitude being less predictable. Moisture had no perceptible effect on the device performance.

In summary, the changes observed in the RF circuitry due to liquid epoxy encapsulation are within the operational capability of most designs. SPS is presently running qualification testing for future offerings using liquid encapsulation. GSTG is encapsulating RF circuitry in the PRC 112-GPS and the GPS Receiver at 1.5 Ghz with no effects on the performance of the RF circuitry. In addition, Motorola has evaluated the encapsulation up to 2.5 Ghz and has seen no noticeable effects.

## 3.2 Quiet Chip MCM

A processor MCM consisting of 12 die was developed in a concurrent engineering effort with Bolt,Branek and Newman (BBN) for application to a noise cancelling processor. The manufacturing( including substrate fab and test), and module test was completed in three weeks with first pass success. A photo of this MCM is shown in Figure 3. The details of this MCM are presented later in this report.

Figure 3 Double Sided Laminate Multichip Module for BBN

# 3.3 Thermal Weapon Sight MCM

The addition of a RS -170 interface to an existing Hughes Thermal Weapon Sight was made possible through the use of an MCM made up of 16 die integrally packaged with a power supply module and three large connectors. A photo of this MCM is presented in Figure 4. The substrate manufacturing, (including substrate fab and test), and module test was completed in three weeks with first past success. Details of this MCM are presented later in this report.

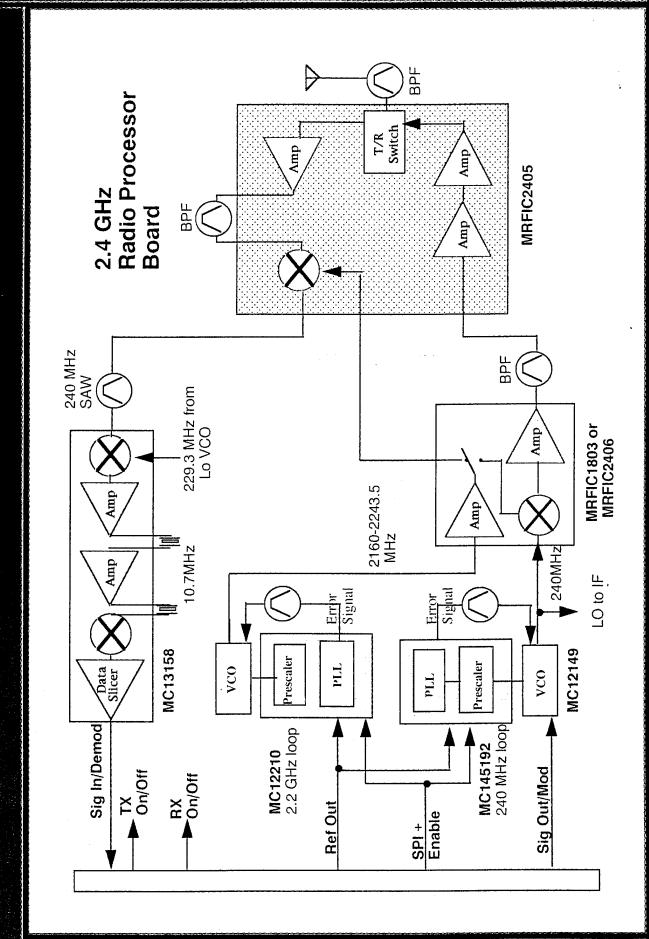
#### 3.4 A PCS RF MCM

A developmental model of an rf module was developed that occupies one-half of an PCM/CIA module for application to wireless LAN applications. A photo of the unit is presented in Figure 5. A block diagram of the MCM is presented in Figure 6. The objective of this development was to achieve the size at a material cost of less than \$25 and meet all performance requirements for a LAN application. We achieved the size and performance and came within \$6 of the cost objective. A consistent feature to this MCM and others the Foundry has developed is the successful mixture of surface mount and wire bond component attach technologies within a single module. This was necessary to accommodate the various component structures and the use of bare die and packaged die on the same substrate.

Figure 5 A Laminate Multichip Module for a 2.4 Ghz PCS Transceiver for a PCMCIA Application.

NCH

Figure 6 Block Diagram of the  $2.4~\mathrm{Ghz}~\mathrm{PCS}~\mathrm{RF}~\mathrm{MCM}$ 



## 3.5 Design Kits

To enable customers to design a layout that would be compatible with the manufacturing processes and design rules in the MEF, Motorola developed a design kit as a master point of reference for MCM design personnel. We found it to be of more interest to the Government MCM projects than it was for the commercial products as the customers' engineers were more involved with the MCM design in the Government projects. A copy of the design kit is included as Appendix C.

## 3.6 Reliability Programs

Reliability evaluation of key packaging approaches was part of this program and involved several Motorola factories and technologies:

- Motorola SPS Memories and Microprocessors Technology Group(MMTG), Advanced Packaging and Prototype Lab (APDPL)
  - -MCM-L
- Motorola Government Electronics Division (GED), Microelectronics Facility (MEF)
  - -MCM-L
  - -MCM-C

## 3.6.1 Reliability Requirements:

The requirements encountered during discussions with customers included the need for hermetic sealing of devices and testing of non-hermetic devices.

#### Hermetic Devices:

Hermetic sealing of MCM devices is performed almost exclusively for Military users. These users almost unanimously require MIL-H-38534 screening and Qualification (qual)/Quality Conformance Inspection (QCI).

### Non-hermetic Devices:

Use of non-hermetic devices has become extremely common in the Commercial/Industrial marketplace due to the relatively low cost and high reliability. Historically the Quality/Reliability requirements of these devices have been driven by the automotive industry. The automotive parts methodology is generally referred to as "Best Commercial Practice". Best commercial practice will vary slightly from company to company and is flexible to keep down costs.

The tests performed for the automotive industry by Motorola's Automotive and Industrial Electronics Group (AIEG) are as follows:

- Temperature Cycle (air to air), -40°C to 125°C, 1000 cycles
- Thermal Shock (liquid to liquid), -40°C to 125°C, 500 cycles
- Humidity, Temperature, Bias, 85°C, 85% RH, Static Bias
- Life Test, 85°C, maximum derated power, 1000 hrs.
- Mechanical Shock, half sine shock of 1000g's, 6 axis
- Solderability, Proven at the vendors option

As the Military and Space user community begin to use commercial/industrial grade devices it is anticipated that they will follow the Automotive lead as addition of the MIL-H-38534 requirements would negate most of the cost savings of using the commercial/industrial devices.

## 3.6.2 Motorola MMTG, APDPL:

APDPL is a Motorola center for excellence in advanced packaging. In this capacity they have a KME automated Chip on Board (COB) assembly line. This assembly line was determined to be compatible with the ASEM Foundry's goals and is available as a manufacturing asset for high volume (> 500K modules per year).

The primary aspects of the KME MCM assembly line that are pertinent to reliability are as follows:

- The KME line uses automated epoxy die bond with Ablestik 84-1 LMI SR4 silver filled conductive epoxy.
- Wirebonding is accomplished using automated Gold Ball Bonding with 1.3 mil gold wire.
- Encapsulation is accomplished using a low viscosity liquid epoxy encapsulant dispensed automatically over the individual die surfaces. An epoxy dam is used to limit the flow of the liquid epoxy.

Due to the non-hermetic nature of these devices the primary reliability concerns for the packaging technology were thermal mismatch and moisture related mechanisms. The reliability testing performed to date has been to accelerate these associated mechanisms. Eight devices containing nine .300" by .750" die, with a total of 2016 wires daisy chained together were subjected to initial test. These devices were tested as follows:

- Thermal cycled from -55°C to 125°C for 2000 cycles with no failures.
- Autoclave at 2 atmosphere, 121°C, with 100% RH for 144 hours with 0 failures.

These test results are impressive for the resistance of the overmolding compound to thermally induced failure mechanisms and resistance of the technology to corrosion.

To date, the KME line has been used primarily for prototyping and test vehicles. Very little in the way of process documentation and Statistical Process Control (SPC) is in place. It is important that at least minimal documentation of the process and regular SPC are in place for production of deliverable devices.

## 3.6.4 Motorola GSTG, MEF: (MCM-C)

The MEF fabricates MCM-C using hermetically sealed Multilayer Ceramic (MLC) Packages with the substrate formed as part of the package. The production of MCM-C at the MEF is a mature line with good reliability history. This history includes several devices which have undergone complete MIL-H-38534 qualification testing. The MEF is also qualified for MIL-STD-1772 for MCM-C. Certification is on hold pending revisions of MIL-STD-1772.

# 3.6.5 <u>Motorola GSTG,MEF: (MCM-L)</u>

The MCMTC has the capacity for MCM-L for prototyping and small to medium quantity production. The primary aspects of the MCM-L assembly line that are pertinent to reliability are as follows:

- The MEF line uses automated epoxy die bond with Ablestik 84-1 LMI NB-1 silver filled conductive epoxy.
- Wirebonding is accomplished using automated Gold Ball Bonding, automated Gold Wedge Bonding or Automated Aluminum Wedge Bonding with 1.0 mil wire.
- Encapsulation of devices is accomplished using a low viscosity liquid epoxy encapsulant dispensed over the individual die surfaces. An epoxy dam is used to limit the flow of the liquid epoxy.

Because of the non-hermetic nature of these devices the primary reliability concerns for the packaging technology are thermal mismatch and moisture related mechanisms. As stated above reliability testing has confirmed the integrity of the epoxy encapsulant. (See Appendix D) The MEF MCM-L assembly line provides for the fabrication of Commercial/Industrial/Military ground support grade products. The line is "Best Commercial Practice" until the Military defines their own requirements. Due to the military background of the MEF, process documentation and Statistical Process Control (SPC) are presently in place.

#### 3.7 ISO 9000 Certification:

Motorola GSTG entered into the process of certifying for ISO 9000. The certification is for "Quality Systems: Motel for Quality Assurance in Design/Development, Production, Installation and Servicing" in accordance with ISO 9001. In order for the ASEM Foundry to advertise ISO 9000 compliance, it will be necessary to control our suppliers (including Motorola SPS) to Motorola GSTG SOI's. As a result we have put the ISO-9000 activities on hold pending resolution of requirements as it relates to the business of the Foundry.

It should be noted that Motorola SPS believes that it's quality system is completely compliant to ISO-9000 but does not want to undertake the expense for it's U.S. facilities.

## 3.8 Mock-Up Models

A key fundamental we adopted in the Foundry to address the complexity and cycle time issues was the extensive use of mock-up models that are form and fit models of the proposed final module. This approach sets the tone for the subsequent development and clearly identifies, early on, the acceptability of the proposed design. By reaching closure on the package and configuration of the package, the number of die required in the design and other factors external to the module that affects its design, an efficient design cycle can proceed. This was clearly demonstrated for the BBN Quiet Chip MCM.

## 4.0 <u>Technical Problems</u>

#### 4.1 Known Good Die

The number one problem that is plaguing the MCM business is the supply of tested die or better known as the "Known Good Die" problem. Our experience todate is first time yields of 50 to 60 % set by performance of the die. Manufacturing, in contrast, has yielded 96-98% first time success results. Motorola is actively pursuing the die yield issues for direct chip attach packaging with many fronts ranging from wafer functional testing to chip scale integration. Other companies are also pursuing this problem. the next one to two years should see major strides in solving the "Known Good Die" problem. For further reading please refer to the Selected Suppliers List included as Appendix E.

During the last year we have been investigating the use of "element evaluation" where sample die are taken from the wafer of die in question, packaged and tested to verify that on a sample basis, the die are good. This approach has yielded excellent results on the Hughes Thermal Weapon Sight MCM program.

## 4.2 Cycle Time

During the course of this contract we have encountered significant problems with achieving short cycle times when one, the electrical design is included in the cycle time measurement and two, the customer participates in the layout of the MCM. We have seen either of these activities exceed three months and in some cases, approach 12 months. In contrast, the cycle time for the substrate procurement, assembly and test is typically less than four weeks. The concurrent engineering that is necessary to develop complicated modules is significant and is independent of the type of packaging. Therefore, the use MCM packaging should not introduce any appreciable cycle time. However, since the MCM packaging is considered "new" it is being incorrectly blamed for excessive cycle times.

## 4.3 MCM Layout Software

Early on in the ASEM Merchant Foundry Program, a team of two individuals (Lucius Lockwood and Mike Greene) performed bench marks of MCM design tools; Cadence Allegro MCM, Harris Finesse MCM, Intergraph MCM and Mentor MCM Station were the tools bench marked. During the bench marking, a rating table was utilized for scoring each tool's performance in various areas. The purpose of this effort was to select the best available tool(s) for Foundry MCM design applications. The bench marking efforts resulted in the Team's recommendation for purchase and implementation of Mentor MCM Station as the "golden" tool for MCM design. The following is a post bench mark experiential analysis of Mentor MCM Station's performance on a real world MCM design application.

## 4.3.1 General Comments

For purposes of consistency, the same rating table (less non-applicable categories) was used to rate Mentor's performance (Refer to Table I in Appendix F). Cadence Allegro is GSTG's standard tool for general PWB and MCM design; Cadence's scores are shown as reference to Mentor's scores. Cadence's scores are unchanged from original bench mark rating and are representative of the bench mark effort (Version 8.x) and experience with the current of the day release 6.x.

## • Support Infrastructure

Local applications engineers were an excellent source of assistance. They were very proficient with the tools and available most of the time for support both by telephone and site visits. The hot-line returned calls sometimes same day, usually within twenty-four hours.

# Physical and Logical Symbols

Both the physical and logical symbol editing environments were very flexible. We had no difficulty in creating or modifying symbols to support the design.

## • Automatic Routing

The standard Mentor router performed very poorly. Yields were very low -- in the 70 and 80 % ranges -- and this took nearly a week . Furthermore, the router ignored pre-routes either ripping them up (despite being locked) or adding routes that already existed. One especially annoying habit of the router was that it randomly ripped-up wire bond traces -- these too were locked. Mentor eventually assisted by performing the routing at their offices on their shape-based router. Even then we were forced to hand route over a hundred traces to complete the design.

## Interactive Routing/Editing

In general I was not impressed with the ease of use of the interactive routing tools. Adding routes was very difficult and the system was very sensitive to picks and guide locations. Layers that were invisible were selectable -- this was incredibly annoying -- it was very difficult in dense areas to select the desired track for editing. During interactive editing it is not practical to constantly toggle selectability -- a not visible/not selectable feature would help. Also, the system is very sensitive to guide origins, limiting the ability to easily add a connection without first adding a new guide and deleting the old one. Z-axis guides at vias, while advertised as a feature, turned out to be very annoying and hard to get rid of, even though the physical connection to the via was achieved -- again, overly sensitive to process.

# Shape Editing

This was an excellent area of capability! All environments had the ability to create polygonal features. This was especially helpful in creating physical symbols, board geometrys, and circuit plane layers. MCMs and PWBs are often irregular in shape and the ability to support this requirement is very necessary.

# Factory/Manufacturing Interfaces

Very easy to use and reliable interfaces for setup of artwork and NC drill output. The symbol and geometry building environments of Librarian allow input of mounting holes, and special vias, etc., that directly flows through to the output. One disappointment was the generation of the NC milling data. The board had an irregular outline with small groves extending inward at four locations. We were unsuccessful (even with AE support) to get the program to properly handle the grooves.

## Design Manager

One of the best features of MCM Station! It was a little difficult to understand all the environmental relationships at first, but afterward, it became evident that this concept is an excellent way of controlling design libraries and entire designs and projects. Designs are easily kept in synchronization and under configuration control with this tool. The logical to physical interface (both directions) was excellent.

## • Layout Clean-up

There is basically no (external to the router) provision for manufacturing clean-up of the routed traces. No conductor balancing, line smoothing or jog elimination features exist --we were required to spend considerable time in modifying the conductor patterns interactively to enhance manufacturability or eliminate potential solutions traps in the pattern.

## 4.3.2 Summary

Overall Mentor is a very strong tool set. Mentor still rates higher than Cadence in the Rating Table. The rating and number of available features and quality of features that support MCM design still exceeds what Cadence provides. Some ratings were increased and some were decreased with respect to the actual performance versus the bench mark. Despite the problems encountered on this design we still support MCM Station as the tool of development for MCM design applications. This design was the first MCM design performed by the Foundry on the system and some allowance should be made for learning curve. We encountered many bugs in the 8.2\_5 software but there were also many features that performed very well. Performance in the areas of design management, physical to logical control/interface, schematic capture through Design Architect, factory/manufacturing interfaces, and many other areas were strong or superior as compared to other benchmarked tools. Still, router performance, interactive editing of traces, and the lack of what we consider a real MCM environment are three vital areas for improvement.

### 5.0 Important Findings and Conclusions

## 5.1 Significant Hardware Development

One of the goals of the ASEM Foundry was to provide government agencies and outside contractors access to Motorola's existing MCM production lines for the purpose of assembling and testing low cost MCMs. In addition to manufacturing, the ASEM Foundry was also established to provide engineering support for the selection of Known Good Die, substrate and package design, and concurrent test engineering to assure producible MCMs. Over the course of the ASEM program, two programs in particular achieved these goals and produced significant MCM developments; The BBN QuietChip MCM, and the Hughes Signal Processor Assembly (SPA).

These programs utilized a low-cost, laminate substrate with the die directly attached to the substrate with conductive epoxy. Thermosonic gold-ball bonding, which is a combination of thermo-compression and ultrasonic bonding, was used for the wirebonds. The die and wirebonds were protected with a low cost, epoxy encapsulation. Both programs achieved a high degree of first time success with the prototype testing taking less than one week. The following paragraphs summarize the significant hardware developments of each MCM.

## 5.1.1 Hughes Signal Processor Assembly (SPA)

#### 5.1.1.1 Product Overview

The Signal Processor Assembly is a major subsystem of the Hughes Thermal Weapon Sight (TWS). The TWS is an advanced infrared weapon sight which is capable of imaging through total darkness, smoke, blowing dust and adverse weather. It can be mounted on a wide variety of weapons, including rifles, machine guns, and shoulder-launched missiles.

The SPA subsystem provides real time video processing including digital frame integration, gain control, reticule generation and scan conversion for RS-170 output. The Hughes Aircraft Company recently upgraded the functionality of its SPA by adding the RS-170 output and enhancing the video processors. In order to maintain the previous TWS size, Chip-on Board or MCM-L technology was utilized to increase the functionality without increasing the existing PWB size. To redesign the substrate, the ASEM Foundry worked with Hughes engineering to replace an existing hybrid and add nine die for video processing.

# 5.1.1.2 ASEM Foundry Tasks

For this program, Motorola's ASEM Foundry performed the following tasks:

- Schematic capture
- Create die library with bonding pad information
- Design substrate
- Conduct Manufacturing Readiness Review
- Procure tested substrates
- Design manufacturing tools
- Assemble 4 prototypes

## 5.1.2 MCM Design

The SPA MCM design consisted of 15 die with 780 wirebonds and 142 surface mount resistors and capacitors. The die included 3 ASICs, 2 microcontrollers, 5 SRAMs, 1 EEPROM, 1 ADC, 1 Video DAC and an Analog Switch. The schematic was captured with Mentor's Design Architect and the substrate was designed using Mentor's MCMStation. Figure 7 shows the conductive layers separated by polyimide in a laminated, 10 layer substrate.

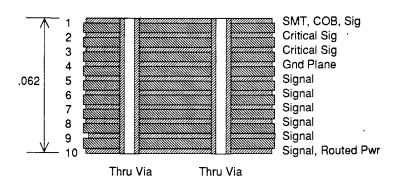


Figure 7, SPA Layer Structure

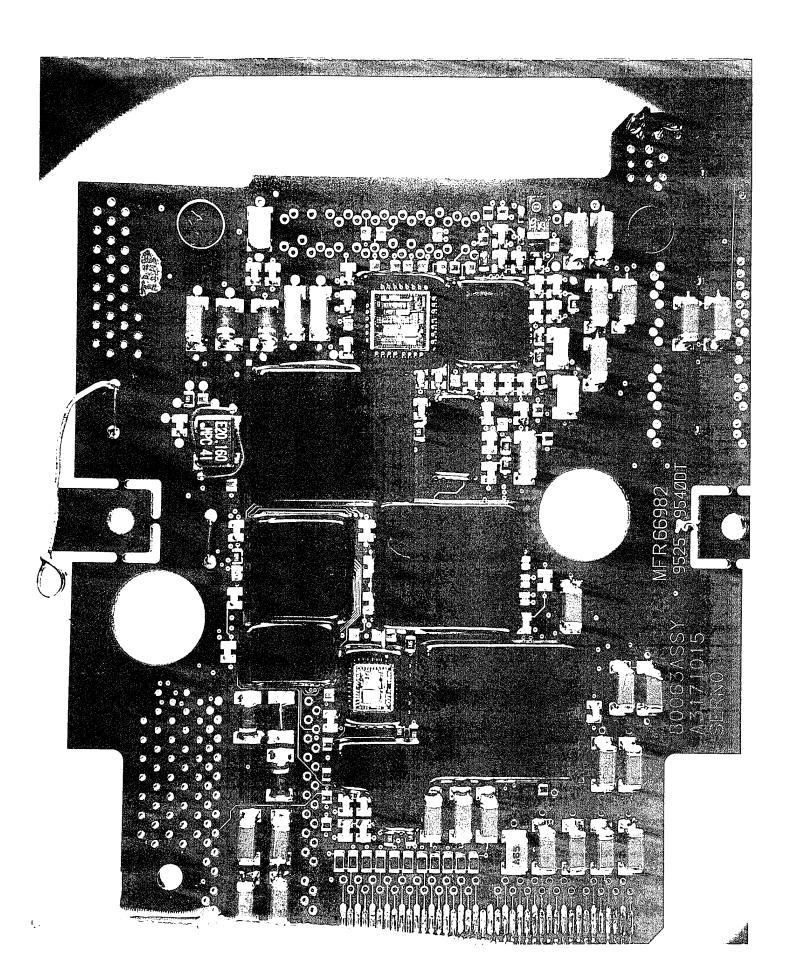
The critical signals were routed on layers 2 and 3 to eliminate crosstalk between digital and critical analog signals. Analog signals associated with the video DAC, the Analog Signal Processor and the A-D Converter were placed on these layers. The 16 mHz clock signal and the write strobes from the Timing Generator were also routed on these layers but did cross the critical analog signals. Hughes engineering tested the prototypes and reported no discernible noise on the video image due to crosstalk.

All of the devices were packaged on a 4 in. by 4 in., .062 "thick, polyimide substrate with the size conforming to the power supply assembly which is bonded to the back or connector side of the substrate. The minimum conductor line width and conductor space was 4 mils. The substrate was designed and fabricated to meet industrial standard IPC-276, type 2, class 3. Testing of the substrates was specified in the fabrication drawing and called out continuity testing to the netlist. Each net was verified and then tested for shorts to ground and to power.

The SPAs were shipped to Hughes for testing, prior to encapsulation, in containers designed by GSTG to protect the die and wirebonds. Figure 3 shows the SPA prior to encapsulation. After testing, the die and wirebonds were encapsulated with a epoxy compound at GSTG. Figure 8 shows the SPA assembly prior to installation in the Thermal Weapon Sight. Note the clear silicon gel used to protect U6 and U10, the microcontrollers. This permitted Hughes engineering to erase the EPROM resident on the micro-controllers and

reprogram the I.C.s using a via field for the electrical interface. The testing done at GSTG showed that this material could withstand high temperatures and would permit UV erasing.

Figure 8, SPA With Encapsulated Die



## 5.1.4 BBN QuietChip MCM

#### 5.1.4.1 Product Overview

The QuietChip MCM was jointly developed by Motorola's ASEM Foundry and BBN Systems and Technologies in Cambridge, MA. The development of this product was sponsored by ARPA to promote expanding commercial and military markets for Active Noise and Vibration Control (ANVC) systems. The controller functionality and algorithms being developed under other ARPA-funded programs were incorporated into this product to provide a general-purpose, fully-adaptive, broadband/tonal, multi-input, multi-output controller.

Two divisions of General Motors Corporation have committed to demonstrate this product in automobiles and locomotives which can use ANVC systems. The first of these demonstrations is scheduled for December, 1995 at the GM Proving Ground. The vehicle supplied by GM, is a 4-cylinder 1995 Cavalier which has been equipped with microphones in the cab and accelerometers on the suspension system. The road noise will be "quieted" by the car's four speakers. Four to six QuietChip MCMs will be installed on the demonstration PWB to control the noise. The goal is control both narrow-band noise (20 dB for engine harmonics in 50<f<200 Hz) and broad-band noise (10 dB for road noise in 50<f<200 Hz) to reduce the road noise in the cab of the car.

## 5.1.4.2 ASEM Foundry Tasks

For this program, Motorola's ASEM Foundry was contracted to perform the following tasks:

- Provide consultation for system design and partitioning
- · Recommend I.C.s based on die availability
- Capture schematic
- Conduct thermal and electrical analysis
- Create die library with bonding pad information
- Design substrate
- Design test fixture for dual MCMs
- Design manufacturing tools
- Conduct Manufacturing Readiness Review
- Procure tested substrates
- Assemble 5 prototypes
- Assemble 20 production units

## 5.1.4.3 MCM Design

The QuietChip MCM design was based on Motorola's digital signal processor, the DSP96002. This is a 96 bit, floating point, dual-port processor capable of 50 MFLOPs. In this application the DSP was clocked at 40 mHz. The final configuration of the QuietChip MCM consisted of 10 die with 850 wirebonds, 3 surface mount I.C.s and 70 SMT resistors and capacitors. The die included the DSP, 4 SRAMS, 1 Altera EPLD, an 80 MHz clock generator, 1 DAC, 1 volt. reference generator, and a 10-bit bus switch.

During the preliminary design phase, BBN followed Motorola's suggestion to partition the design to take advantage of repeated circuitry. The final configuration of 10 die was chosen to increase first time yield and reliability while lowering the total production costs. Also during this phase, a concurrent engineering effort between BBN and Motorola's ASEM Foundry optimized the MCM design for testability, die availability and thermal management.

Cadence Concept was used for the schematic capture and Cadence Allegro was used to design the substrate. All of the die and SMT parts were packaged on a double-sided, 2.0 in. x 2.0 in., 140 pin quad flat package. Eight layers were utilized for the design and are shown in Figure 9. The design consisted of 294 nets which required 1300 vias. To accomplish this, 450 blind vias and 850 thru vias were used.

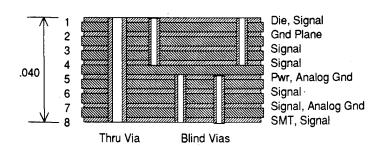


Figure 9, QuietChip Layer Structure

To control crosstalk between the digital signals and the critical analog signals, the substrate was partitioned as shown in figure 10. The analog components were physically isolated from the digital components. The designer paid special attention to the signals at the analog/digital boundary as any digital signals that crossed the analog ground plane could be the source of noise. This proved to be a very effective method for controlling the noise, especially in consideration of the resolution required for the 16-bit, AD7882, A/D converter. Figure 8 and 9 on the following pages shows both sides of the QuietChip MCM.

Figure 10 QuietChip Ground and Power Planes

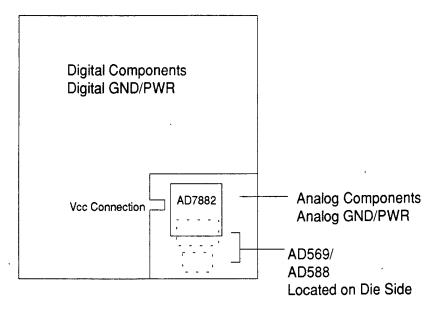


Figure 11 QuietChip MCM, Die Side

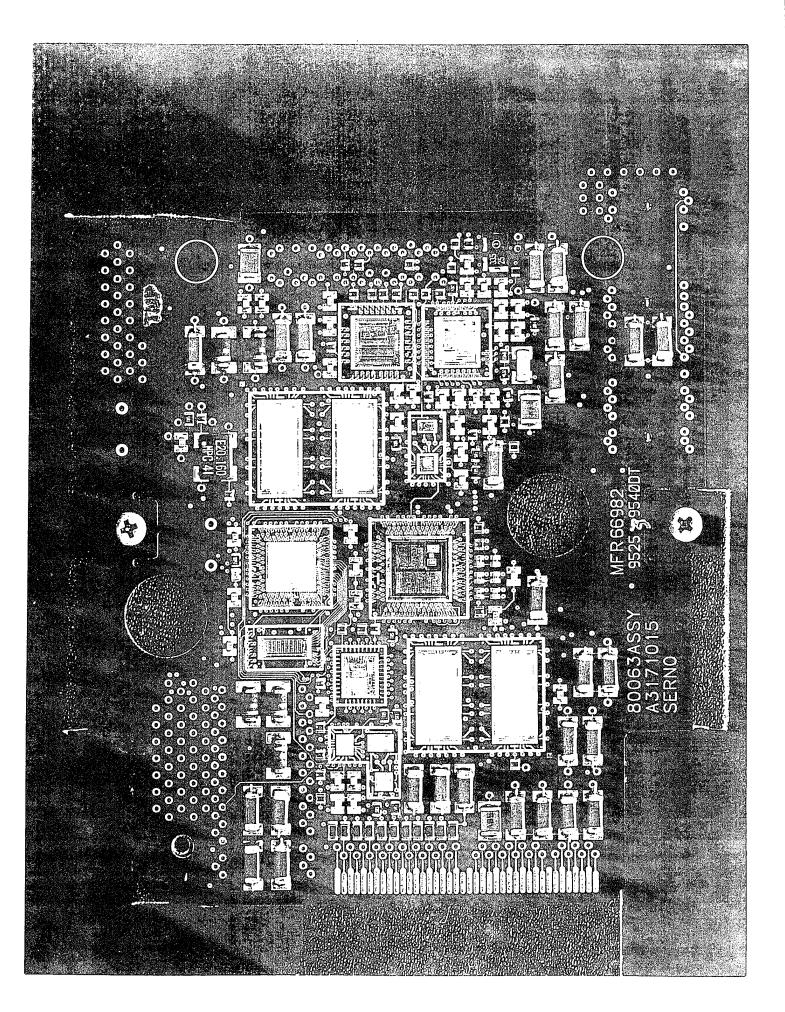
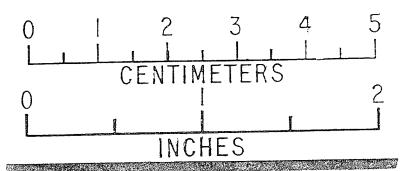
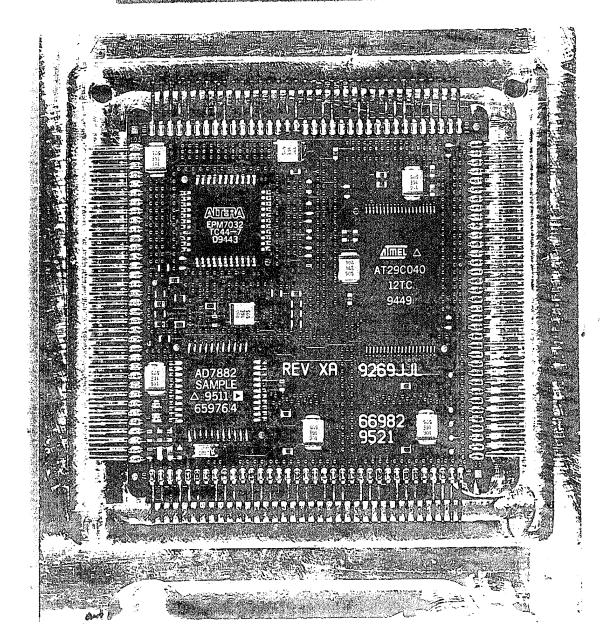


Figure 12 QuietChip MCM, Surface Mount Side





## 6.0 Important Findings and Conclusions

## 6.1 Substrate Design

These two designs were accomplished using two different workstations. The design of the BBN QuietChip was accomplished using Cadence Allegro MCM. The Hughes SPA was designed using Mentor MCMStation. A comparison of the two MCM development tools is included in this report in Appendix G and addresses the support infrastructure, automatic routing and other criteria used in our comparison.

From a project schedule standpoint, the BBN QuietChip design went much smoother primarily because of the experience of the designer on this machine from other programs. There was a considerable learning curve associated with the Mentor MCMStation used for the Hughes SPA. We experienced automatic routing problems with the Mentor workstation with only 70-80% of the nets being successfully auto-routed. In contrast, the Cadence design tool successfully routed 94% of the nets on the first pass.

Metrics are difficult to quantify for these two designs because of the variances in complexity and the problems associated with using a new tool for the first time. The BBN design was difficult because of the density of the components, the number of nets and the number of vias/in. Components had to be grouped within encapsulation areas and breakout vias had to be located under the encapsulation area to keep the 2.0 in. x 2.0 in. substrate size. The total time for the substrate design was approximately 280 hours including a re-design to move some of the digital signals away from the analog power planes. The cycle time was kept to minimum because we were able to electrically transmit the design files to BBN for quick checking.

The Hughes SPA design took less time, approx. 240 hours, partially due to the lower component density and the way the critical signals were routed on separate layers. The SPA was a single-sided MCM with only the connectors on the opposite side of the die. The QuiteChip was double-sided with die on one side and surface mount parts on the other side. The added layers for the SPA added cost to the substrate (10 layers vs. 8) but helped to lower the overall design time.

#### 6.2 Die and Module Yield

For the BBN program, the ASEM Foundry specified and procured all of the die. The quality level varied from die that was DC probed at the wafer level to die that was 100% tested. None of the die was burned-in or could be considered as Known Good Die. Some die was tested, but not at the maximum rated speed. For example the 256K x16 Micron SRAMs were 100% functionally

tested but not speed sorted. The DSP96002 was only tested to 10 mHz. To date, GSTG has manufacture 5 QuiteChip prototypes and 2 die have failed functional in circuit test. The first time yield was 40% (2 out of 5) for the modules due to die yields.

For the Hughes SPA, Hughes specified and procured all of the die. The quality level for this program was element evaluation. A sample of die (10-20) for each wafer were packaged and tested. To date there has not been any SPA failures attributed to die.

Manufacturing

Very few problems arose during the manufacturing effort for these two programs. For BBN, two prototype MCMs were fabricated first and tested at GSTG. Two open wirebonds were investigated and revealed that the gold thickness on the wirebond pads did not meet the thickness specified. Gold thickness is very critical for thermosonic gold-ball wirebonding. An ASEM Foundry study concluded that a thickness between 50 and 80 microns is required for reliable wirebonds. The first lot of BBN substrates had gold too thin and were returned to the supplier. Subsequent substrates, which met the thickness requirement, showed no signs of open wirebonds and passed a wire pull test.

#### 6.3 Testing

Early on in the QuietChip program, BBN and Motorola decided to fabricate two identical test fixtures so that each company could have a local test set-up. To further assist trouble-shooting, these two fixtures were electronically linked together using a modem and a Sun Workstation. This allowed BBN to download test programs to Motorola and to monitor testing at their facility The BBN test set-up used a SPARC 2, Sun Workstation for the DSP in-circuit emulation. For JTAG Boundary Scan, a T.I. Asset Board was installed in a PC. Using these two interfaces and software generated by BBN, all of the die can be tested and verified for correct operation.

All of the devices were packaged on a 4 in. by 4 in., 062 "thick, polyimide substrate with the size conforming to the power supply assembly which is bonded to the back or connector side of the substrate. The minimum conductor line width and conductor space was 4 mils. The substrate was designed and fabricated to meet industrial standard IPC-276, type 2, class 3. Testing of the substrates was specified in the fabrication drawing and called out continuity testing to the netlist. Each net was verified and then tested for shorts to ground and to power.

The SPAs were shipped to Hughes for testing, prior to encapsulation, in containers designed by GSTG to protect the die and wirebonds. Figure 3 shows the SPA prior to encapsulation. After testing, the die and wirebonds were encapsulated with a epoxy compound at GSTG. Figure 9 shows the SPA assembly prior to installation in the Thermal Weapon Sight. Note the clear silicon gel used to protect U6 and U10, the microcontrollers. This permitted Hughes engineering to erase the EPROM resident on the micro-controllers and reprogram the I.C.s using a via field for the electrical interface. The testing done at GSTG showed that this material could withstand high temperatures and would permit UV erasing.

#### 7.0 Suggestions for Further Research

#### 7.1 Chip Scale Integration

The future of integrated electronic packaging is "direct chip attach" schemes that enable the testing of die at the wafer level and utilization of low cost manufacturing techniques. Motorola is quite interested in the "chip scale integration" schemes as a enabling technology to implement these concepts and recommends that ARPA support research and development in this area. The concept of high interest in chip scale integration, is the interconnection of die at a wafer level (functional grouping of the die and common processing are assumed) followed by flip chip interconnect to the host substrate. The advantages of this approach include:

Facilitates functional testing of die

Avoids die interconnect dispersion

Enhances performance

Compatible with "chip on board" packaging

Allows for integration of passives on the die

Low cost

#### 8.0 Summary

Motorola has established a merchant ASEM Foundry to serve both Government and commercial opportunities. This has been accomplished using two separate design centers, one for Government customers and one for Commercial customers(Dual Use) together with a common manufacturing facility that is maintained with the latest state of the art equipment and personnel and guided by proven Motorola processes. A block diagram of the ASEM Foundry is shown in Figure 1.

The commercial part of Motorola's ASEM Foundry is the responsibility of GSTG's Diversified Technologies Division (DTD) and is a joint venture with Motorola's Semiconductor Products Sector (SPS). SPS is responsible for the marketing support of the Foundry and support of devices for use in the Foundry. It should be noted that the Foundry is not bound to use Motorola devices exclusively, but rather use Motorola devices to the maximum extent possible consistent with function and cost considerations. DTD provides the lead for the Foundry and is responsible for performance of the MCM development including design, part selection, layout and test, manufacturing processes and equipment for the successful build of MCMs. In addition the MEF is also responsible for the development and maintenance of the design rules as they pertain to the manufacturing process and for the development and maintenance of qualified personnel. The Government portion of the Foundry is the responsibility of GSTG's Government Electronics Division (GED). GED is responsible for the design, part selection, layout and test of ASEMs. Each ASEM opportunity is addressed as a separate project beginning with the identification of an opportunity and continuing through the delivery of finished modules. This portion of the Foundry is fully compliant with all Government requirements and as a result, is responsible for seeing that the MEF is also compliant to the Government's requirements. Additionally, the Government Foundry is responsible for maintenance of the design kits, the layout systems and the test systems necessary for the support of the ASEM Foundry at GSTG.

Staff functions of GSTG also support the Foundry in the areas of quality assurance, material acquisition and tracking, management systems and corporate technology transfer.

Motorola met the cycle time objectives for the fabrication (including substrate procurement) and test with first pass success of less than four weeks on two separate programs. The Government portion of the Foundry was the first in operation and during the period of this contract, aggressively pursued over 30 MCM opportunities for Government applications. The first program was an MCM for BBN that consisted of 12 die on an laminate substrate using "glob top" encapsulation. The second was an MCM for Hughes that consisted of 16 die on a laminate board.

Most of the projects for ASEMs that utilized the Foundry were in support of Government applications where the ASEM development was a part of the project and not "the project". Notably, the Foundry was key to the development of the PRC 112-GPS where an MCM solution allowed insertion of a GPS receiver into the PRC-112. In addition, the Foundry supported the development of the GPS MCM with Mayo Clinic that resulted in the smallest GPS receiver, a credit that stood until mid-95.

Motorola is anticipating significant ASEM opportunities from commercial applications including a number of projects in support of Motorola's other equipment Groups and Sectors as well as merchant projects. SPS's World Marketing organization is already bringing ASEM opportunities to the Foundry that are characterized as MCMs with chip on board, mixed signal design and quantities in excess of 200K modules per year.

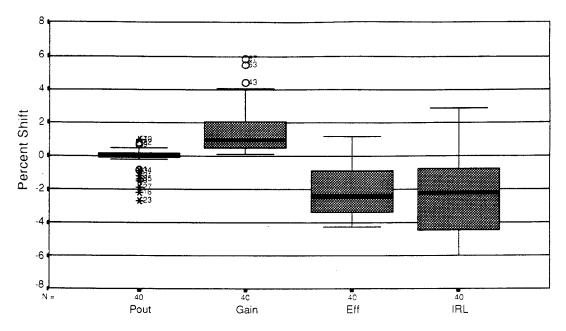
Motorola thanks ARPA-ESTO for its support in the establishment of the ASEM Foundry and looks forward to many years of prosperus business for the Foundry.

#### Appendix A

**Business Plan** 

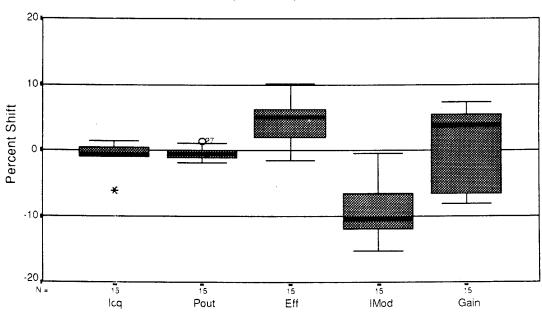
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**ASEM Foundry Joint Venture** 



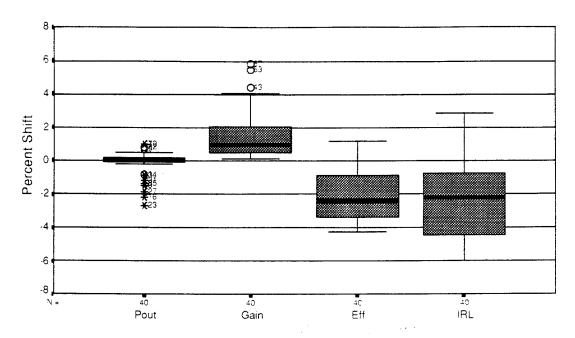
Electrical Parameter

Figure 2 MRF897, tested at 900 MHz Pre to post encapsulation



Electrical Parameter

Figure 3 MRF15090 tested at 1500 MHz Pre to Post encapsulation



Electrical Parameter

Figure 4
MRF898 tested at 830-960 MHz
Pre to Post humidity exposure

#### Appendix C

Design Kit

for

Motorola's ASEM Foundry

#### **DESIGN KIT**

for the

#### APPLICATION SPECIFIC ELECTRONIC MODULE (ASEM)

MERCHANT FOUNDRY

Based on favorable results from standard databook testing of the three device types, further qualification and full-blown characterization activities have been planned. Qualification studies will include power cycling, temperature cycling, life test, humidity and popcorning test. Characterization efforts will concentrate on established parameters of the databook devices compared with devices which utilize liquid encapsulant. Hopefully, further testing will show that liquid encapsulant does not alter the RF performance and that liquid encapsulant can become a "drop-in" for the current ceramic lidded RF device with improved reliability and manufacturability.

#### **Conclusion**

The authors have drawn several conclusions based on the testing presented in this paper. First and primary is that the Dexter Liquid encapsulation is capable of use up to at least 1.5 GHz although how it affects electrical performance can vary radically depending on circuit and package design. Second: is that testing of the encapsulation can be performed quite inexpensively using hand application of the materials. Third: application of the liquid encapsulation does not disturb the geometry of the bond wire. Fourth, normal levels of humidity have little effect on the circuit performance.

The development of a reliable liquid epoxy encapsulation system has greatly increased packaging options when designing RF and mixed signal equipments. Applications in low volume where tooling cost of transfer molding is prohibitive, package designs that do not lend themselves to molding, and in places where only portions of the circuit need encapsulation are prime candidates for Liquid Epoxy Encapsulation.

#### References

- 1/ D. Robinson, M. Papageorge, C. Naito, "A New Epoxy Based Liquid Encapsulant With Performance Comparable To Mold Compounds" Proc.. Int. Electronics Packaging Society, (Sep. 1993)
- 2/ B. Besser, L. Bell, D. Robinson, "MCM-L Approach Provides Cost-Effective MultiChip Modules" Solid State Technology, (April 1994)

#### **Experimentation**

To determine the effects of liquid encapsulant on RF devices in the range of 830MHz to 1.5GHz, three standard Motorola databook device types were chosen. The three devices chosen had gold metallization and used gold wedge bonds. Devices were selected after completion of wire bond. All samples were tested to the standard databook tests as a minimum using control samples as verification for fixture correlation. Devices were then manually liquid epoxy encapsulated using Dexter FP4451 dam followed by encapsulation with Dexter FP4450. Testing--identical to pre-encapsulant--was performed on both encapsulated devices and correlation control units.

The first device type, the MRF897, was a 30W power transistor typically used in amplifier applications. Device testing was performed per the data sheet at 900MHz with critical parameters of gain, efficiency, and intermodulation. Additionally, Input Return Loss was also measured. Pre and post liquid encapsulant parameter measurements showed an average degradation of 1.0% (0.2dB down from pre-encapsulation measurements), a 2.5% decrease in average efficiency and an Imod change of 6.6%. Additionally, input return loss on the average was 2.0% lower. All measurements were well above minimal databook limit levels and these minor changes are considered more indicative of test fixture repeatability than of actual pre-encapsulation effects. (figure 2)

The second device type, the MRF898, was a power transistor which was tested during this experiment at frequencies of 850MHz, 900MHz (databook), 930MHz, and 960MHz. Critical parameters include gain and efficiency. Although not specified in the databook, input return loss was also measured. Based on averages, changes in gain measurements showed maximum degradation of 7.2% (a shift of 0.5dB) at 960MHz. efficiency took the largest decrease of 13% at 930MHz (from 61.5% to 53.5%) while worst case input return loss changed from -20.7dB to -28.0dB at 850MHz after encapsulation. Although gain stayed within specification limits, post encapsulation efficiency at 900MHz would be considered out of specification limits by 2%. Due to the RF performance variances experienced over the different frequency ranges, a future restudy of this device is recommended.

The third device type, the MRF15090, was a 1.5GHz, 90W device. Key RF parameters during test at 1.49GHz include, gain, efficiency, return loss, and intermodulation. Gain and efficiency were both affected by nearly 5%. A 10% shift in intermodulation was also experienced. However, all performance shifts were within allowable specification limits. (figure 3)

To determine the susceptibility of liquid encapsulant on the RF devices, humidity testing at 85°C/85% RH for 48 hours was performed on the MRF898 devices described above. With less than a 2% shift in post liquid encapsulant (pre-humidity testing) to post humidity testing, the RF liquid encapsulated devices appeared to be impervious to humidity effects. (figure 4)

One of the commonly asked questions of the effects of liquid encapsulant on high frequency RF devices is a question of changes in wire bond topography. Due to the very sensitive nature of RF performance caused by wire bond changes in internal wire spacing, real time X-rays were taken before and after encapsulation. No shift in wires was observed.

#### Representation of the Liquid Epoxy Encapsulation System

Epoxy based liquid encapsulant formulations include several constituents which are blended together in precise amounts to modify the Coefficient of Thermal Expansion (CTE) of the cured encapsulant. The most common additive to encapsulants and mold compounds is spherical fused silica. Fused silica, with a (CTE) of about 0.5 ppm/°C, is used to modify the cured encapsulant expansion coefficient. Generally, most liquid encapsulants contain more than 60% by weight fused silica before the CTE begins to approach that of commonly used substrate materials. Other additives in encapsulant formulations include elastomer additions which disperse throughout the structure of the encapsulant during curing and adhesion promoters.

The most common method of mechanical and chemical protection in use for MCM-L devices is epoxy overcoatings, sometimes referred to as "glob top" or "liquid encapsulation". Historically, these materials have not demonstrated reliability on par with molded plastic packages. This is now changing with the advent of new epoxy resin chemistries which exhibit excellent moisture resistance and thermal cycling performance. Encapsulant chemistries are based on silicones, epoxies and silicon-carbon. Caution must be exercised in the use of silicones and silicon-carbon chemistries since the commonly used platinum catalyzed hydro-silation cure mechanism can be easily "poisoned" by epoxy materials containing amine curing catalysts.

#### **Purpose**

Since initial development the use of Liquid Epoxy Encapsulants has spread to applications such as MCM-L, SLIC and SIM packages. These applications have expanded to productions of more than one million devices with excellent field history. To date, all applications have been low frequency or digital. Motorola Multichip Module Systems and Motorola RF hybrids have identified the need for liquid encapsulant materials in RF circuitry.

Motorola's business has a strong emphasis on communication systems technology. The heart of these systems are based on mixed signal circuitry (digital and RF). It is believed that Multi-Chip Modules and RF hybrids will play an important roll in the demand for smaller, lighter and cheaper communication devices. Attempting to cost effectively integrate mixed signal circuits and achieve higher packaging density with acceptable reliability in RF hybrids and MCM's requires development of encapsulation techniques compatible with RF circuitry. Motorola has previously demonstrated the reliable use of liquid encapsulants in conjunction with laminate substrate technology and is presently qualifying use with ceramics. This presentation deals with testing performed to extend the use of this liquid encapsulant to frequencies 900 MHz and above.

Very little information is available about the effect of encapsulating an already tuned RF circuit with an epoxy coating. There is much conjecture among the RF design community about the detuning that may occur due to the change in dielectric constant from near 1 in free air, where the device is tested, to a dielectric constant of 4 or more for the epoxy encapsulant. Accurate modeling of the encapsulation effects are difficult because the results depend on the assumptions. In some applications devices must be tuned prior to encapsulation and must remain tuned. Other applications require only that changes due to encapsulation are predictable.

#### **Introduction**

As experienced with other integrated circuit technologies, liquid encapsulant has provided a low cost with equal or improved reliability sealing method. RF technologies, especially in the high frequency ranges (900MHz and above), have appeared reluctant to shift existing sealing methods for concern over RF performance changes. It was assumed that the already delicate balance of internal wirebonding would be affected through a shift in wire position and/or the change in dielectric constant from free air to the fully encapsulating material would have disastrous effects.

In an attempt to quantify whether basic parameter shifts would occur in known established RF devices, three standard high frequency Motorola RF power transistors were chosen for encapsulation. Performance characteristics--such as gain, efficiency, return loss, and intermodulation--were measured before and after encapsulation. With this cursory investigation, no attempt was made at a full-blown characterization comparison between standard and liquid encapsulated devices.

#### Liquid Epoxy Encapsulants

Liquid epoxy encapsulants, commonly referred to as Glob Tops, are presently being used at Motorola for a variety of applications. Lower equipment costs and the elimination of costly tooling have made this technology ideal for small productions, non-standard package configurations, and packages that do not lend themselves to transfer molding. Motorola first helped develop and qualify the present formulations of Liquid Epoxy Encapsulants at their Advanced Packaging Development and Prototyping Laboratory for use with Laminate Multichip Modules [1][2]. This research has resulted in the development of a Liquid Encapsulation process that is capable of passing equivalent qualification requirements to that of molded plastic devices. These requirements include 1000 temperature cycles from -65°C to 150°C and 144 hours of autoclave at 121°C, 2 ATM and 100% RH with no failures. The multichip test vehicles for these tests included 9 test die measuring .75" X .3" chips with over 2000 bond wires. Other tests have been ran exposing test vehicles to biased 85°C/85% RH for in excess of 5000 hours without failure.

The Liquid Epoxy Encapsulant system chosen by Motorola requires two part application. The process begins with the dispensing a flow constraining dam of highly thixotropic epoxy just prior to encapsulant deposition (Figure 1). Subsequent encapsulant is deposited within the constraining dam and allowed to fill the area. The entire encapsulation system is (dispensed dam and the encapsulant) is concurrently cured in a furnace or oven.

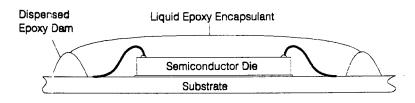


Figure 1

#### The Effect of Liquid Epoxy Encapsulants on RF Device Performance

By
Brant Besser
Motorola GSTG
Multichip Module Systems
Lori Carroll-Shearer
Motorola SPS
RF Communication Components

#### **Abstract**

Due to recent innovations in formulation chemistry. Liquid Epoxy Encapsulation (glob top) has been gaining in use for mechanical and environmental protection of Integrated Circuits, Hybrids & Multichip Modules. Liquid Encapsulants offer advantages in non-recurring costs such as tooling and capitol equipment. Presently these encapsulation materials are being used primarily for digital and low frequency applications. Motorola Multichip Modules Systems (MCM/S) and RF Communication Components (RFCC) operations anticipate the need for this technology in RF and mixed signal applications in order to maintain cost efficiency. This paper deals with testing performed to extend the use of this liquid encapsulant to frequencies of 900 MHz and above.

Very little information is available about the effect of encapsulating tuned RF circuits with an epoxy coating. There is much conjecture among the RF design community about the detuning that may occur due to the change in dielectric constant from near 1 in free air, where the device is tested, to a dielectric constant of 4 or more for the epoxy encapsulant. Accurate modeling of the encapsulation effects is difficult because the results depend on the assumptions.

In an attempt to-quantify changes in RF circuit performance due to encapsulation, Motorola MCM/S and RF Hybrids Operation have tested several RF hybrid device types ranging in center frequency from 900 MHz to 1.5 GHz. RF performance of a typical device was measured before and after encapsulation. Additionally, tests were run to check for the effects of moisture penetration into the epoxy encapsulant due to 85°C/85%RH exposure. Power out, Gain, Return Loss and Efficiency were the device parameters of interest.

Results of the testing indicate that the encapsulant has minimal effect on most RF parameters. Gain, Power Out and Efficiency were typically less than 10% change from pre to post encapsulation. Return loss was effected more dramatically with the magnitude being less predictable. Moisture had no perceptible effect on the device performance.

The changes observed in the RF circuitry due to liquid epoxy encapsulation are within the operational capability of most designs. RFCC is presently running qualification testing for future offerings using liquid encapsulation. GSTG plans on encapsulating RF circuitry beginning with the MCM-L GPS being designed and built by Motorola MCM/S.

#### Appendix B

#### The Effect of Liquid Epoxy Encapsulants on RF Device Performance

# **Distinctive Competencies**

#### GSTG

- multiple engineering disciplines and manufacturing Program Management for complex programs with content.
- Engineering expertise in RF, DSP, Software, and packaging.
- Systems engineering expertise in developing up front requirements for first time success for program development
- Six Sigma product quality leadership.

#### Spo

- Global presence; local design centers.
- Breadth of product portfolio.
- High volume Manufacturing.
- Automotive, communications leadership.
- Longevity of customer relationships.
- Six Sigma product quality leadership.

## Critical Success Factors

Systems level design knowledge/capability.

Packaging Expertise.

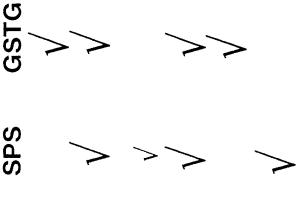
Volume suppliers of tested good die.

High reliability manufacturing process.

Rapid turnaround on prototypes.

Access to high volume customer base.

Low cost manufacturing.



#### · IBM

- Actively pursuing MCM business.
- Experience in KGD and die level packaging.
- Technology on the shelf.
- Image.
- \$450M in sales in 1994.

## Micro Module Systems

- Most visible in MCM manufacturing.
- High performance deposited substrate technology.
- Technology partner with Intel.
- Currently building standard product MCM's based on Pentium and 486 products.
- Aggressively pursuing relationship with Motorola
- Major program with Dell Computer on Intel based MCM.
- Sales in the \$20-30M range.
- Building & equipment fully paid for.
- Lacks packaging expertise.

## National Semiconductor

- Broadest line of bare die products
- Offer 4 levels of bare die testing
- DC probe (mature devices)
- » DC probe with lot acceptance test
- Full AC/DC test at worst case temp.
- 69 products currently offered at this level
- 100% die level test at all temps with burn in.
- NRE \$5000-15,000
- Strengths
- » Broad product line in MOS Logic
- Weaknesses
- » Limited processor and memory technology
- » Image

# **Competitive KGD Programs**

#### 

- Most experience in industry on die level packaging.
- Currently using R3 process on C4 bumped die.
- Qualified dendrite technology in July, bringing volume production on line.
- Working on KGD process for aluminum bond pad die.
- Recognizes advantages of multi-chip packaging.
- » PowerPC<sup>TM</sup>.
- » Automotive (pursuing Chrysler).
- Strengths.
- » Vast experience in die level packaging.
- » Technology on the shelf.
- » Aggressive.
- Weaknesses.
- » Inexperienced marketing and sales organization.
- » Limited product line.

# Competitive Known Good Die Programs

#### • Intel

- Established KGD program-"Smart Die"
- Uses TI/MMS Die-Mate approach
- AC/DC probe and at speed testing @ 0-80C
- Comprehensive portfolio of supported product.
- Using KGD to help leverage entry into embedded control marketplace.
- manufacturers to implement advanced packaging. Technology partners in the form of contract
- Strengths
- » Micros, MCUs, Flash Memory
- » Highly profitable organization
- » Key technologies-Flash, PicoPower relationship
- Weaknesses
- » Limited product line. . . no DSP or Fast SRAM
- » Limited customer base (currently)

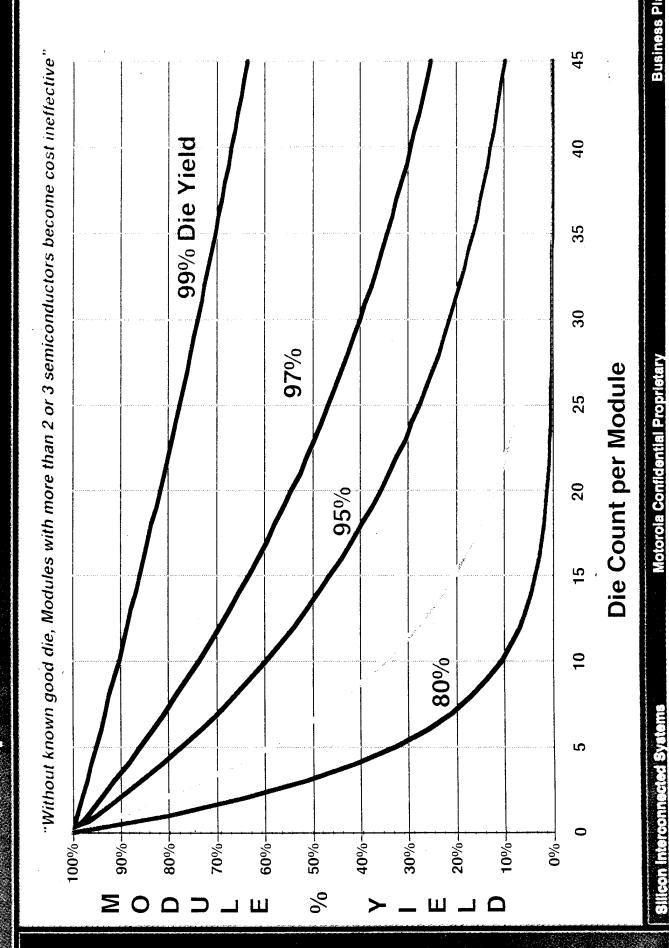
# ssue - Testability/Acceptance

- SIS Level Test Design Concepts
- Requires access, and design-in test strategy.
- No one test strategy followed ... must strategically identify test qoals.
- Possible Test Goals:
- Identify interconnectivity testing
- Employ 1149.1 JTAG commands to exercise connections.
  - Check patterns between die for connectivity.
- Die level testing using internal test vectors generation.
  - Utilize functional testing between components.
- Exercise internal microprocessors systems.
- Die level testing via external supplied test vectors.
  - Utilize test vectors into 1149.1 JTAG port.
- Target complete or partial functionality testing.
- Clock control for sampling in module.
- Utilize clock to view specific lines for test outputs.
- Employ 1149.1 language for sampling

## Issue - Known Good Die

- Dataquest estimates by the year 2000 that approximately 15% of all semi's will be shipped as bare die.
- Low yielding untested dice will have an adverse effect on module
- 98%, however will not solve at speed testing which requires die level Hot chuck probe will increase yield expectations to approximately
- Bare die testing can only be cost justified in volume
- Can use TI/MMS die mate approach
- SLIC package from LMPS shows promise as a low cost chip carrier for die level testing. . . requires bumped die.
- SPS is currently testing only Fast SRAM for known good die . . . limited burn-in of HC11 at wafer level for automotive.
- Critical products that will be involved in MCMs include: Processors; DSP; ASICs; RFICs; Custom MOS D-A; Memories.
- Implementation of a known good die program will take 9 to 12

# mpact of Die Yields on Module Yield



## **Competitive Overview**

- Semiconductors competitors implementing known good die programs . . ,~o⊻er 20 announced
- possess high volume manufacturing expertise... lack systems engineering of MCM modules. . . SCI, Solectron, Flextronics all Contract Manufacturers attempting to move to value added engineering expertise.
- possess captive MCM production lines. Although not competitors consumer goods manufacturers, and Mainfraine manufacturers Vertically integrated companies, e.g., AT&T, NEC, Japanese today in the merchant market . . . potentially in the future.
- MicroModule Systems achieving some success, primarily in personal computers.
- IBM and TI are both active in the MCM market.

## 目の言語が

## **Driving Forces for SISs**

· Size and weight.

## Barriers to SIS Growth

- Multi-chip packaging must provide a lower cost.
  - · Known good die testing cost.

### Substrate Usage

 Laminates to achieve lowest possible cost.

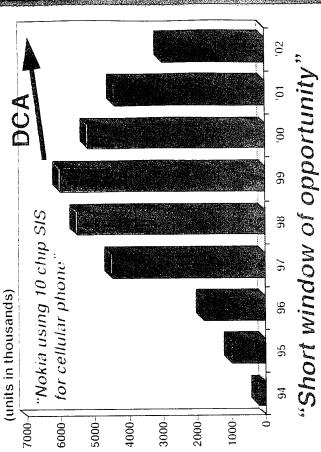
### SIS Current Usage

- Matsushita using in a pager.
- Nokia using a 10 chip module in a cellular phone.

### Likely Scenario

- Pagers will move directly from SMT to direct chip attachment or chip on board, only 5% to 10% adoption rate for SISs.
  - 30% to 40% of Digital Phones (includes cordless) will use SISs.
- Direct chip attach will dominate by year

## Cellular Phones/Pagers SIS Usage



## **Driving Forces for SISs**

- Primarily driven by electrical requirements for data rates of 2622 Mbit/second.
- Lower power consumption.

### Likely Scenario

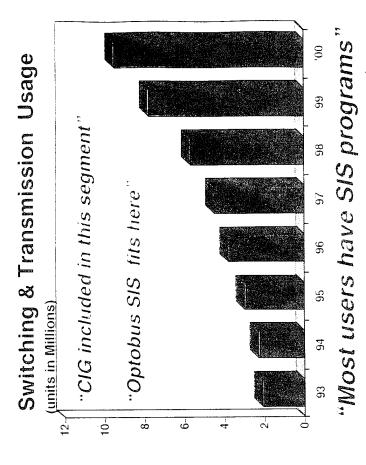
- Line cards emerge as volume application.
  - Adoption of Broadband ISDN and SONET will drive volume.

## Barriers to SIS Growth

Reliability requirements.

### Substrate Usage

- · Laminates for cost sensitive line cards.
  - Thin films/Ceramics for switching and transmission modules.



# STOPEN TO TO THE STOPEN OF THE

## **Driving Forces for SISs**

Smaller size and less mass to reduce the effect of vibration, increasing reliability.

## Barriers to SIS Growth

- Reliability requirements.
- · Cost.

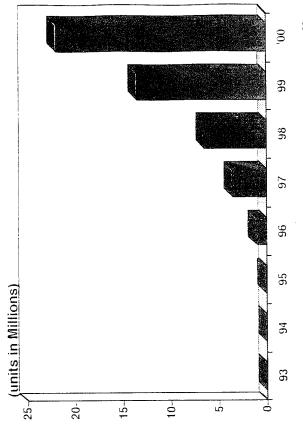
#### Substrate Usage

- Ceramics for on the engine applications.
  - Laminates for Powertrain controllers.

### Likely Scenario

- On the engine applications for injection, ignition and throttle control- 15% adoption by 1999 using ceramic substrates.
- Powertrain controllers with a 32 bit processor and logic control chips- 25% adoption by 2000 using laminates.

### Automotive Usage



"Development now taking place"

# Melvievo strembes tento/strotteoliminimines

Subsegment	Market Characteristics	Competition	Unit Volumes 1997 2000	Potential Customers
Switching/Transmissior	<ul> <li>High Volume line cards</li> <li>Cost Sensitive</li> <li>NT, NTT, AT&amp;T in-house capability</li> </ul>	• Captives	4.3M 9M	• CIG • NT • AT&T
Cellular phones/pagers	<ul> <li>High Growth</li> <li>Short window- move to DCA</li> <li>Cost sensitive</li> </ul>	• Nokia? • AT&T	4.5M 5.2M	• csg • pwdg
Personal Communication Networks	<ul> <li>R&amp;D now</li> <li>Volume in 2000 (if any)</li> <li>End applic. cost must be competitive with wireline</li> </ul>	• AT&T? • Contract MFGs?	0 .4M?	• RBOCs • Cable? • IBM (RF LAN)
Automotive	<ul><li>High Volume by 1999</li><li>Control applications</li><li>Driven by Reliablity</li></ul>	<ul><li>Captives</li><li>AECG</li><li>IBM</li></ul>	4M 23M	• Ford • GM • Chrysler • Bosch
Multimedia	•	•	¿ ¿	
Consumer	<ul><li>Slow growth market</li><li>Camcorders heavy usage</li><li>Mostly Japanese captives</li></ul>	<ul> <li>Captives</li> </ul>	· ·	Most likely none
Military	<ul><li>Declining market</li><li>Controlled by Captives</li><li>Gov't funded activities</li></ul>	<ul><li>Military OEMs</li><li>TI, Harris, AT&amp;T</li></ul>	Not Applicable	No Participation

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## Side in PC Cards

## **Driving Forces for SISs**

- · Portable Computing.
- Upgrade path to memory and communications.
- · Size

## Barriers to SIS Growth

- · Known good die availability.
  - Low cost substrates.
- Low power devices.

### Substrate Usage

Laminates for low cost

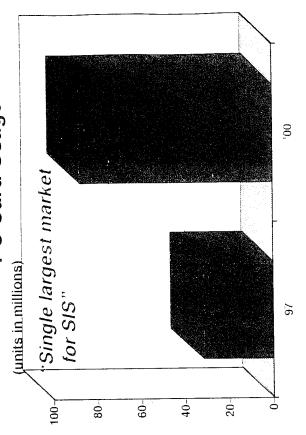
#### Competition

- · IBM, Intel, 3COM, Sundisk
- Epson, Toshiba, Fujitsu

#### Likely Scenario

- Market driven by portable computing . . small size, low cost.
- Expansion for laser printers, faxes, etc.
- Set top boxes, cartridges for video games applications emerge.
- Migration to desk top computing applications.

#### PC Card Usage



## Driving Forces for SISs

- Decreasing size.
- SISs for processor &communications circuitry for high density.

## Barriers to SIS Growth

- Highly competitive market . . . . prices of end products <\$1000.</li>
- Cost of SIS cannot exceed cost of the components

#### Substrate Usage

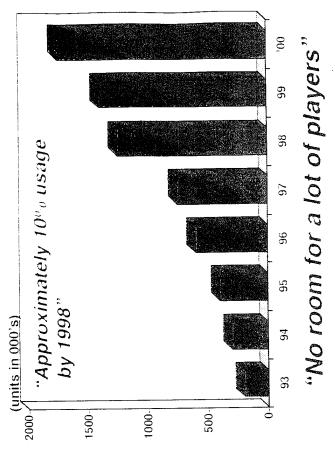
 Laminates will represent virtually 100% of the market due to cost, low electrical performance requirements.

Note: Does not include PC cards

### Likely Scenario

- Thin single chip SMT packages will dominate.
- DCA with wire bonding, TAB, or flip chip attachment offers the highest density.
- Processor circuitry will remain single chip.
  - SISs to integrate communications.

## Pen Based & PDA Usage



# 

## Driving Forces for SISs

- Decreasing size for notebooks.
- Increasing performance for servers.
- Enhanced features, e.g., higher resolution displays, communications in same or less space.

## Barriers to SIS Growth

- Known good die, cost and testability are most significant barriers.
- Single chip package performance, e.g.,
   BGA, delaying need for higher performance packaging.
- ASIC suppliers slow in introducing fully tested bare die.
- · Integrating silicon chips from different suppliers.

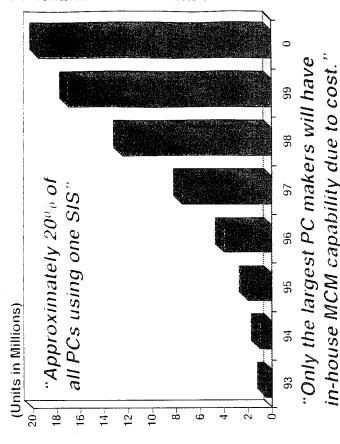
#### Substrate Usage

- Laminates will represent 85% of the market due to cost and moderate performance requirements.
  - Ceramics will be used for high performance, high power chip sets.
    - Thin films limited to applications requiring high packing density and performance.

#### Adoption Rate

- Notebook 10% in '97, 30% in '00
- Desktop 10% in '97, 20% in '00
- Server 30% by '97,
- · Average one SIS per computer

## Desktop & Notebook Usage



## Driving Forces for SISs

 Performance improvement by minimizing signal propagation delay between chips

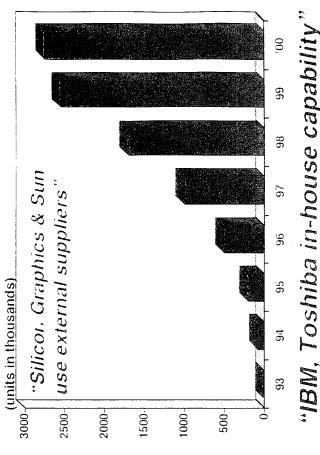
## Barriers to SIS Growth

- High manufacturing cost
- Availability of known good die

#### Likely Scenario

- clock rates, mainly servers, with two Adoption in systems with >100 MHz SISs per server
- Some laptop workstation applications with size constraints

### Workstation Usage



Source: TechSearch International Inc.

Thin films for clock rates >200 MHz

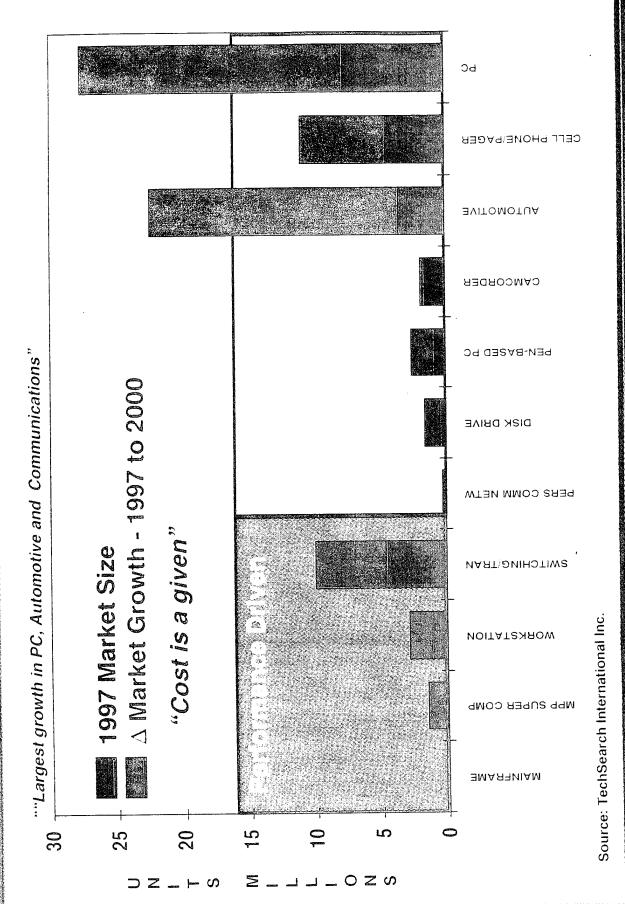
sensitive applications

 Initially multicavity ceramic PGAs BGA laminate packages for cost

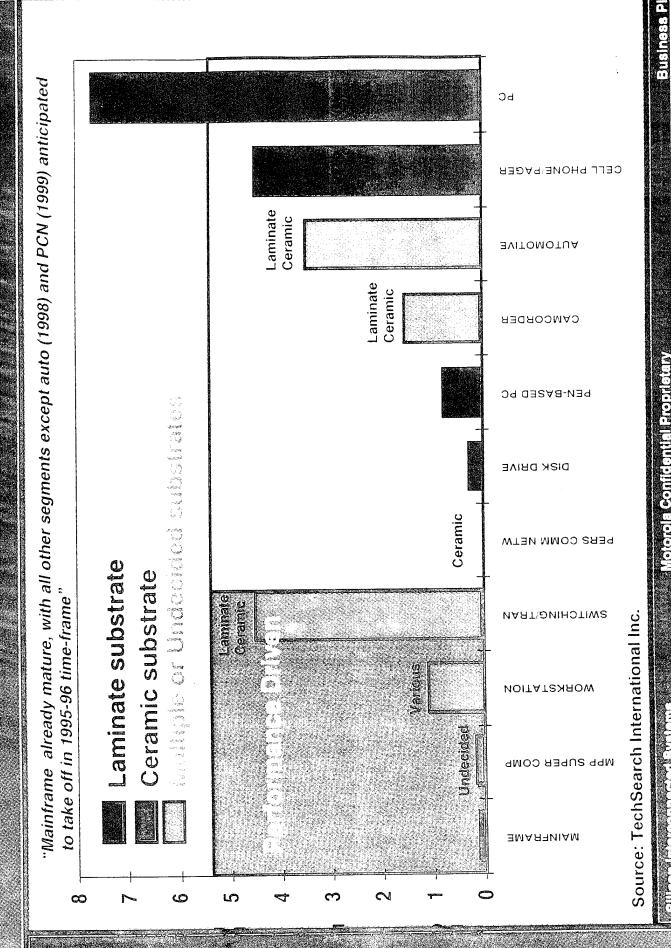
Substrate Usage

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Subsegment	Market Characteristics	Competition	1997 2000	2000	Customers
Mainframe	<ul><li>Declining market</li><li>Controlled by Captives</li></ul>	• Captives	90K	70K	• None
Supercomputer	<ul><li>Performance driven</li><li>Controlled by Captives</li></ul>	• Captives	M1.	1.3M	• Cray • Unisys
Workstation	<ul> <li>Moderate growth market</li> <li>Performance driven</li> <li>Usage at &gt;100MHz</li> <li>Multicavailty ceramics</li> </ul>	• IBM, Toshiba in-house mfg.	1.0M	2.7M	• Sun • Silicon Graphics • MCG
PC	<ul> <li>Micro/Memory/ASIC performance driven</li> <li>Laptop size constraints</li> <li>20%+ usage of SISs</li> </ul>	<ul> <li>IBM/MMS</li> <li>Contract houses</li> </ul>	8f/J	19M	• Apple • IBM • Dell • Compaq
Pen-based PCs/PDAs	<ul> <li>Size/Density</li> <li>Cost Sensitive</li> <li>10% usage of SISs</li> <li>DCA will dominate</li> </ul>	• IBM/MMS • Captives • Contract houses	.8M	1.8M	<ul><li>Apple</li><li>MIMs</li><li>Comedge</li><li>Proteq</li></ul>
Hard Disk Drives	<ul> <li>1.3"/1.8" drives only</li> <li>Will move to DCA &lt;1.3</li> <li>Cost Sensitive &lt; 5% usage</li> </ul>	<i>.</i> .	.5M	1.6M	• Seagate • Conner
Peripherals	• Scanners?	· ;	c·	ż	<ul> <li>Spectra Physics</li> </ul>
PC cards	<ul> <li>Driven by size, upgrade path to memory &amp; comm.</li> <li>Wide variety of applic.</li> </ul>	• IBM • Toshiba • Intel • Sundisk • 3COM• Epson	32M	88M	• Sega • Sci ATL • Sony • Canon • Gl



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Forecasts vary widely, partially due to definitions.

Dataquest- Yr 2000 \$32B (\$21B semiconductor content)

Toshiba estimates market @ \$32B in 2000

ICE- Yr 2000 \$2.2B (excludes semiconductor content)

In-Stat- Yr 1998 \$247M (excludes semiconductor content)

TechSearch International Inc. - 81 million modules by 2002

the most thorough analysis of the market and is the basis for TechSearch International study, although in units, provides most of the segment/application information.

TechSearch, e.g., Multimedia, and PC cards to fully define the We have added some missing applications from the scope of the market.

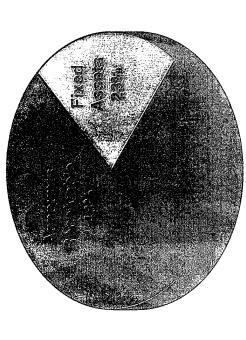
## Market Overview

- SIS Market has been limited to low volume performance driven applications where cost is not a major driver, e.g., Millitary, Mainframe and Medical.
- Major barriers to faster growth have been the availability of low cost substrates, and volume suppliers of known good die.
- Volume drivers are now emerging:
- high end PCs, and size considerations for laptops and pen-based PC. . .driven by performance requirements in workstations and systems including PDAs.
- Communications... Size for line cards, broadband performance requirements, Cellular performance requirements (DSP).
- Automotive... Size and reliability driven ... applications include: injection, ignition and throttle controls; and powertrain controllers.

- Set up 50-50 Joint venture . . . Decide on Board Members, Select operations manager and team.
- Support Motorola equipment business opportunities.
- Aggressively pursue IBM and Spectra Physics opportunities to drive volume and attain critical mass.
- Selectively pursue new business in areas of strength, e.g., communications (RF and DSP).
- Purchase additional capital equipment approx. \$4M.



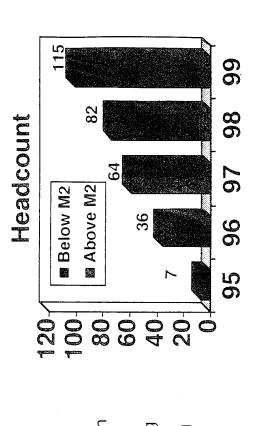
Capital Investment

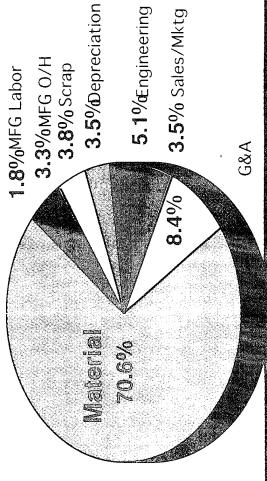


**Business Cost Makeup** 

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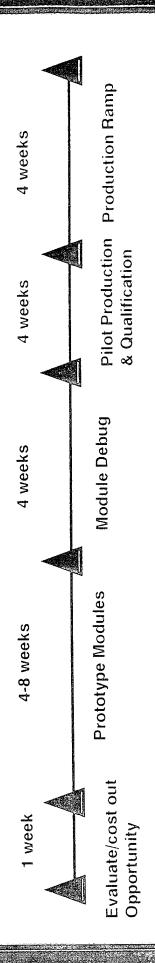
- High Asset turnover business
- \$175M of sales per year from a 4000 square foot manufacturing area with \$18M of equipment.
- Inventory turns run 8 to 10.
- RONA asset turns of 4.5 expected at reasonable volumes.
- Not a labor intensive business Mfg labor costs runs 1% of sales . . no impetus to move offshore.
- Major cost is material 60 to 65% of sales.
- Financials similar to DRAMs . . . low mfg. margin 25% to 30%, 7% G&A, 3% each for engineering and sales/marketing.
- P&L assumes die pricing from SPS at preferred customer prices... no bargain prices.

# Joint Venture Evolution

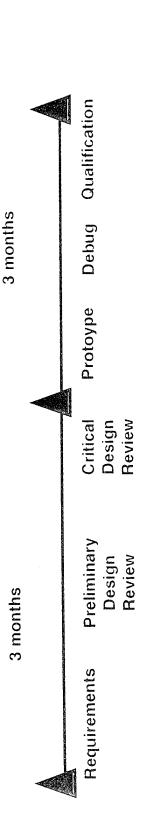
	Phase 1 0-\$40M	Phase 2 \$40M-\$80M	Phase 3 \$80M-\$120M	Phase 4 \$120M
Type of Business	• Joint Venture	• Joint Venture	• Joint Venture	• Motorola Operation
Segment Participation	• Motorola • Communications	• Add PDAs/PICs	• Add PC and Automotive	• Full participation (where feasible)
Customer base	• Motorola + 1 key customer	• add 2-3 more customers	• add 2-3 more customers	
JV Engineering Scope	• Limited Development • 2 full-time Engineers	• add 6-10 Engineers	• add 6-10 Engineers	• 3% of sales
JV owned functions	• Operations Mgmt • Marketing • Purchasing		• R&D • Manufacturing	
Manufacturing	·GSTG	·GSTG	• Offsite?	· Offsite?
Capital Requirements	• Mfg, limited CAD	• Full MFG & CAD • \$7M	• \$3M capital	• \$5M capital
Financials	• Proforma P&L • Simplified RONA	• Separate financials		
RONA Expectation	• Breakeven at \$23M Sales	• 15%	. 20%+	. 20%+

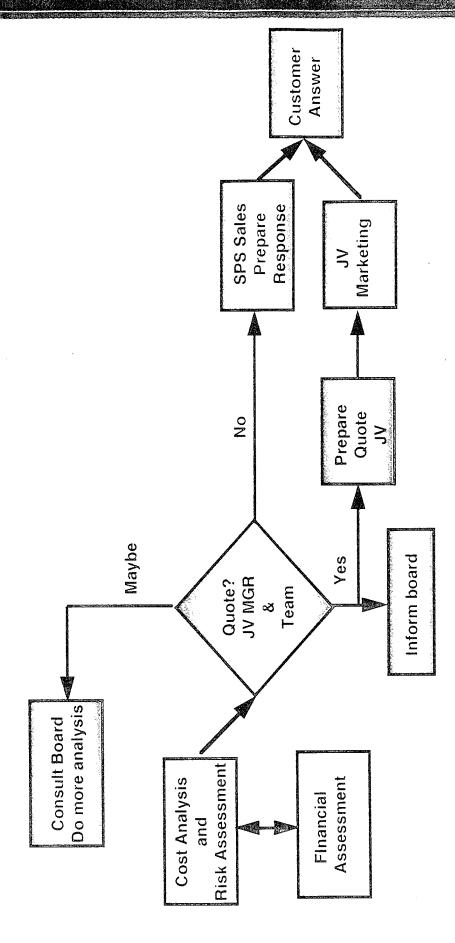
- Treat as an experiment in nontraditional (cheap) program management.
- Enter the business "Cheapest Way Possible"
- JV initially has 6-10 employees . . . 1995 start-up expense=
- Contract for manufacturing, additional engineering services.
  - Pay "fees" for distribution, finance, sales, personnel.
- Fund additional equipment for mfg, engineering ... \$4.2M.
- Be selective on opportunities . . . satisfy Motorola, make money.
- Earn the right for additional investment
- Add organizational structure as it becomes cost efficient, e.g., manufacturing, additional engineering.

### Chip & Wire



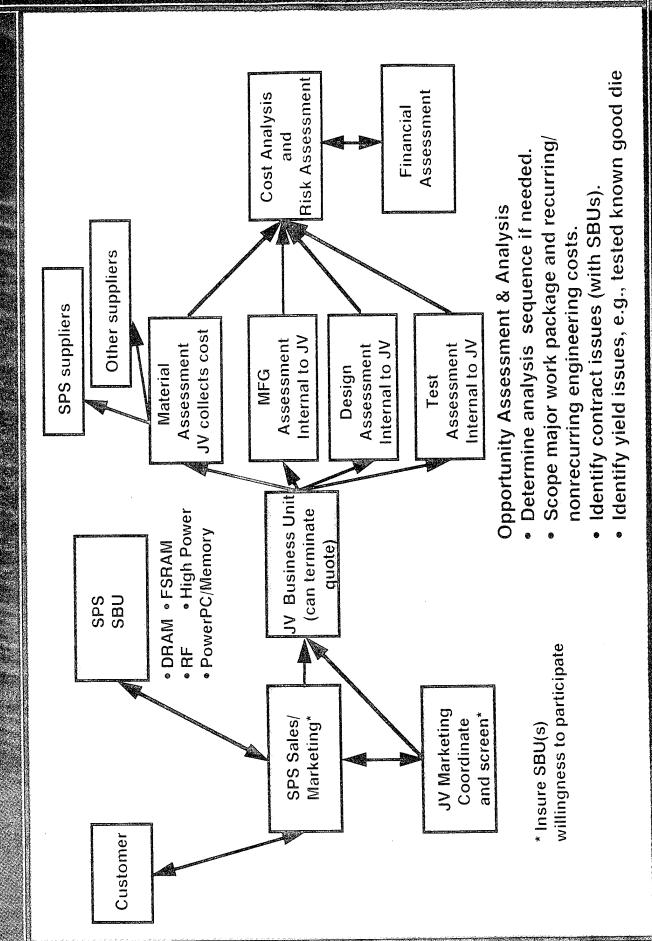
## **Engineering Design**





Decision & Prepare Quote

- Review Assessment, e.g., within guidelines application, customer, financials
  - Identify terms and conditions
- Identify assumptions
- Identify SPS B.U. contract book



# Strategic Priorities

	Module Semi Content	Competencies/ Technology	Markets/ Applications	Customers	<b>Target</b> <b>RONA</b>	Target Share of Business
Strategically Critical Required for	- RF - Custom (Mot) - MCU Cores - DSP - ACP	-Tested good die - RF - Flip chip - Low cost substrates - Low Cost Mfg	- Communications (portable products) - PDAs/PICs - PCNs	Motorola - LMPS - Cellular - MIMS - AECG - MCG	15%, +	65%.
Top Priority  SPS Key Customer High SPS/ Engineering Content High Volume/Growth	- PowerPCIM - Hi Pert - CMOS GA - Custom - FSRAMS (CMOS & Bipolar) - Sensors - SmartMOS <sup>FM</sup>	- Test Technology - Known good die - Rapid Prototyping capability	- Computing (PC) - Auto - Communications (merchant market) - Multimedia	- Apple - Ford - Bosch - NT - AT&T - GM - IBM - HP - Chrysler - Sci Ati	20%	15 <sup>0;0</sup>
Cash Generators Good SPS/Eng		- Low Cost Mfg	- Consumer - Workstations - Build to Print - PC Cards	- Mot-ISG - Sony - Matsushita - Philips - Canon - Toshiba - Small Customers?	25%	"spuedep
Only Do with Help Limited opportunity Missing Competency		- Thin films	- Supercomputer - Disk Drive	- Cray - Unisys - Conner - Seagate	25%	"th"
Exit or Don't Do Low Volume Low SPS Content	- Hybrid Modules - Mil Spec - Equip group FGs - IPAs - SBU existing Pkgs		- Miltary - Distribution - Maintrames - Medical			ο;άΟ

Note: No interdependencies across columns

= change

## SPS Provides

GSTG Provides

Legal/Contracts Engineering Distribution Finance Sales

### Limited Engineering Operations Manager Purchasing Marketing Interface MFG Coordination Customer Service JV Provides

**Board of Directors** 

- •2 SPS
- 2 GSTG 2 Others

### SPS Gets:

- Higher share at key customers
- Differentiation from competitors
- Partner with complementary competencies

### Motorola Gets:

- expertises for system solution Merging of communications
- In-house solution for equipment business needs

### Known quality/volume suppliers Complete solution from

one supplier

Venture

5

Customer Gets:

### GSTG Gets:

- High growth/RONA opportunity
  - Partner with complementary

competencies

## Why We are Here

- Customers' have increasing performance requirements needing to be condensed into smaller spaces and are asking for MCMs.
- Customers want to define their system(s) and pass these requirements to a limited set of suppliers.
- Customers expect suppliers to act as a responsible party to provide integrated solutions.
- Motorola equipment businesses are examples of the above.
- Motorola and other SPS key customers need a capability to meet these demands.
- We are offering a solution via a GSTG-SPS joint venture.

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  - 1.1 Design Kit Contents
  - 1.2 Scope
  - 1.3 A Note about "TBD's"
- 2.0 Multichip Module Definitions
  - 2.1 Application Specific Integrated Circuit (ASIC)
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  - 2.4 Multichip Module Microcircuit (MCM)
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Appendix A. CADENCE CAE TECHNOLOGY FILES

Appendix B. MENTOR CAE TECHNOLOGY FILES

Appendix C. CADENCE PHYSICAL SYMBOL REFERENCE

Appendix D. CADENCE STANDARD LOGIC SYMBOL REFERENCE

Appendix E. MCM DESIGN PREPARATION CHECKLIST

### 1.0 Introduction

### 1.1 Design Kit Contents

The Motorola Multichip Module Systems (MCM/S<sup>TM</sup>) Design Kit exists as a master point of reference for MCM design personnel who plan to utilize MCM/S<sup>TM</sup> to fabricate and test multichip modules. The kit is organized into sections relating to general MCM technology, Materials and Components, Design Considerations, Assembly Processes, Layout Rules, Documentation, CAE/CAD/CAM Interface Specifications, and appendices for CAE Design Kit/Technology File availability and Design Checklists. The MCM/S<sup>TM</sup> Design Kit is a living document which is continually updated as CAE tools, product offerings, process constraints, and design guidelines change with advances in technology. Before embarking on any new design efforts, contact Motorola MCM/S<sup>TM</sup> for the latest edition of this document.

### 1.2 Scope

This specification covers design guidelines for ceramic multichip modules (MCM-C) and ruggedized laminated multichip modules (MCM-L) in compliance with the requirements of Motorola Multichip Module Systems (MCM/S<sup>TM</sup>) producibility standards.

### 1.3 A Note about "TBD's"

At the time this document was printed, some information from suppliers was not yet available. The missing information does not affect the current product offerings of the MCM/S<sup>TM</sup> foundry but reflects future product information. The information that is "To Be Determined" (TBD) will be annotated with a TBD\* place holder mark, indicating that the text will be populated in a future edition of this manual.

### 2.0 Multichip Module Definitions

### 2.1 Application Specific Integrated Circuit (ASIC)

ASIC represents a semiconductor device intended to satisfy a unique complete circuit function.

### 2.2 Application Specific Electronic Assembly (ASEA)

ASEA represents printed board assemblies consisting of electronic components attached to an interconnecting substrate, intended to perform a complete circuit function.

### 2.3 Application Specific Electronic Module (ASEM)

ASEM represents a grouping of components intended as a subassembly or super-part that will be interconnected to an ASEA.

### 2.4 Multichip Module Microcircuit (MCM)

An MCM is an ASEM intended as a super-part or subassembly that will be mounted on an interconnectiong structure or substrate.

### 2.4.1 Ceramic Multichip Module (MCM-C)

### 2.4.1.1 Thick-film Multilayer (TFM)

TFM refers to the technology and the associated conductive and passive circuit elements that are made by a screen print process. TFM technology includes ceramic substrates, typically alumina, with a top circuit pattern housing conductive and passive circuit elements of thick-film technology. In TFM the top layer usually contains all device I/O bonding sites and the substrate I/O lands. However, it is possible through use of dielectric tiers to interconnect to multiple levels within the substrate structure and embed thick-film components such as resistors and capacitors on internal layers. The processed substrate is subsequently placed into higher level packaging.

### 2.4.1.2 High Temperature Cofired Ceramic (HTCC)

HTCC refers to the technology in which unfired ceramic and unfired refractory metals are laminated and subsequently cofired, producing a substrate which can support various types of component interconnection as well as high-temperature brazing processes. HTCC is fired between 1200 and 1800 degrees Celsius and Nickel and Gold are subsequently plated on the top and bottom metallized surfaces. In HTCC it is possible through use of vias and cavities to define sites for wire bonding or component attachment on any layer. HTCC technology supports the inclusion of cavities, various styles of lead frames, and ceramic or metal sidewalls to create hermetic enclosures.

### 2.4.2 Laminate Multichip Module (MCM-L)

MCM-L's utilize reinforced, laminated, organic dielectric in a multilayer construction. The conductive pattern is usually copper etched technology which refers to conductive patterns that are etched from a metal foil clad dielectric. MCM-L's incorporate chip on board (COB), flipchip, and various technologies for component attachment.

### 3.0 Materials

### 3.1 Substrate Materials

### 3.1.1 Alumina Substrates

Alumina substrates are made of polycrystalline Al<sub>2</sub>O<sub>3</sub> with small amounts of metal oxide glasses to achieve certain physical properties. Alumina is the most popular substrate material because of its good mechanical strength, good electrical insulative properties, resistance to corrosion and oxidation, stability at high temperatures, ability to be metallized, and availability. Refer to Section 6 Table 6.3.A for ceramic substrate properties.

### 3.1.2 Aluminum Nitride Substrates

Aluminum nitride is a highly thermally conductive substrate. Refer to Section 6, Table 6.3.A for ceramic substrate properties.

### 3.1.3 Polymer Substrates

A variety of polymer based materials are available for use as substrates for hybrids and MCM's. These materials support reflow solder or conductive epoxy attachment methods. Refer to Section 6, Table 6.5.A for polymer substrate properties.

### 3.2 Conductive Materials

3.2.1 Many types of thick-film materials are available for various applications. Refer to Section 6, Table 6.3.B for some common thick-film conductive materials and their characteristics.

### 3.3 Resistive Materials

### 3.3.1 Thick-Film Resistive Materials

Ceramic thick-film resistors have sheet resistivities in the range 10 ohms to 10 megaohms. Resistivity is controlled by varying the metal-to-glass content. Firing temperatures are typically 750-900 degrees Celsius. To achieve precise resistance values, the resistors are adjusted or trimmed to value to tolerances as low as +/- .5 %. Consult MCM/S<sup>TM</sup> for available resistor materials and fields.

### 3.4 Thick-film Dielectric Materials

The most widely used thick film dielectrics are overglazes, multilayer dielectrics, and capacitor dielectrics. The overglaze is a low-melting temperature vitreous glass material. It is generally used as a resistor overcoat to passivate thick-film resistors. It can also be used as a conductor insulator and solder barrier. A multilayer dielectric is a mixture of ceramic and devitrifying glasses. It is used as an insulating barrier between conductor crossover layers and between multilayer conductors. Capacitor dielectric is a high K material used to create thick-film capacitors. Refer to Section 6, Table 6.3.C for typical thick-film dielectric materials and their characteristics

### 3.5 Adhesives

A variety of organic adhesives are used to attach substrates to packages, devices to substrates, and lids to packages. A temperature hierarchy must be established with respect to the serial attachment of substrates, devices, and package lids. The properties important in the selection of an adhesive are the cure temperature, outgassing properties, ionic contaminants, creep, bond strength, thermal stability, thermal conductivity, flexibility, solvent resistance, corrosivity and volume electrical resistivity. Military applications require compliance to MIL-STD-883D, Method 5011, Evaluation and Acceptance Procedures for Polymeric Adhesives.

### 3.6 Bonding Wires

Gold and Aluminum are the preferred materials for wire bonding. Gold wires are typically alloyed with small amounts of beryllium or copper to control grain growth during bonding. Aluminum wires are typically alloyed with approximately 1 % silicon.

### 4.0 MCM Design Considerations

### 4.1 Substrate Features

### 4.1.1 Substrate Camber

Substrate camber (degree of planarization) is equivalent to bow and twist for a printed wiring board (PWB). Excessive camber can be detrimental to many assembly and seal processes, thus minimization of camber should be a design goal. Proper balancing of dielectric and conductive layers is essential to minimizing camber.

### 4.1.2 Conductors

### 4.1.2.1 Conductor Width and Thickness

Conductor width and thickness should be determined by the current carrying capacity required and the maximum permissible temperature rise in the conductive material. Conductor width and thickness should also be specified with respect to producibility (wider widths are preferred, while maintaining proper conductor spacing). For military applications, MIL-H-38534A, establishes maximum allowable current density.

### 4.1.2.2 Conductor Length

To maximize performance and producibility, conductor lengths should be made as short as possible. For thick-film conductors consider the minimum conductor length based on the producibility of the thick-film screen print process. Also, take into consideration the higher resistance of thick-film conductors. Refer to Section 6, Table 6.3.B.

### 4.1.2.3 Conductor Spacing

Conductor spacing should be made with knowledge of voltage differences in adjacent conductors and the properties (i.e., dielectric strength) of the dielectric material. Spacing should be maximized when possible to improve the producibility of the process. Conductor spacing is critical with respect to corona. Corona is the flow of small erratic current pulses resulting from discharges in voids in a dielectric during voltage stress. Corona occurs at high voltages with relatively small conductor spacing. Designers should refer to the dielectric strength of the substrate material (see Table 6.3.A and Figure 6.3.C) when spacings are small (typically 1 mil or less) and voltages are large (greater than 100 Volts).

### 4.1.2.4 Power and Ground Planes

Planes that span a majority of the substrate area should be located symmetrically about the thickness of the substrate. Each design must consider the metal distribution and location of planes in the substrate cross-section. Diagonal or orthogonal lattices are often required to assist in layer to laver metal distribution.

### 4.1.2.5 Layer Structure

The recommended maximum number of conductive layers is (8) for MCM-L technology, (9) for TFM substrates. HTCC can support in excess of (30) layers. The order of layers should be arranged to minimize asymmetry of the metallization on the substrate.

### 4.1.3 Pads

Pads are conductive contact surfaces used to interconnect the substrate with discrete micro devices and the substrate with the package. Pads can also be used for test probes and resistor trimming. Pads must be designed to accommodate the preferred technology.

### 4.1.3.1 Wire Bond Pads

The materials used on surface layers of an MCM vary based on the type of wire bonding. In TFM, noble metals, usually a Gold alloy, are used. HTCC uses refractory metals, thereby, requiring deposition of a Nickel/Gold plating to support wire bonding. MCM-L bond sites also require the application of Nickel/Gold plating to support wire bonding.

### 4.1.3.2 Component Pads

Component pads are used for reflow soldering or adhesive attachment of discrete devices to the substrate.

### 4.1.3.3 Test Pads

In order to facilitate testing and troubleshooting, the substrate should be designed such that there is 100% physical nodal access. However, this is often unobtainable due to mechanical or electrical performance limitations. Given these constraints, a determination of the quantity and location of test points must be a joint decision between the personnel involved with design, layout, and test of the MCM. Test points can take the form of unused inputs/outputs (I/O) or unobscured test pads on the surface of the substrate. Information on the layout requirements for test pads is given in section 6.7.2.

### 4.1.3.4 Probe Pads

Probe pads are required for taking measurements during thick-film resistor trimming. 4.1.4 Vias

Vias are used to interconnect signals on different layers in a multilayer structure. Thermal vias can be utilized to conduct excessive heat generated by components away from localized areas within the module/substrate.

### 4.2 Package Features

The predominant packaging configuration is surface mount solder attach using conventional solder paste print and reflow. It is recommended to first review standard packages before proceeding with a custom package design. Standard packages should be used whenever possible in order to minimize tooling costs associated with custom package design. The interconnection circuitry may be on a separate substrate or as in HTCC it may be an integral part of the package base. Custom MCM packages are diverse in form and application. Their design requires consideration of numerous technical issues. To ensure design suitability with the MCM/S<sup>TM</sup> foundry, it is recommended that customers consult with MCM/S<sup>TM</sup> early in the design conceptualization. General considerations for the package are contained in the following paragraphs.

### 4.2.1 Package Body

The package should be compatible with the manufacturing processes, desired real estate, heat transfer requirements (i.e., thermal conductivity), mechanical requirements, and the environmental requirements. Because of their superior properties, ceramic and kovar material are recommended for package construction.

### 4.2.2 Lead Type

Lead type depends on the package type and the anticipated manufacturing method. The "gull wing" is the recommended lead form for surface mount packages. The lead finish should be compatible with both substrate pad attach and package to PWB attach. Leads should be constrained prior to attach to keep them properly spaced and planar. Non-conductive tie-bars are available to support electrical test prior to lead forming. It is also beneficial if the package hold down provides self-alignment of leads and circuit board pads.

### 4.2.3 Lead Feed-Throughs

Lead feed-throughs refer to the method of passing the leads from the interior of the package to the outside of the package on metal sidewall packages. The selected type of feed-though depends on the package material and the lead type. Glass to metal (compression) seals are the preferred feed-through style for metal packages. (The minimum distance between the glass to metal seals and the package sealing surface for seam welded packages after final seal shall be .040in.) Ceramic brazed feed-throughs are also excellent for high-reliability applications.

### 4.2.4 Package Seal

The package must provide a hermetic seal to prevent corrosion of the internal circuit elements. The package seal integrity depends on the lid seal, the lead feed-throughs, and the package and seal materials. In hermetic applications, the lid seal is the critical element. Hermetic seals are possible with metal, ceramic, or glass package and seal material. Polymers (i.e., epoxy) do not provide a hermetic seal.

The preferred lid seal techniques for MCM's are conventional seam welding and laser welding techniques. Also, a metal lid with a seal ring permits well-established precision machining techniques to be used for lid removal. The lid and seal ring should be designed to accommodate either braze or solder sealing methods for metal packages.

### 4.2.5 Non Hermetic Seal

Non hermetic seals provide a degree of protection from corrosion and are used with MCM-L and some ceramic applications. Non hermetic seals are achieved by using B-stage epoxies or thermoplastic materials to attach a lid or cover to a substrate or by surface coating the chips on the laminate substrate with an encapsulant material. A silicon die coat material is usually used in conjunction with non hermetic seals. The silicon die coat slows the rate of moisture/corrosion penetration.

### 4.3 Design for Testability

### 4.3.1 Test Strategy Concepts

Testability must be considered at the inception of an MCM design, since techniques such as boundary scan and Built-In-Self-Test (BIST) may require additional circuitry or may influence the selection of parts. Each MCM design must be examined to determine the optimum test approach necessary to assure a functional, reliable product. Despite differences, however, certain considerations will enhance the testability of any design. These are the fundamental concepts of testability, which are based on the classic principals of Initialization, Visibility, Controllability, and Partitioning.

### 4.3.1.1 Initialization

Initialization is defined as the act of placing each sequential state machine to a known logic state. This capability is required to provide a predictable starting point for the test system. The lack of this capability imposes significant penalties in the areas of test software development, diagnostic accuracy, and increased test times.

### 4.3.2.2 Visibility

Visibility is the ability to view circuit nodes of the assembly during the test process. The implementation of test visibility points is extremely important for functional test approaches. The benefits associated with proper visibility techniques are that the operation of each device may be individually observed and diagnostics to the component level is achieved. The lack of this capability will result in increased test software development costs, inaccurate diagnostics, and longer test times.

### 4.3.2.3 Controllability

Controllability is the capability to override the normal function of the assembly. Utilization of this feature is the basis for in-circuit analog and digital test techniques. The benefits associated with implementation of this concept are that the test set can direct the operation of the unit under test (UUT) and that test set synchronization may easily be established. The inability to control the UUT will result in inaccurate diagnostics, increased test software development time, and longer test times.

### 4.3.2.4 Partitioning

Partitioning is the electrical or physical division of the UUT into a number of easily testable smaller functional blocks. This feature provides the benefit of allowing structured test programs that are designed to exercise these blocks of circuitry. Partitioning has an additional benefit in the case where total physical nodal access is not achievable. In this instance the circuit topology may be divided into functional circuit blocks and then electrically accessed on the peripheral I/O pins, or with boundary scan cells. This minimizes the number of probes, however the test software task is significantly increased and the achievable diagnostic accuracy is reduced. Partitioning is more appropriately considered an effective technique that the test programmer may utilize if all previously addressed testability concepts have been implemented.

### 4.3.2 Test Guidelines

These common test guidelines apply to all MCM designs, regardless of physical implementation (i.e. test points, boundary scan cells, etc.):

1. Isolate all Reset, Set, Clear, POR lines from ground or VCC by a unique pulldown or pullup resistor.

NOTE: Ensure that pulldown or pullup resistors are less the 10K. The exact value will depend on the logic family used.

- 2. Isolate timing capacitors associated with microprocessor Reset lines from the Reset pin with a series resistor.
- 3. Provide access to critical nodes via unused I/O, test pads, or boundary scan cells.
- 4. Isolate all <u>unused</u> control, output enable, Chip Select (CS), Chip Enable (CE) Tri-state, Mode lines, etc., from ground.
- 5. Allow on-board oscillators to be inhibited with a digital input to allow external oscillator injection.
- 6. Allow nodal access to no-connect pins on complex IC's.
- 7. Where possible, isolate analog circuitry such as Codecs, A/D converters, active filters, etc. from their electrical environment by the use of digitally controlled analog switches, or other digitally controlled circuitry.
- 8. Use IC's with tri-state outputs to allow circuit isolation. Also, provide access to the tri-state control pin via unused I/O, test pads, or boundary scan cells.
- 9. Obtain all simulation vectors in a format compatible with the tester (see section 10.4).
- 10. Obtain files of all PLD JEDEC design equations used in the design.

### 4.3.3 Circuit Accessibility Techniques

The following techniques may be used to achieve the circuit accessibility required by the guidelines in the previous section.

### 4.3.3.1 Test Points

The most effective way to enhance testability is through the addition of test points to the MCM to allow physical nodal access. This can be accomplished by using dedicated probe pads on the substrate surface (described in section 6.7.2), of through the use of unallocated Inputs and Output (I/O). However, the addition of physical access is often constrained by mechanical and electrical considerations. Two additional in-situ test techniques can be used to improve circuit observability without the addition of physical test points. These techniques, Boundary Scan and Built-In-Self-Test (BIST) are described in the following sections. As with all testability techniques, implementation of these approaches must be considered on a design-by-design basis.

### 4.3.3.2 IEEE 1149.1 / JTAG / Boundary Scan

Boundary scan is a relatively new embedded testability technique that is primarily directed towards resolving test probe access issues associated with high density assemblies. The IEEE 1149.1 standard was adopted in February, 1990 and is rapidly gaining the support of major

corporations. The basic premise of this approach is a method whereby test instructions and stimulus patterns are serially loaded into an assembly. This is complemented by the capability to serially read out the results of the test execution.

The IEEE standard serial interface is composed of four signal lines, Test Data In, (TDI), Test Data Out (TDO), Test Clock (TCK), and Test Mode Select (TMS). The primary use for boundary scan is for detecting and accurately diagnosing opens and shorts that occur during the manufacturing process. Additional features of boundary scan include the capability to apply test stimulus to individual devices, initiate and monitor Built-In-Self-Test (BIST), improve MCM fault coverage by providing visibility/control capabilities, and to perform software debug using on-chip emulation features. The incorporation of boundary scan provides benefits in significant test program development cost reductions, overall quality improvement, minimization of time to market, and overall product cost reduction. Implementation of this technique involves using boundary scan parts in the design which comply with the IEEE standard. Several manufacturers now offer standard offerings of boundary scan parts. Additionally, the IEEE specification offers guidelines for the incorporation of boundary scan into proprietary devices such as ASIC's.

The following guidelines should be considered when implementing boundary scan into an MCM design:

- 1. Utilize commercial components with JTAG 1149.1 capability.
- 2. Incorporate JTAG 1149.1 capability into custom ASIC/PLD designs.
- 3. If required, implement JTAG 1149.1 capability in the microprocessor for software emulation.

### 4.3.3.3 Built-In-Self-Test (BIST)

Built-In-Self-Test (BIST) is one of the most effective techniques available to minimize expenses associated with developing test capability for new products. It utilizes resources on the MCM, such as microprocessors and memory, to perform at speed testing of components on the MCM. Typically, special BIST software is loaded into onboard memory, and replaced with deliverable product software prior to shipment. This approach is effective at the MCM, subassembly and system test levels. Additionally BIST is an excellent complement to boundary scan testing techniques. BIST is a verification of the system functionality and must be customized for the product itself; however representative contents of the BIST test philosophy may be characterized as follows:

- 1. Memory Checksum tests
- 2. Ram R/W tests
- 3. Loopback I/O tests
- 4. Display tests
- 5. Keyboard Interaction tests
- 6. System Status tests
- 7. High Resolution Internal Error Logging
- 8. BIST Continuous test capability
- 9. Capability to initiate and monitor BIST results

The most common problem confronted when considering the implementation of BIST capability is memory capacity. Fortunately with new technologies such as Flash memory this issue can be eliminated. In the case of Flash memory, the entire memory may be utilized for test software during the manufacturing test flow and then easily reloaded with the operational software prior to delivery to the customer. Regardless of the method utilized to provide sufficient memory capacity for BIST, the inherent benefits achieved include a significant reduction in test development costs, reduced field product support costs, and a major reduction in time to market for the product.

The following guidelines should be considered when implementing BIST into an MCM design:

- 1. Allow external initiation and monitoring of Built-In-Self-Test (BIST) status via external I/O or boundary scan.
- 2. Use BIST to test the functionality of the System via loopback and/or monitoring internal status signals.
- 3. Perform the BIST sequence Power up.
- 4. Incorporate a loop test function in BIST for ESS/Burn-in testing and provide nonvolatile error logging capability.
- 5. Allocate memory space been allocated for BIST firmware on the MCM using on-board Flash memory, RAM, etc.

### 5.0 Assembly Processes

### 5.1 Wire Bonding

### 5.1.1 Wire Bonding Methods

The MCM/S<sup>™</sup> foundry supports (2) types of wirebonding: ultrasonic, and thermosonic. A comparison of the two methods is shown in Table 5.1.A

Table 5.1.A
Bonding Method Comparison

	AUTOMATIC	ULTRASONIC
	THERMOSONIC	(GOLD AND ALUMINUM
PARAMETER	(GOLD WIRE)	WIRE)
DEVELOP AND CONTROL	EASIEST TO CONTROL	MUST CONTROL
	1	ACOUSTICAL ENERGY AND
		FORCE
SPEED	ABOUT 170 WIRES/MIN	ABOUT 240 WIRES/MIN
CURRENT CAPACITY	ABOUT 0.55 AMPS	<0.40 AMPS
(.001IN) (WIRE ≤ .040 IN)		
HEAT REQUIRED	150°C WORK STAGE	NO HEAT REQUIRED ( FOR
	·	TYPICAL ALUMINUM WIRE)
ACOUSTIC ENERGY	CONTROLLABLE	CONTROLLABLE
PEQUIRED		
FDAUS REQUIRED	LESS THAN ULTRASONIC &	LESS THAN
	THERMOCOMPRESSION	THERMOCOMPRESSION
DIRECTION	OMNI-DIRECTIONAL (360°)	STRAIGHT LINE BOND
		±7.5° OFF TRUE LINE
LOOPING	BEST CONTROL (MACHINE	GOOD CONTROL
	CONTROLLABLE)	(MACHINE
		CONTROLLABLE)
PAD SIZE (.001IN DIA.)	BALL SIZE DEPENDENT	WEDGE SIZE DEPENDENT
	WEDGE SIZE = 1.5X TO 5X	WIDTH = 1.2X TO 2.5X WIRE
	WIRE DIAMETER IN	DIAMETER AND LENGTH =
	LENGTH AND 1.5X TO 3X	1.5X TO 5X WIRE
2012 1512 6: 5: 5:	WIRE DIAMETER IN WIDTH	DIAMETER
BOND HEAD CLEARANCE	SMALLEST HEAD SIZE	LARGE HEAD SIZE
CENCITI #T/ TO	MIN CLEAR REQUIRED	DEEP ACCESS AVAILABLE
SENSITIVITY TO	LESS	LEAST
CONTAMINATION PURPLE PLAGUE	10.005.405.	
FUNFLE PLAGUE	INCREASES WITH	INCREASES WITH
	REDUCED HERMETICITY	REDUCED HERMETICITY
	AND INCREASED	AND INCREASED
	TEMPERATURE	TEMPERATURE

### 5.1.1.1 Ultrasonic/Thermosonic Bonding

This technique uses ultrasonic energy to weld wire to the chip pad and circuit land. The process is performed at room temperature. Aluminum and gold wire is used almost exclusively. Aluminum wire is stronger than gold and is less likely to sag at elevated temperatures. The advantages of ultrasonic bonding include: low working temperatures and it is more workable with smaller lands than thermosonic. Some disadvantages are: it is unidirectional, and the component or package-wall proximity must allow for bonding tool and wire-clamp clearances.

### 5.1.1.2 Thermosonic Ball Bonding

Thermosonic bonding is a combination of thermocompression and ultrasonic bonding. Gold wire ball-and-stitch bonds are made with a capillary that is driven by a burst of ultrasonic power at the second bond to augment metal bonding. The process uses moderate temperatures and may be successful in attaching wires to "hard to bond" MCM substrate metallizations. The advantages of this process include: moderate bond temperature, omni-directional (Gold ball), and it is less sensitive to contamination than thermocompression. Some disadvantages are: minimum bond pad size of .004in x .004in, the requirement that acoustic energy be controlled, and the need for special fixturing.

### 5.2 Component Attachment Methods

Component attachment methods refers to the attaching of unpackaged semiconductor dice or chip components to the substrate. Curing and brazing temperatures are very important to the reliability of adjacent components and previously made bonds. There are five principle die/component to-substrate attachment methods:

### 5.2.1 Thermoplastic Film Adhesives

Thermoplastics (heat activated) can be stored at room temperature for more than a year. A disadvantage of thermoplastics is their propensity to heat unevenly and melt in a non uniform manner, making it difficult to obtain a planar surface. Thermoplastics are available in low or high temperature versions. Advantages include ease of repair, storage at room temperature, snap cure, and little or no out-gassing. Thermoplastic paste can also be screen printed.

### 5.2.2 Epoxy

Epoxy (with or without silver filling) is available in both low and high temperature. Cure cycles of 1 to 2 hours and voids of 5 to 8 % of the die area are typical. The advantages include ease of processing, ease of handling, ease of repair, high yield, ruggedness and low temperature curing (<150°C). In the case of organic substrates, epoxy can often be applied to the substrate using the same screen printing equipment used to create the substrate. Disadvantages include outgassing, lengthy cure cycles (hours), limited shelf life (6 to 8 months), and the need to store under refrigeration. Also, rework may require significant force to remove die. Silver-filled epoxy is easy to work with, can be applied with automation and is a good conductor of heat and electricity. A good conductive or non-conductive epoxy should have a Tg > 100° C, less than 1 % total outgassed material, and less than 1 % total condensable materials during/after cure.

5.2.3 Silver filled glass - TBD\*.

### 5.2.4 Gold/Silicon eutectic

This method uses a bonding temperature of 380°C and has excellent thermal conductivity making it excellent for high power/dense layouts, however, it is costly.

### 5.2.5 Gold/Germanium eutectic

This method uses a bonding temperature of 360°C and is used to enhance the bonding of the chips to gold plated surfaces especially when the chips are not Gold backed

### 5.2.6 Solder Attachment

Reflow solder attachment refers to the process of placing solder paste or preforms at the sight of the joint and applying heat by means of hot vapor, infrared radiation, plasma energy, or laser beam until the solder becomes liquid. Solder attachment of IC chips is performed with AuSn 80/20 solder. This solder is used for GaAs devices particularly and is at the border between hard solders such as Gold/ Silicon and the Tin Lead families.

### 5.3 Adhesive Deposition Methods

### 5.3.1 Screen printing

In this method the adhesive compound is applied utilizing screen printing processes. It is good for high volume production, and maintains good control over the thickness and structure of the adhesive. Time to apply is typically 5-10 seconds for a single substrate.

### 5.3.2 Liquid and/or paste dispensing

In this method the adhesive is extruded through a needle or multi-point dispensing tool to the substrate by either positive displacement or pneumatic control. Typical dispensing times are 1 to 2 seconds per dot. Any amount of adhesive can be placed anywhere on the substrate and there are minimal restrictions about placement of other devices prior to dispensing.

### 5.4 Substrate Bonding

Substrate bonding refers to the attachment of the substrate to the MCM package.

### 5.5 Package Sealing

Package sealing refers to the final sealing of the MCM package after all internal attachments and bonds have been made. This can be done with polymer adhesives, solder, brazing, or seam welding. The type of bond depends on the type of package. Polymer adhesives do not provide a hermetic seal.

### 6.0 Layout Rules

### 6.1 Design Advisor

6.1. 1 TBD\*

### 6.2 MCM Module Design Review / Checklist

The MCM Module Design Review (MDR) Checklist is designed to ensure that all research and data required for designing an MCM is available prior to beginning physical design. Completion and approval of the checklist is required prior to beginning physical design. Refer to Appendix E.

### 6.3 MCM-C Thick-Film Multilayer Layout (TFM)

### 6.3.1 Substrate Dimensions and Tolerances

- 6.3.1.1 Refer to Table 6.3.A for ceramic substrate material selection.
- 6.3.1.2 Substrate tolerances shall be +/- .005in or +/- 1 % whichever is greater.
- 6.3.1.3 The print registration tolerance shall be .0025in.
- 6.3.1.4 The stepping tolerance shall be .001in. per image. This is used in determining array image separation. If panelization is required MCM/S™ should be consulted for specification of panel requirements.
- **6.3.1.5** For determining minimum conductor to edge distances, the minimum substrate size is calculated by subtracting the substrate tolerance, the print registration tolerance, and the stepping tolerance, from the nominal substrate dimension. (Subtract stepping tolerance only if panelized).
- 6.3.1.6 The recommended datum for a single image design is the lower left-hand corner of the substrate. If panelization is required MCM/S™ should be consulted for specification of panel datums.
- 6.3.1.7 The recommended grid is 1010in x .010in.
- 6.3.1.8 Substrate camber shall be .002in maximum per linear inch measured diagonally.

### 6.3.2 Thick-Film Conductor Layout

- **6.3.2.1** Refer to Table 6.3.B for thick-film conductor materials and Table 6.3.D, Figure 6.3.E, Table 6.3.F and Figure 6.3.G for thick-film dimensional requirements.
- 6.3.2.2 Conductors should run in X and Y direction only and the length between any two lands should be kept at a minimum. Forty-five (45) degree angles are permissible but use and length should be minimized. Use of curves or arcs is discouraged and requires prior approval.
- 6.3.2.3 Conductor junctions and corners of conductor patterns should have right angle turns.
- 6.3.2.4 Avoid running conductors over the edge of multiple dielectric layers; use vias instead.
- 6.3.2.5 The spacing between conductors must be a minimum of .015in if it is necessary to run conductors over the edge of a single dielectric layer.

- **6.3.2.6** Avoid running conductors parallel to other conductors that are directly beneath them for long distances.
- **6.3.2.7** Metal overlaps on adjacent conductors should be staggered to minimize shorts due to bleeding or misalignment.
- 6.3.2.8 All conductive artwork layers shall be generated as positive artwork.

### 6.3.3 Thick-Film Crossover and Dielectric Layout

- 6.3.3.1 Refer to Table 6.3.C for thick-film dielectric material properties.
- 6.3.3.2 All crossovers shall be orthogonal to the substrate edge and to adjacent layer metal.
- 6.3.3.3 The preferred method for creating a crossover is a via crossover as shown in Figure
- 6.3.G.4, however, It is acceptable to create a crossover as shown in Figure 6.3.E.

### 6.3.4 Thick-Film Via and Multilayer Dielectric Layout

- **6.3.4.1** Refer to Table 6.3.D, Figure 6.3.E, Table 6.3.F and Figure 6.3.G for thick-film dimensional and layout requirements.
- **6.3.4.2** In multilayer structures vias shall be staggered as shown in Figure 6.3.G.2.
- 6.3.4.3 In multilayer structures the dielectric shall be staggered as shown in Figure 6.3.G.3.

Table 6.3.A
Ceramic Substrate Material Properties

MATERIAL	96 PCT ALUMINA	92 PCT ALUMINA	ALUMINUM NITRIDE
THERMAL CONDUCTIVITY W/M/K	19	11	170
COEFFICIENT OF LINEAR THERMAL EXPANSION PPWC (25-200 DEG C)	60	7.2	4.7
YOUNG'S MODULUS X10^6 PSI	44	45	331 GPA
TENSILE STRENGTH X10^3 PSI (25 DEG C)	28	33	276 MPA
DIELECTRIC CONSTANT  @ 1MHZ, 25 DEG C	9.0	9.8	8.6
DIELECTRIC STRENGTH V/MIL	450	540	TBD*
VOLUME RESISTIVITY OHM/CM (25 DEG C)	>10^14	>10^14	>10^14
DIELECTRIC LOSS @ 1MHZ	.001	.200	.0005

Table 6.3.B
Thick-film Conductive Materials

MATERIAL	FIRED THICKNESS (MICRONS)	SHEET RESISTANCE	THERMAL CONDUCTIVITY W /CM-DEG C	
GOLD	9-13	< 5 MOHMS/SQ	TBD*	
TUNGSTEN *	10-13	13 MOHMS/SQ MAX	TBD*	
SILVER	11-13	< 2 MOHMS/SQ	TBD*	

<sup>\*</sup> Outer Layer Tungsten must receive gold or nickel/gold plating to support wirebonding and to prevent oxidation and corrosion (HTCC).

Figure 6.3.C Thick-film Dielectric Materials

MATERIAL	FIRED THICKNESS (MICRONS)	DIELECTRIC CONSTANT @ 25 MHZ	THERMAL CONDUCTIVITY W/CM-DEG C
DIELECTRIC	35-60	8-9	TBD*
OVERGLAZE	18-20	TBD	TBD*
CAPACITOR	CONSULT MCM/STM	CONSULT MCM/STM	CONSULT MCM/S™

Table 6.3.D

Dimensional Requirements for Thick-Film Conductors and Dielectric

DIMENSIONAL REQUIREMENTS	DIM	FIGURE	NOM	MIN
CONDUCTOR TO EDGE OF MINIMUM SUBSTRATE	Α	6.3.E	.010	005
CONDUCTOR WIDTH	В	6.3.E	.010	007
WIDTH OF CONDUCTOR < .050 LONG	С	6.3.E	.015	.010
CONDUCTOR TO CONDUCTOR SPACING	D	6.3.E	.010	.008
CONDUCTOR TO CONDUCTOR SPACING - ADJACENT LAYERS	E	6.3.E	.015	.010
CONDUCTOR TO RESISTOR SPACING (ON SAME LAYER)	F	6.3.E	.020	.015
CONDUCTOR TO RESISTOR SPACING (ON ADJACENT LAYER)	G	6.3.E	.025	.020
CONDUCTOR TO RESISTOR SPACING (TOP HAT CONFIGURATION)	Н	6.3.E	.030	.020
CONDUCTOR LINES OVERLAP - SAME LAYER	l	6.3.E	.010x .020	.010x .015
CONDUCTOR LINES OVERLAP - ADJACENT LAYER	J	6.3.E	.015x .015	.010x .020
DIELECTRIC FOR CROSSOVER, DISTANCE EXTENDED BEYOND WIDTH (ON EITHER TOP OR BOTTOM CONDUCTOR	К	6.3.E	.020	.010

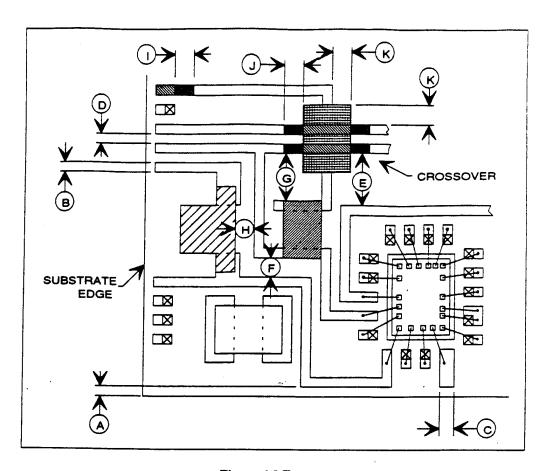
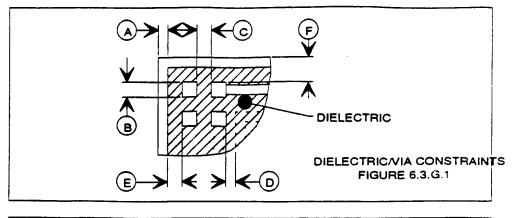


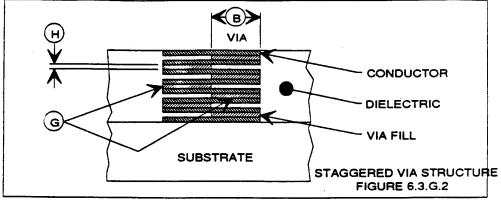
Figure 6.3.E

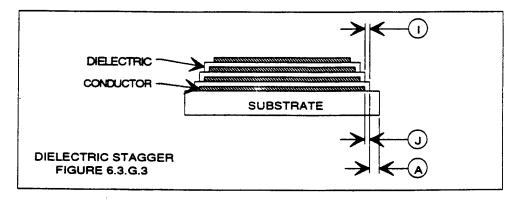
Dimensional Requirements for Thick-Film Conductors and Dielectric

Table 6.3.F
Thick Film Via and Multilayer Dielectric

DIMENSIONAL REQUIREMENTS	DIM	FIGURE	NOM	MIN
DIELECTRIC TO SUBSTRATE EDGE	A	6.3.G.1,3	.010	.005
VIA SIZE	В	6.3.G.1	.015 X	.010 X
			.015	.010
VIA TO ADJACENT VIA SPACING	С	6.3.G.1	.015	.010
VIA TO ADJACENT CONDUCTOR	D	6.3.G.1	.015	.010
SPACING				
VIA TO EDGE OF DIELECTRIC SPACING	Ε	6.3.G.1	.015	.010
VIA TO EDGE OF SUBSTRATE SPACING	F	6.3.G.1	.025	.020
VIA TO VIA SPACING (PITCH) (SAME NET)	G	6.3.G.2	.010	.010
MAXIMUM VIA STACK	Н	6.3.G.2	1 DIEL	1 DIEL
DIELECTRIC/CONDUCTOR OVERLAP	1	6.3.G.3	.010	.005
DIELECTRIC STAGGER	J	6.3.G.3		.005
VIA CROSSOVER DIELECTRIC OVERLAP	К	6.3.G.4	.015	.010
VIA CROSSOVER 2ND CONDUCTOR	L	6.3.G.4	.005	.000
OVERLAP	-	3.3.2.		
VIA CROSSOVER VIA SIZE	М	6.3.G.4	.015	.015







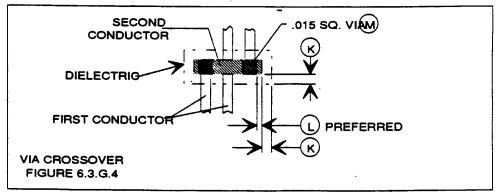


Figure 6.3.G Thick-film Via and Multilayer Dielectric

### 6.3.5 Thick-Film Component Layout

- 6.3.5.1 Thick-Film Resistors
  - 6.3.5.1.1 Refer to Table 6.3.H and Figures 6.3.I, 6.3.J, and 6.3.K for layout and dimensional requirements.
  - 6.3.5.1.2 A good design avoids the use of more than three resistor pastes per substrate.
  - 6.3.5.1.3 Resistors may be screened directly onto the substrate or on any equiplanar level (with MCM/S™ approval). All resistors of the same field must be screened onto the same level.
  - 6.3.5.1.4 Both terminations of any individual resistor must be in the same metal mask.
  - 6.3.5.1.5 Resistors must never be designed into a dielectric hole.
  - **6.3.5.1.6** Probe pads must be available for measurements during trimming. Probe shadowing (the effect of a probe being in the path of a trim) must always be a consideration.
  - 6.3.5.1.7 All resistors screened with 10, 30, or 100 ohm/square paste must be protected with overglaze.
  - **6.3.5.1.8** Top hat resistor designs should not be used for resistors with tolerances of less than 1 PCT.
  - **6.3.5.1.9** Noise can be reduced in thick-film designs by making the resistors longer or by increasing total resistor area.
  - **6.3.5.1.10** Top hat or meander designs should be considered rather than conventional rectangular designs where voltage sensitivity is a problem.
  - 6.3.5.1.11 Matched resistors should be designed for the same ink, placed as close to each other as possible and in the same axis.
  - 6.3.5.1.12 Wire bond pads shall not be used for resistor probe pads.
  - 6.3.5.1.13 Component, i.e., chip capacitor, pads may be used for passive resistor probe pads.
- 6.3.5.1.14 Each resistor must be individually trimmable. Resistor loops must be opened by splitting pad metallization or using a wire bond jumper. Refer to Figure 6.3.K.
- 6.3.5.1.15 All resistors shall be orthogonally oriented to the substrate edges.
- 6.3.5.1.16 All resistors of same field should be oriented in the same direction.
- 6.3.5.1.17 Passive trim resistors may be placed under components which are solder attached with prior approval of MCM/S™.
- 6.3.5.1.18 The maximum aspect ratio for rectangular resistors whose tolerance is <20 % shall be TBD\*. The maximum aspect ratio for inverse aspect ratio resistors shall be TBD\*. The maximum aspect ratio for top-hat resistor designs after trimming shall be TBD\*.

Table 6.3.H
Thick-film Resistor Guidelines

DIMENSIONAL REQUIREMENTS	DIM	FIGURE	NOM	LEAST
RESISTOR DISTANCE TO SUBSTRATE EDGE	Α	6.3.J	.040	.030
RESISTOR DISTANCE TO DIELECTRIC	В	6.3.J	.030	.025
RESISTOR OVERLAP ON A CONDUCTOR	C	6.3.J	.010	.010
TERMINATION				
RESISTOR TERMINATION WIDTH FOR RESISTORS OF	D	6.3.J	NONE	.020
DIFFERENT FIELD		<u> </u>		
RESISTOR TERMINATION WIDTH FOR RESISTORS OF	E	6.3.J	NONE	.015
SAME FIELD WITH DIFFERENT WIDTH		<del>   </del>	015 V	220 Y
TOPHAT RESISTOR OVERLAP ON A CONDUCTOR	F	€ -	.015 X .015	.020 X .020
TERMINATION	G	6.3	.010	.020
EXTENSION OF TERMINATION BEYOND RESISTOR	٦	0.3.0	.010	.005
EXTENSION OF TERMINATION BEYOND RESISTOR	Н	6.3.J	.010	.005
EDGE FOR TOPHAT	п	0.3.5	.010	.000
RESISTOR TO RESISTOR SPACING	<u> </u>	6.3.0	.030	020
TOPHAT TERMINATION SPACING	J	6.3.J	NONE	.030
RESISTOR DISTANCE TO COMPONENT ON SAME	К	6.3.J	NONE	.010
TERMINATION	,,	0.0.0	,,,,,,,	
RESISTOR OVERGLAZE OVERLAP (2)	L	6.3 J	.0075	0.005
RESISTOR LENGTH (INK VALUE <= 100K OHMS SQ.)	М	6.3.J	.040	.030
RESISTOR LENGTH (INK VALUE >=100K OHMS/SQ.)	М	6.3.J	.060	.040
RESISTOR WIDTH (INK VALUE <= 100K OHMS/SQ.)	N	6.3.J	.040	.030
RESISTOR WIDTH (INK VALUE > 100K OHMS/SQ.)	N	6.3.J	.060	.040
RESISTOR WIDTH, +/-1% TOLERANCE	N	6.3.J	TBD*	TBD*
RESISTOR WIDTH, 5% TOLERANCE	N	6.3.J	TBD.	TBD*
RESISTOR WIDTH, TOP HAT CONFIGURATION	0	6.3.J	.080	.060
RESISTOR HEIGHT, TOP HAT CONFIGURATION	P	6.3.J	500	.030
AIR ABRASIVE TRIMMING ALLOWANCE (FROM	Q	6.3.J	.020	.050
RESISTOR TO ADJACENT CONDUCTOR, RESISTOR		1		
OR LAND)				
AIR ABRASIVE TRIMMING ALLOWANCE FOR TOP HAT	R	6.3.J	.035	.030
DESIGNS				
MINIMUM PROBE PAD AREA FOR PASSIVE TRIM	S	6.3.J	.040 X	.020 X
		-	.040	.015
MINIMUM PROBE PAD AREA FOR ACTIVE TRIM	Т	6.3.J	.050 X	.040 X
		<del>                                     </del>	.050	.040
ACTIVE TRIM PROBE PAD CLEARANCE FROM	U	6.3.J	.035	.030
COMPONENT PERIOTOR LOOP		624	010	.010
BREAK IN RESISTOR LOOP	٧	6.3.K	.010 <b>MAX</b>	.010
		1	IVIAA	L

**6.3.5.1.19** The following formula shall be used to calculate rectilinear and inverse aspect ratio resistor geometry's:

- The design value (as fired value) shall be 80 % of the nominal trimmed value
- The preferred length and width of .040in should be considered.
- Power dissipation consideration at 50 watts /in (100 watts/in derated 50 PCT to 50 watts/in for a 100 % reliability factor) and 50 % trimming.

R = Resistance

AR = Aspect Ratio

# WHEN SUBSTITUTING FOR (AR)

**6.3.5.1.20** The following shall be considered to calculate tophat resistor geometry's: Refer to Figure 6.3.I.

- Tophat resistors reach value by increasing the resistive path (as opposed to reducing width).
- The resistor length is increased 50 % to assure that the desired value is attained before running out of length.
- Figure 6.3.I shows the unit value of each tophat square.
- The minimum tophat square shall be .015in.
- The trim allowance shall be .005in.

R = Resistance

SR = Sheet Resistivity

AR = Aspect Ratio

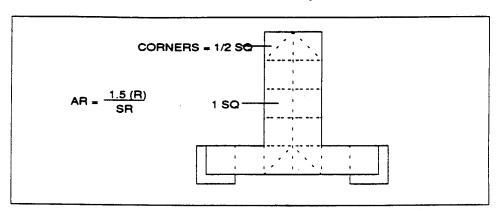


Figure 6.3.I Tophat Guidelines

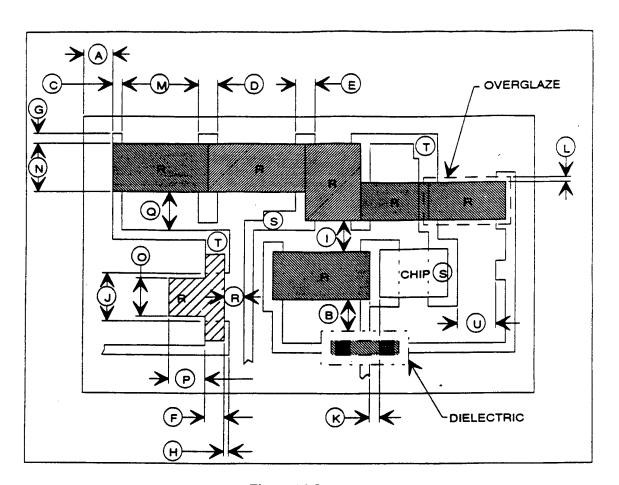


Figure 6.3.J Resistor Layout Guidelines

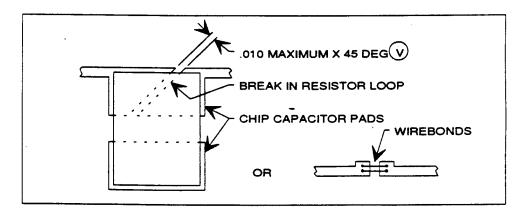


Figure 6.3.K Resistor Loop Break

# 6.3.5.3 Thick-film Capacitor Layout

6.3.5.3.1 Consult MCM/S™ for thick-film capacitor design considerations.

# 6.4 MCM-C High Temperature Cofired Ceramic (HTCC) Layout

# 6.4.1 HTCC Substrate/Package Dimensions and Tolerances

- 6.4.1.1 Refer to Table 6.3.A for ceramic substrate material selection.
- 6.4.1.2 The recommended datum or database origin, for generation of manufacturing files and NC data is the geometric centroid of the design. MCM/S<sup>TM</sup> should be consulted for definition of the appropriate datum for dimensioning and tolerancing for the mechanical fabrication drawing.
- **6.4.1.3** The recommended grid is .005in with the grid origin defined as the geometric centroid of the design database.
- 6.4.1.4 The recommended camber is .002in per linear inch measured diagonally. Large packages or substrates may require reduction to .001in per linear inch measured diagonally 6.4.1.5 The recommended tolerance for ceramic features is +/- 1 % of the design dimension. It is possible to achieve +/- .5 % for critical design features. It is recommended that post fire printing be utilized for critical dimensional features of the metallization patterns, e.g. fine pitch connector or LGA patterns.

# 6.4.2 HTCC Conductor Layout

- 6.4.2.1 Refer to Table 6.3.B for thick-film conductor materials.
- 6.4.2.2 Refer to Table 6.4.A for HTCC conductor layout and dimensional requirements.
- 6.4.2.3 The exposed tungsten conductive pattern shall be Gold plated 60 microinches minimum, 150 micro inches maximum, over (optional) Nickel underplate 250 microinches minimum, 350 microinches maximum. Exception: LGA patterns shall be plated Gold 10 microinches minimum, 35 microinches maximum, over Nickel underplate 100 microinches minimum, 200 microinches maximum.
- 6.4.2.4 Planes shall be solid coverage metallization or orthogonal lattice.
- 6.4.2.5 All conductive artwork layers shall be generated as positive artwork.

## 6.4.3 HTCC Via Construction

- 6.4.3.1 Refer to Table 6.4.A for HTCC via layout and dimensional requirements.
- 6.4.3.2 Vias are allowed to make a solid contact connection to planes.
- 6.4.3.3 There is no minimum or maximum via stack requirement. However, it is recommended that at least (1) stagger occurs in the via stack to ensure hermeticity of the package.

# 6.4.4 HTCC Thick-film Component Layout

6.4.4.1 TBD\*.

# 6.4.5 HTCC Special Considerations

#### 6.4.5.1 Cavity Layout

Cavity area will be dictated by the size of the substrate or components. The same general tolerances apply to a cavity as other ceramic features. It is recommended that a cavity be located asymmetrically within the design to minimize the risk of fracturing during leak testing or excessive environmental conditions.

# 6.4.5.2 (avity Depth

6.4.5.2.1 The minimum allowable substrate or cavity base thickness shall be .015in for areas  $\leq$  .25 sq. in.; .020in for areas > .25 sq. in. but  $\leq$  1.00 sq. in.; and .025in for areas > 1.00 sq. in.. The base thickness should always be maximized, especially for larger packages and cavities.

6.4.5.2.2 The package or cavity depth shall be defined by consideration of the following:

- Thickness of the base/substrate.
- · Maximum component or post height.
- Bond lines Allow .003in max for adhesive.
- Interconnection height allowance Allow a minimum of .015in above the thickest die for wirebond loops.
- Clearance and tolerances. (For mil applications MIL-STD-883D, Method 2017 requires .005in minimum clearance from wire loop to lid.)
- Lid encroachment.
- Module environment.
- Screening.
- Qualification.
- 6.4.5.2.3 The cavity inside corner radius shall be .020in maximum.

## 6.4.5.3 Seal Rings

- **6.4.5.3.1** The seal ring shall be constructed of Kovar or Alloy 42 in accordance with Mil-1-23011C, and shall support attachment to the substrate or package by high-temperature Gold/Tin, Copper/Silver, Indium/Copper/Silver, or other equivalent brazing processes. Gold/Tin is the preferred brazing process.
- 6.4.5.3.2 The seal ring plating shall be electroplated Gold 60 microinches minimum, 150 microinches maximum, over Nickel underplate 350 microinches minimum, 350 microinches maximum in accordance with Mil-G-38354.
- 6.4.5.3.3 The preferred seal ring width is .040in +/- .005in, Any deviation requires MCM/S™ approval. Refer to Figure 6.4.B.
- 6.4.5.3.4 The preferred seal ring inside corner radius is .020 +/- .005in.
- 6.4.5.2.5 The preferred seal ring outside corner radius is .020 +/- .005in and shall not exceed .030in.
- **6.4.5.3.6** The seal ring metallization shall be .010in larger per side than the seal ring for packages  $\leq 2.000$ in in dimension and .015in larger per side for packages > 2.000in in dimension.

# 6.4.5.4 Stepped Lid Design

**6.4.5.4.1** Refer to Figure 6.4.B for stepped lid layout and dimensionals requirements. **6.4.5.4.2** The lid shall be constructed of Kovar or Alloy 42 in accordance with Mil-I-23011C.

## 6.4.5.4.3 Lid Plating

- 6.4.5.4.3.1 Nickel/Gold lid electroplating shall be Gold 50 microinches minimum, 350 microinches maximum over Nickel underplate 50 microinches minimum, 225 microinches maximum in accordance with Mil-G-38354 and QQ-N-290.
- **6.4.5.4.3.2** Nickel only electroplating shall be 100 microinches minimum to 250 microinches maximum in accordance with QQ-N-290.
- 6.4.5.4.3.3 The required lid manufacturing process is etching.

# 6.4.5.5 Post Considerations

6.4.5.5.1 The application of post(s) should be a considered when package designs are very large or lids are thinner than specified in Figure 6.4.B. A post can prevent damage of wirebonds from oil-canning during leak testing or excessive environmental conditions.

## 6.4.5.6 Land Grid Array (LGA) Fiducials

**6.4.5.6.1** Refer to Figure 6.4.C for fiducial requirements for Land Grid Array (LGA) applications.

Table 6.4.A HTCC Conductor and Via Requirements

DIMENSIONAL REQUIREMENTS	DIM	FIGURE	NOM	MIN
CONDUCTOR TO EDGE OF SUBSTRATE - EXTERNAL	Α	_	.020	.010
CONDUCTOR TO EDGE OF SUBSTRATE - INTERNAL	В	_	_	.020
CONDUCTOR TO EDGE OF CAVITY	С		_	.020
CONDUCTOR WIDTH	D	_	.010	.005
CONDUCTOR PITCH	E	_	.020	.010
CONDUCTOR TO CONDUCTOR SPACING	F	_	.010	.005
VIA HOLE DIAMETER	G	_	.008	.004
VIA COVER PAD DIAMETER	Н	_	.015	.008
VIA PITCH	1	_	.025	.013
VIA TO CONDUCTOR SPACING	J	_	.010	.005
VIA TO SUBSTRATE EDGE SPACING	К	_	.030	.025
VIA TO CAVITY EDGE SPACING	L	_	.025	.020
VIA PAD CLEARANCE IN PLANE (ANTE-PAD)	М	_	.043	.032
VIA PAD CLEARANCE IN PLANE	N	_	.014	.014
VIA STAGGER - 1 X PAD DIAMETER	0		.015	.008

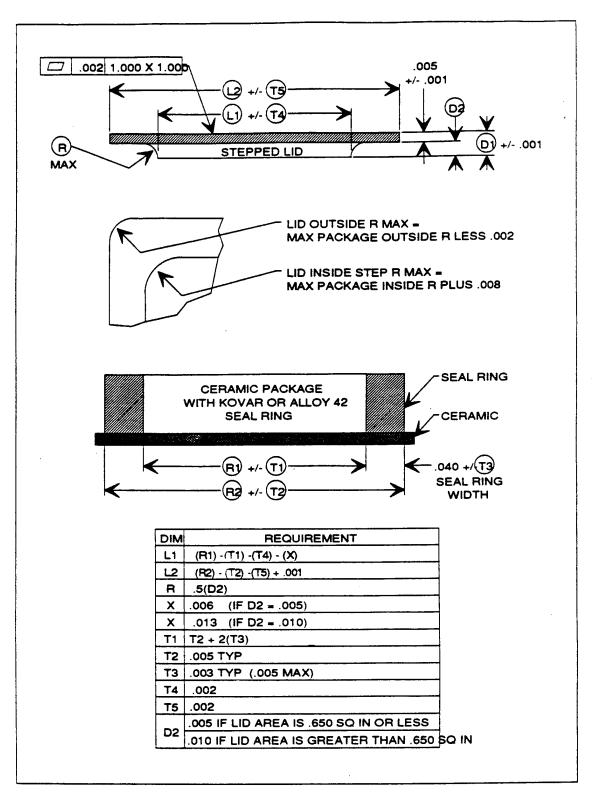


Figure 6.4.B Stepped Lid Design

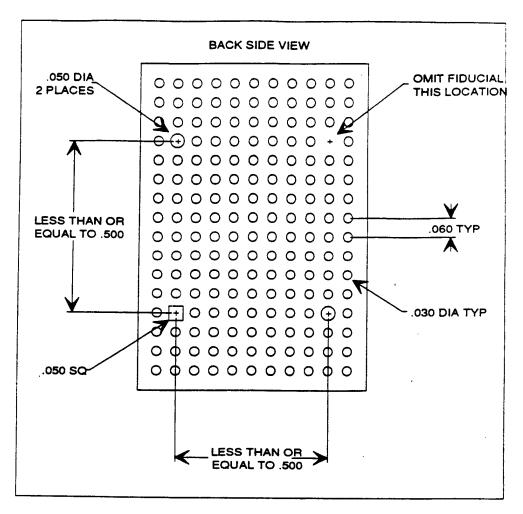


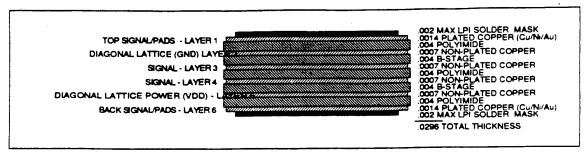
Figure 6.4.C LGA Fiducial Requirements

# 6.5 MCM-L Layout

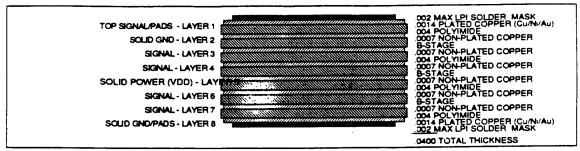
# 6.5.1 MCM-L Substrate Dimensions and Tolerances

- 6.5.1.1 Refer to Table 6.5.A for MCM-L polymer substrate materials.
- 6.5.1.2 The recommended datum is a non-plated through tooling hole at least .031 in diameter. In the event substrate density or other requirements prevent the utilization of a tooling hole within the substrate layout area, the lower left fiducial or lower left corner shall be used as a datum for dimensioning and generation of NC drill data.
- 6.5.1.3 The recommended grid is .005in. Smaller grids of .001in or .0005in are typical.
- 6.5.1.4 The recommended camber is .7 % per linear inch measured diagonally.
- 6.5.1.5 Substrate thickness may not exceed .040in. Thicker boards require approval of MCM/STM
- 6.5.1.6 The recommended tolerance of profile is .010in all around the substrate image area. The outer edge of panels may be incrased in profile tolerance to .020in all around. 6.5.1.7 Substrate panel size may not exceed 4.016in (102 mm) by 7.874in (200 mm). Substrate panel size shall be a minimum of 1.968in (50 mm) by 2.952 in (75 mm) length. MCM/S<sup>TM</sup> standard products are specifically panelized to increase production yields from substrate fabrication though final manufacturing.

6.5.1.8 Wire bond surface metallization, for laminate based systems, shall be 150 microinches minimum to 300 microinches maximum of Nickel (electroless or electrolytic is acceptable), followed by 50 microinches minimum to 150 microinches maximum of Soft High Purity wire bondable gold per MIL-45204G, Type III-A.



## **6 Layer Formation**



**8 Layer Formation** 

Figure 6.5.A Standard MCM-L layer Structure

## 6.5.2 MCM-L Conductor Layout

- 6.5.2.1 Refer to Table 6.5.B for MCM-L layout and dimensional requirements.
- 6.5.2.2 The length of a conductor between any two lands should be kept at a minimum and conductors that are straight lines and run in X, Y or 45° directions are preferred.
- 6.5.2.3 All conductors that change direction, where the included angle is less than 90 degrees shall have their internal and external corners rounded.
- 6.5.2.4 The width of a conductor should be as uniform as possible over its length, however, it may be necessary because of design restraints to "neck down" a conductor to allow it to be routed between restricted areas (e.g. between two through holes).
- 6.5.2.5 Conductor spacing should be maximized where possible.
- **6.5.2.6** Except for edge board contacts, the minimum distance between conductive surfaces and the edge of the finished board shall not be less than the minimum spacing defined.
- 6.5.2.7 Large conductive areas (.125in wide or larger conductors) increase the likelihood for blistering or warping. Areas that cover more than a 1.0in diameter should be broken up into cross-hatched areas and should be on the primary side of the substrate. External conductors that extend beyond a 1.0in diameter circle should contain etched areas that break up the large conductive area. Internal conductive areas that extend beyond the 1.0in diameter should be as near to the center of the board as possible, and should contain etched areas as well.

6.5.2.8 No mechanical routing (slots) shall be in the substrate in an area bounded by the following area: From the substrate (0, 0) origin point, where the origin point is the substrate upper right hand corner as it travels down the system conveyors with travel from left to right: An area from 1.181in (30 mm) to 1.456in (37 mm) in the x-direction, and from .787in (20 mm) to .984in (25 mm) in the y-direction.

6.5.2.9 All conductive artwork layers shall be generated as positive artwork. (Panelization).

# 6.5.3 MCM-L Solder mask Layout

- 6.5.3.1 Refer to Table 6.5.B for layout and dimensional requirements.
- **6.5.3.2** The solder mask shall be Type B liquid film, photo defined image (LPI) per IPC-SM-840.
- 6.5.3.3 All solder mask shall be over bare copper or over Nickel Gold.
- 6.5.3.4 The maximum allowable solder mask inside any encapsulation area shall be .008in.

# 6.5.4 MCM-L Via Construction

6.5.4.1 Refer to Table 6.5.B for dimensional requirements. Refer to Table 6.5.F for minimum drilled hole sizes to be used with various board thicknesses. Refer to Table 6.5.C for the plated through hole size to board thickness aspect ratio for plated-through hole vias.

6.5.4.2 Minimum annular rings for supported and unsupported holes shall be as specified in Table 6.5.G. The minimum annular ring on external layers is the minimum amount of copper (at the narrowest point) between the edge of the hole and the edge of the land after plating of the finished hole (Figure 6.5.D). The minimum annular ring on the internal layers is the amount of copper (at the narrowest point) between the edge of the drilled hole and the edge of the land after drilling the hole (Figure 6.5.E).

Table 6.5.A
Polymer Substrate Material Properties

MATERIAL	BT EPOXY	POLYIMIDE	FR5	
THERMAL CONDUCTIVITY W/CM - DEG C	1.674	.00243	TBD*	
COEFFICIENT OF LINEAR THERMAL EXPANSION PPM/C	1.3-1.5 X 10^-3 (CM/CM/DEG C)	TBD*	TBD*	
DIELECTRIC CONSTANT @ 1MHZ	4.1	4.4	TBD*	
DIELECTRIC RESISTANCE (OHMS/CM)	5 X 10^13-10^15	TBD*	TBD*	
VOLUME RESISTANCE (OHM/CM)	5 X 10^15 - 10^16	TBD*	TBD*	
DISSIPATION FACTOR @ 1MHZ	.00550095			
Тд	TBD*	TBD*	TBD*	

Table 6.5.B MCM-L Conductor and Via Requirements

DIMENSIONAL REQUIREMENTS	DIM	FIGURE	NOM	MIN
CONDUCTOR WIDTH	Α	6.5.	.004	.003
CONDUCTOR SPACE	В	6.5.	.004	.003
CONDUCTOR TO BOARD EDGE - OUTER LAYER (T = BOARD THICKNESS)	С	6.5.	.020	.000 (PLANE)
CONDUCTOR TO BOARD EDGE - INNER LAYER (T = BOARD THICKNESS)	D	6.5.	.020	.005
VIA DRILL DIAMETER	Ε	6.5.	010	.008
VIA DRILL TO BOARD EDGE (T = BOARD THICKNESS)	F	6.5.		≥T
OUTER LAYER VIA PAD DIAMETER	G	6.5.	-30	.016
INNER LAYER VIA PAD DIAMETER	Н	6.5.	: 20	.016
INNER LAYER VIA PAD PLANE CLEARANCE DIAMETER (D + .012)	I	6.5.	.032	.028
BLIND VIA DRILL DIAMETER	J	6.5.	_	.006
BLIND VIA PAD DIAMETER	K	6.5.		.014
SOLDERMASK PAD CLEARANCE	L	6.5.	.003	.002
SOLDERMASK WIDTH	М	6.5.	_	.006
MINIMUM ANNULAR RING	-	6.5.G	.002	TANGENT

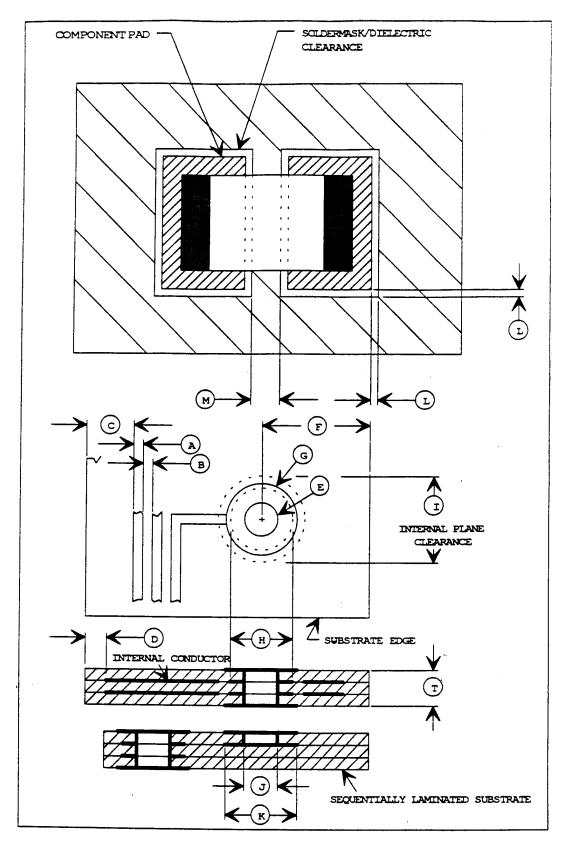
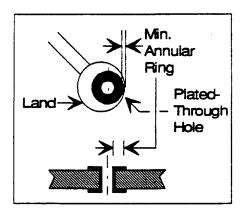


Figure 6.5.B MCM-L Conductor and Via Requirements

Table 6.5.C
Plated-Through Hole Size to Board Thickness Aspect Ratios

	LEVEL A	LEVEL B	LEVEL C
ASPECT RATIOS	1:3 TO 1:5	1:6 TO 1:8	1:9 & UP



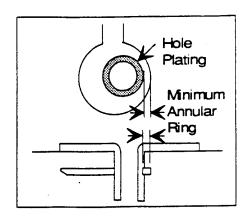


Figure 6.5.D: External Annular Ring

Figure 6.5.E:Internal Annular Ring

Table 6.5.F

Minimum Drilled Hole Sizes for Plated-Through Hole Vias
(as defined in IPC-D-275)

BOARD THICKNESS	CLASS 1	CLASS 2	CLASS 3
<0.04 (IN)	LEVEL C	LEVEL C	LEVEL C
	0.006	0.008	0.010
0.040 - 0.063	LEVEL C	LEVEL C	LEVEL B
	0.006	0.010	0.012
0.063 - 0.080	LEVEL C	LEVEL B	LEVEL B
	0.012	0.016	0.020
>0.080	LEVEL B	LEVEL A	LEVEL A
	0.016	0.020	0.024

Table 6.5.G Minimum Annular Rings

ANNULAR RING	CLASS 1 AND 2	CLASS 3 MILITARY
INTERNAL SUPPORTED	TANGENT, NO BREAKOUT	.002 IN
EXTERNAL SUPPORTED	TANGENT, NO BREAKOUT	.004 IN
EXTERNAL UNSUPPORTED	.006 IN	.01 IN

# 6.6 General Layout and Design for Manufacture

# 6.6.1 Die and Component Attach

- 6.6.1.1 Die/Component bond clearances to high profile features and components shall be as shown in Table 6.6.A, Table 6.6.J, and Figure 6.6.K.
- 6.6.1.2 The die attach designated area must be at right angles to the edges of the board/substrate.
- 6.6.1.3 The die attach pad shall be smooth and continuous beneath the die. No patterned die attach pad may be used.
- **6.6.1.4** The maximum bond stage area for the Hughes 2500 II Semi-Automatic Epoxy Die Bonder is 11.25in by 4.25in.
- **6.6.1.5** The maximum package depth for the Hughes 2500 II Semi-Automatic Epoxy Die Bonder from the top of the package to the lowest bond site is .300in.
- **6.6.1.6** The maximum bond stage area for the MRSI 501 Automatic Die Bonder is 2.00in by 10.00in.
- 6.6.1.7 The maximum package depth for the MRSI 501 Automatic Die Bonder from the top of the package to the lowest bond site is .300in.
- **6.6.1.8** If possible all components of like type shall be orientated in the same direction and shall have identical wirebond patterns. This will save programming and assembly time.
- 6.6.1.9 If the die is not square and has a large aspect ratio (e.g., .300in x .750in) then the per side allowance should be decided based on each side's dimension (i.e.: the per side allowance need not be the same). Other per side allowances must be approved by MCM/S<sup>TM</sup>. (See Tables below).
- 6.6.1.10 Die thickness shall not exceed .025in or be less than .014in except on approval of MCM/S<sup>TM</sup>.
- 6.6.1.11 Die attach area may be recessed into the board/substrate surface. The substrate recess must be .020 in per side (including corners) larger than the die regardless of die size. Die top surface must not be lower than substrate surface by more than .010in.
- 6.6.1.12 Minimum die size: .050in x .050in. Smaller die sizes require approval of MCM/S™.
- 6.6.1.13 Maximum die size: 1.000in x 1.000in. Larger sizes require approval of MCM/S™.

# 6.6.2 Die/Component Attach MCM-C TFM

- 6.6.2.1 A minimum of (2) diagonally opposing fiducials is required. The fiducials shall be as specified in Figure 6.6.F, Figure 6.6.G, Figure 6.6.H, and Figure 6.6.I.
- 6.6.2.2 Above fiducials shall be printed on the first conductor layer (of each substrate side).
- **6.6.2.3** The die attach pad or designated die attach area, if no pad is used, shall be larger than the die per the following table:

DIE SIZE	PER SIDE PAD ALLOWANCE
.000200 IN	010 IN
.200500 IN	.015 IN
.500 - 1.000 IN	.020 IN

## 6.6.3 Die/Component Attach MCM-C HTCC

- 6.6.3.1 A minimum of (2) diagonally opposing fiducials is required. The fiducials shall be as specified in Figure 6.6.F, Figure 6.6.G, Figure 6.6.H, and Figure 6.6.I.
- 6.6.3.2 The die attach pad or designated die attach area, if no pad is used, shall be larger than the die per the following table:

DIE SIZE	PER SIDE PAD ALLOWANCE
.000200 IN	.010 IN
.200500 IN	.015 IN
.500 - 1.000 IN	.020 IN

# 6.6.4 Die/Component Attach MCM-L

6.6.4.1 The die attach pad may be plated or bare laminate substrate material. Determination of reliability of die attachment to designated surfaces, other than gold plated metal is the responsibility of the requesting customer unless other arrangements are made in advance.
6.6.4.2 A minimum of (2) diagonally opposing fiducials is required. The fiducials shall be as specified in Figure 6.6.F, Figure 6.6.G, Figure 6.6.H, and Figure 6.6.I
6.6.4.3 The die attach pad or designated die attach area, if no pad is used, shall be larger than the die per the following table:

DIE SIZE	PER SIDE PAD ALLOWANCE
.000200 IN	.010 IN
.200500 IN	.015 IN
.500 - 1.000 IN	.020 IN

# Table 6.6.A Pick and Place/Dispense Tool Clearances For Hughes 2500-II Semi-Automatic Epoxy Die Bonder and MRSI 501 Automatic Die Bonder

REQUIREMENT	DIM	FIGURE	MAX	MIN
COMPONENT PAD > .040 SQ TOWARD VERTICAL OBSTACLE	A	_	_	.010
COMPONENT PAD < .040 SQ TOWARD VERTICAL OBSTACLE	В		_	.032
COMPONENT CENTER TO HIGH PROFILE OBSTACLE	С		_	.0415
MINIMUM DIE SIZE	D	_	_	.020 X .020
MAXIMUM DIE SIZE (IF DIE SIZE EXCEEDS .130 X .130 THERE MUST BE A WAY TO DETERMINE THE DIE CENTROID).	E	_	.300 X .300	_

#### TBD\*

# Figure/Table 6.6.B MCM-L Automatic Pick and Place/Dispense Tool Clearances

# 6.6.5 Epoxy Dispense

6.6.5.1 In general, the guidelines defined in Table 6.6.A for die/component placement provide ample clearance for epoxy daubing. Tool clearances for MCM-C automatic epoxy dispensers shall be as specified in Figure 6.6.A, and for MCM-L, as specified in Figure 6.6.B.
6.6.5.2 A minimum of (2) diagonally opposing fiducials is required. Fiducials shall be as specified in Figure 6.6.F, Figure 6.6.G, Figure 6.6.H, and Figure 6.6.I.

# 6.6.6 Wire bonding

6.6.6.1 Wire bond connections shall never be made between pads on an IC die.

**6.6.6.2** Wires shall never cross other wires or chip components, shall be uniform in length, and shall be orthogonal when possible.

- **6.6.6.3** Table 6.6.C specifies recommended minimum and maximum wire lengths between bonds.
- 6.6.6.4 The preferred jumper wire length is .020in .060in.
- **6.6.6.5** Wirebond clearances to high profile features and components shall be as shown in Figure 6.6.D for automatic thermosonic gold ball bonding (Hughes 2460 II).
- **6.6.6.6** The maximum bond stage area for automatic thermosonic gold ball bonding (Hughes 2460 II) is 3.25in by 3.25in.
- **6.6.6.7** The maximum package depth for automatic thermosonic gold ball bonding (Hughes 2460-II) from the top of the package to the lowest bond site is .250in.
- **6.6.6.8** Wirebond clearances to high profile features and components shall be as shown in Figure 6.6.E for automatic ultrasonic aluminum or gold wedge bonding (K & S).
- **6.6.6.9** The maximum bond stage area for automatic ultrasonic aluminum or gold wedge bonding (K & S) is 12.0in by 5.0in.
- 6.6.6.10 The maximum package depth for automatic ultrasonic aluminum or gold wedge bonding (K & S) from the top of the package to the lowest bond site is .250in.
- 6.6.6.11 For purposes of determining minimum parallel wirebonding clearances to obstacles, design clearances listed in Figure 6.6.D should be used for both the Hughes 2460-II (Figure 6.6.D) and K & S (Figure 6.6.E).
- 6.6.6.12 For fine pitch die bond pads (< .006in) consult MCM/S™ for assistance in defining wire and bond pad configuration.
- **6.6.6.13** A minimum of (2) diagonally opposing fiducials is required. Fiducials shall be as specified in Figure 6.6.F, Figure 6.6.G, and Figure 6.6.I.

# 6.6.7 Wire bonding MCM-C TFM

- 6.6.7.1 For layout of wire bond sites and connections refer to Table 6.6.J and Figure 6.6.K. 6.6.8 Wire bonding MCM-C HTCC
  - 6.6.7.1 For layout of wire bond sites and connections refer to Table 6.6.J and Figure 6.6.K.
  - 6.6.7.2 Wire bond fiducials shall, as a minimum, be included in 2 opposite corners of each die site. The fiducials shall be per the design shown in Figure 6.6.H.

# 6.6.9 Wire bonding MCM-L

- 6.6.9.1 For layout of wire bond sites and connections refer to Table 6.6.J and Figure 6.6.K.
- **6.6.9.2** Whenever possible, wire bond design shall be of orthogonal type, where in the wires leave the die periphery at 90 degree angles to the die edge.
- **6.6.9.3** Wires where angles are used shall have bonding fingers wherein the finger angle on the substrate matches the angle of the wire. The bond finger and the wire shall be parallel where ever possible.
- **6.6.9.4** Wire bond fingers should not be closer than .010in to the die attach pad and begin not further than .020in from the die attach pad.
- 6.6.9.5 Wire bond fiducials shall, as a minimum, be included in 2 opposite corners of each die site. The fiducials shall be per the design shown in Figure 6.6.H.
- 6.6.9.6 Each wire bond finger shall have no obstructions within that length or within a .010in wide area down the entire length of the wire bond finger.

Table 6.6.C

Minimum and Maximum Wire Lengths

		C Dengins
WIRE TYPE	MINIMUM	MAXIMUM
.7 MILS	20 MILS	80 MILS
1.0 MILS	20 MILS	100 MILS
1.25 MILS	20 MILS	100 MILS
1.5 MILS	20 MILS	100 MILS

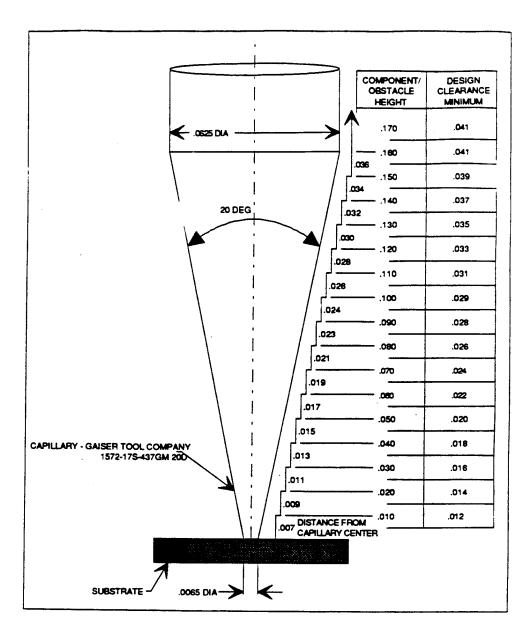


Figure 6.6.D Hughes 2460 II Thermosonic Gold Ball Bonder

Figure 6.6.E K & S \* NOTICE\*

\*NOTICE\*

Design Guidelines for K & S 1470 and K & S 1472 wirebonders are currently being prepared for incorporation into a future revision of these guidelines. For direction in advance of this incorporation consult MCM/S™.

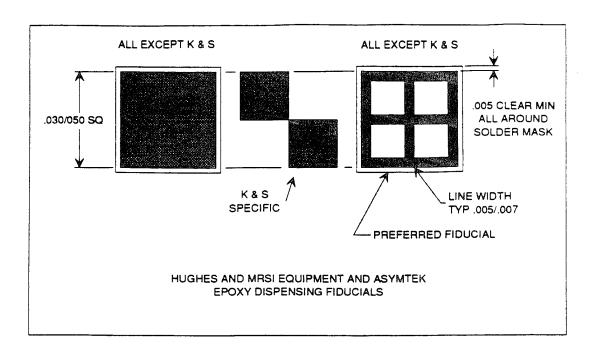


Figure 6.6.F

Fiducials For Hughes 2500-II Semi-Automatic Epoxy Die Bonder,

MRSI Pick and place, K & S and Asymtek Automatic Epoxy Dispenser,

and Hughes Wire Bonders

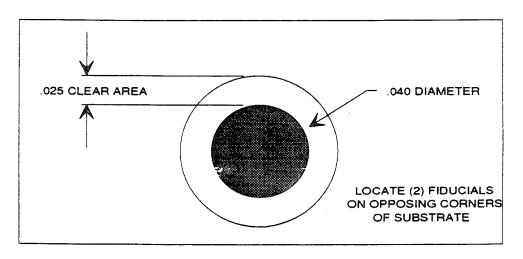


Figure 6.6.G Bad Board Sensor Fiducials (Optional)

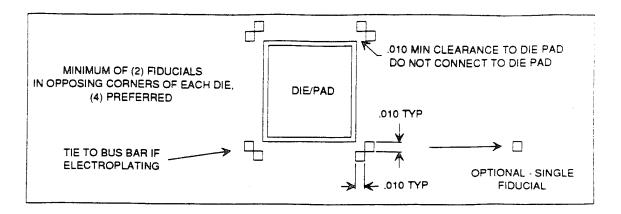


Figure 6.6.H MCM-L and MCM-C Wire and Die Bond Fiducials

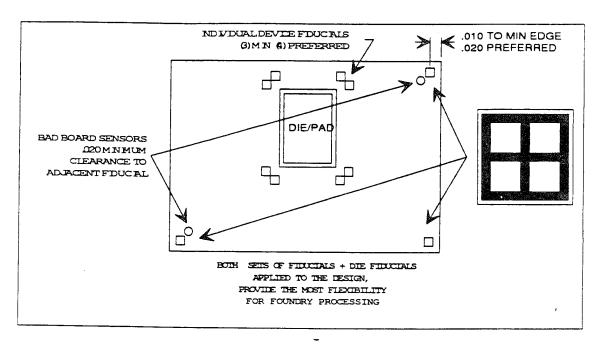


Figure 6.6.I Global Referencing Fiducial Locations

Table 6.6.J MCM-C and MCM-L Assembly Producibility Guidelines

DIMENSIONAL REQUIREMENTS	DIM	FIGURE	MOM	MIN
EXIT BONDING LANDS (WIDTH AND LENGTH) (TFM)	Α	6.6.K	.010 X.025	010 X.020
LENGTH - WIRE BONDING LANDS (TFM)	В	6.6.K	.020	.010
WIDTH - WIRE BONDING LANDS (1 WIRE ON SITE) (TFM)	С	6.6.K	.010	.010
WIDTH - WIRE BONDING LANDS (2 WIRES ON SAME SITE)	D	6.6.K	.015	.015
ADD .005 FOR EACH ADDITIONAL WIRE) (TFM)				
WIRE BONDING LANDS - PITCH (TFM)	E	6.6.K		.020
EXIT BONDING LANDS (WIDTH AND LENGTH) (HTCC)	Α	6.6.K	.010 X.025	.010 X.020
LENGTH - WIRE BONDING LANDS (HTCC)	В	6.6.K	.015	.008
WIDTH - WIRE BONDING LANDS (1 WIRE ON SITE) (HTCC)	С	6.6.K	.008	.004
WIDTH - WIRE BONDING LANDS (2 WIRES ON SAME SITE)	D	6. <b>6</b> .K	.008	.008
(ADD .004 FOR EACH ADDITIONAL WIRE) (HTCC)				
WIRE BONDING LANDS - PITCH (HTCC)	E	6.6.K	_	.010
EXIT BONDING LANDS (WIDTH AND LENGTH) (MCM-L)	Α	6.6.K	.010 X.025	.010 X.020
LENGTH - WIRE BONDING LANDS (MCM-L)	В	6.6.K	.025	.010
WIDTH - WIRE BONDING LANDS (1 WIRE ON SITE) (MCM-L)	С	6.6.K	.006	.005
WIDTH - WIRE BONDING LANDS (2 WIRES ON SAME SITE -	D	6.6.K	.010	.010
(ADD 005 FOR ADDITIONAL WIRE) (MCM-L)				
WIRE BONDING LANDS - PITCH (MCM-L)	E	6.6.K		.009
DIE OR COMPONENT PAD TO ADJACENT CONDUCTOR	F	6.6.K	.015	.010
COMPONENT PAD TO ADJACENT COMPONENT PAD	G	6.6.K	.015	.010
COMPONENT PAD TO ADJACENT DIE PAD	H	6.6.K	.015	.010
DIE PAD TO ADJACENT DIE PAD		6.6.K	.020	015
DIE OR COMPONENT PAD TO SUBSTRATE EDGE	J	6.6.K		020
DIE OR COMPONENT PAD TO CAVITY EDGE	K	6.6.K		.020
DIE/COMPONENT PAD AND CONDUCTOR TO SEAL RING	L	6.6.K	_	.020
METALLIZATION				
WIREBOND PAD CLEARANCE TOWARD VERTICAL	M	6.6.D	_	_
OBSTACLE		6.6.E	, i	
		6.6.K		
WIREBOND PAD CLEARANCE PARALLEL TO VERTICAL	N	6.6.D		_
OBSTACLE	<del> </del>	- C C K		010
WIREBOND PAD CLEARANCE TO WIREBOND PAD - DIRECT	0	6.6.K		.010

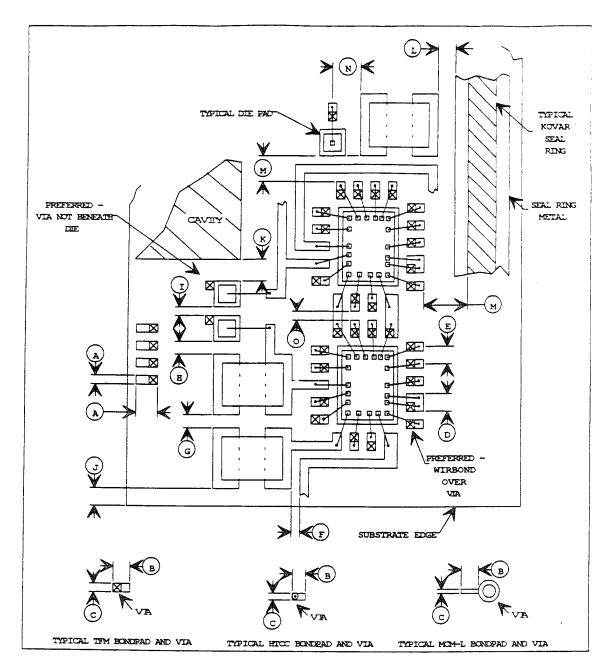


Figure 6.6.K MCM-C and MCM-L Assembly Guidelines

# 6.6.10 MCM-L Encapsulation

6.6.10.1 Encapsulation area should be defined with white printed silk screen denoting the maximum extent of encapsulation acceptable. Width of the silk screen should be .015in (0.38mm). Widths wider than .015in (0.38mm) must be approved by MCM/S™. Widths narrower than .015in (0.38 mm) are not practical for production and must be reviewed by substrate vendors.

Liquid encapsulation area shall be determined by the following formula:

Die size + 2 \* Die pad clearance + 2 \* Die pad to wire bond finger clearance + 2 \* Wire bond finger length + .030in

= Inside dimension (ID) of silk screen

Outside dimension (OD) of silk screen printed area = ID + (.015in \* 2)

**6.6.10.2** Solder mask shall not intrude inside the encapsulation area except by more than .008in.

6.6.10.3 Vias shall not intrude inside the encapsulation area except by approval of MCM/S™. Any vias inside the encapsulation area must be tented. The tenting method must be reviewed and approved by MCM/S™.

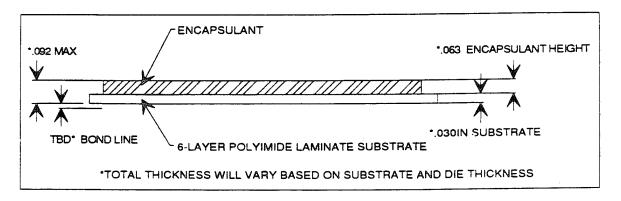


Figure 6.6.L MCM-L Encapsulation

## 6.7 Pad Layout

# 6.7.1 Chip Component Pads

6.7.1.1 Refer to Figure 6.7.A for layout guidelines for chip component pads. These guidelines are for discrete passive device, and discrete active devices.

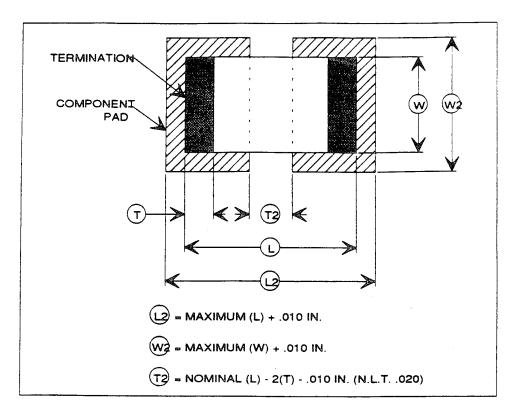


Figure 6.7.A

Dimensional Requirements for Chip Mounting Pads

## 6.7.2 Test Pads

# 6.7.2.1 Recommended Dimensions/Spacings

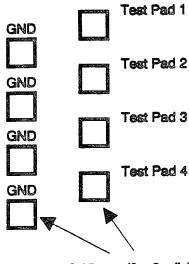
The recommended dimensions/spacings for test pads shall be as follows:

- 1. Test Pad Size: The minimum test pad size shall be  $0.05 \times 0.05 \text{ mm}$  (2 x 2 mils) and the recommended minimum size shall be  $0.10 \times 0.10 \text{ mm}$  (4 x 4 mils). Although pads smaller than 0.05mm square can be contacted, probing becomes difficult below 0.05mm.
- 2. Test Pad Pitch: The minimum center-to-center test pad spacing shall be 0.15mm (6 mils).
- 3. Test Pad Height Variation: The maximum pad height variation between two pads being probed by the same probe unit (1 signal and 1 ground contact) is +/-1 mm (40 mils).
- 4. Maximum Ground Pad to Signal Pad Spacing: Ground pads shall be located within 18 mm of every signal pad and node.
- 5. Passivation Opening: The passivation or conformal coating shall be opened a minimum of 0.075 mm x 0.075 mm (3 x 3 mils) so the probes can make electrical contact with the pads. Coating thicknesses greater than 1 mil require larger openings to avoid the probe tip colliding with the coating.

# 6.7.2.2 Recommended Layout Guidelines

The recommended layout guidelines for test pads shall be as follows:

The general guidelines are to: 1) specify one test pad pitch and spacing, and 2) lay out all the signal pads oriented the same way in relation to the ground pads. Figure 6.7.B shows a typical layout with small, 0.15 mm (6 mils) pads, staggered to closely space the test pads.



0.15 mm x 0.15 mm (6 x 6 mils) pads spaced 0.25 mm (10 mils) apart

Figure 6.7.B
Typical MCM Test Pad layout

Note that in this example each signal pad has a ground pad located the same distance and location from it. This means that when probing these test pads, test engineers do not need to reposition the signal contact with respect to the ground pad each time. If possible, test pads should be grouped by signal type (i.e. all clock signals) and grounds should be marked so that power is not accidentally shorted to the ground probe. Depending on specific testing requirements, it may be desirable to lay out the test pads symmetrically about the center of the assembly, as shown in Figure 6.7.C. This is often useful when positioning probes over the entire MCM under test.

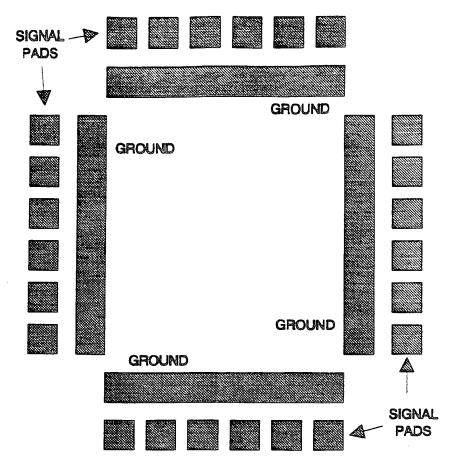


Figure 6.7.C
Test Pad Symmetry Useful for Manual Probing

If autoprobing is anticipated, it is useful to consider orienting all of the test pads the same way. Probes can then be moved anywhere on the MCM without re-orienting signal and ground, as shown in Figure 6.7.D

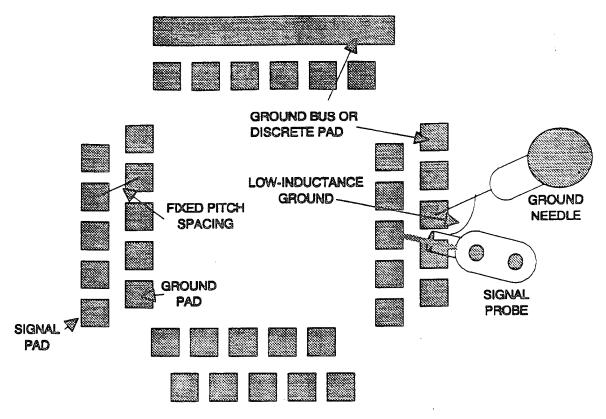


Figure 6.7.D
Test Pad Symmetry Useful for Auto-Probing

# 7.0 Documentation

# 7.1 Substrate Master Drawing

## 7.1.1 Notes

Standard notes will be embedded in all Design Start-up files for Substrate Master Drawings. Some customization may be required.

## 7.1.2 Views

Standard views along with all appropriate dimensions will be embedded in all Design Kit start-up files. Some customization may be required.

# 7.2 Substrate Artwork

## 7.2.1 Layer Masks

Design Kit start-up files include standard format and aperture and parameters assignments.

## 7.2.2 Epoxy Masks

Epoxy Mask definition is included in Cadence Standard Package models.

# 7.2.3 Solder Paste Masks

Solder Paste Mask definition is included in Cadence Standard Package models.

## 7.3 Schematic Diagram

In the event that MCM/S<sup>TM</sup> generates the schematic design files, the drawing format and detail will be in accordance with Motorola standard drawing requirements. If a customer captures and generates schematic design files and supplies netlists, etc to MCM/S<sup>TM</sup>, no further documentation is required.

## 7.4 Assembly Drawing

#### 7.4.1 Standard Notes

**7.4.1.1 Standard notes will be embedded in all Design Kits for Substrate Assembly Drawings.** Some customization may be required.

## 7.4.2. Standard Views

7.4.2.1 Standard view along with all appropriate dimensions will be embedded in all Design Kit start-up files. Some customization may be required.

## 7.5 Parts List

In the event that MCM/S<sup>TM</sup> generates the parts list, the drawing format and detail will be in accordance with Motorola standard drawing requirements. If a customer supplies a parts list, etc to MCM/S<sup>TM</sup>, no furthur documentation is required, unless MCM/S<sup>TM</sup> is required to purchase the components. In this case, the former applies.

# 8.0 CAE Interface Specifications

# 8.1 Schematic Capture

# 8.1.1 Standard Libraries

8.1.1.1 Refer to Appendix D for MCM/S™ Standard Graphical Symbols.

# 8.1.2 Cadence Concept

Cadence Concept is frequently utilized by MCM/S™ for schematic capture and netlist generation. MCM/S™ can accept schematics in Concept format and produce netlists to work with our preferred tool sets.

# 8.1.3 Mentor Design Architect

Design Architect is directly integrated with the foundry's preferred design tools. As such, MCM/S™ can accept Mentor DA or Neted schematics without difficulty.

# 8.1.4 EDIF Interchange

For schematics that cannot be supplied in Cadence Concept or Mentor DA format, the foundry can accept full graphical EDIF netlists.

## 8.2 Electrical Design Simulation

# 8.2.1 Standard Libraries

MCM/S™ utilizes the libraries of Logic Modeling Corporation (LMC) to perform digital logic, timing, and fault simulation. LMC's behavioral SmartModels, VHDL SourceModels, and LM-Series hardware models are all supported in the MCM/S™ design environment.

# 8.2.2 System HILO 4

System HILO 4 is the foundry's preferred digital simulator. SHILO4 offers digital logic simulation, fault simulation, and true dual-delay worst case timing analysis. MCM/S™ can accept GHDL netlists for SHILO4 without translation.

#### **8.2.3 SHADO**

MCM/S™ plans to utilize the SHADO simulator from GenRad for mixed mode simulation. This tool interfaces the popular ELDO behavioral analog simulator into System HILO 4.

#### 8.2.4 VHDL

IEEE 1076-compliant VHDL netlists are directly compatible with the foundry's System HILO 4 simulator, provided they utilize the STD\_ULOGIC package definition in IEEE 1164.1, and models compliant to EIA standard 567C. Foundry users are encouraged to furnish VHDL netlists along with MCM/STM-compatible schematic formats to assist in validating connectivity and schematic translation.

## 8.2.5 Quad Design

MCM/S<sup>TM</sup> utilizes Quad Design tools to perform post-layout substrate transmission line and parasitic analysis. Crosstalk analysis results are used to determine whether the substrate routing needs adjustment, and the timing effects from the transmission lines are back annotated to verify correct timing performance.

# 8.2.6 Analog Workbench and HSpice

Analog simulation is performed using a combination of Cadence's Analog Workbench and HSpice. The foundry can accept AWB design files or spice decks for use in analyzing MCM analog performance.

## 8.3 Thermal Analysis

#### 8.3.1 Standard Libraries

#### 8.3.2 Cadence Thermax

Thermax is Cadence Allegro's thermal analysis tool. Although it is not the foundry's preferred application, MCM/S<sup>TM</sup> has access to Thermax and can accept Thermax design files if furnished by the customer.

## 8.3.3 Mentor AutoTherm

AutoTherm is the foundry's preferred thermal analysis program. Although the primary supplier of this program is Pacific Numerix, it is directly integrated into Mentor and a number of other MCM design tools.

# **8.3.4 ANSYS**

MCM/S<sup>™</sup> also has access to the ANSYS finite element analysis program, and can support users with ANSYS design files.

# 8.4 Substrate Design Tools

#### 8.4.1 Standard Libraries

8.4.1.1 Refer to Appendix C for Physical Design Models.

# 8.4.2 Cadence Allegro

Cadence Allegro is the application currently utilized by the foundry for MCM substrate place and route design. MCM/S<sup>TM</sup> can accept Allegro design files for complete or partial MCM designs. One possible application for furnishing partial designs is the scenario where part placement is critical and must be controlled by the end user. MCM/S<sup>TM</sup> can accept the partially designed substrate and complete the substrate design in our environment.

# 8.4.3 Mentor MCM Station

Mentor's MCM Station release 8.2+ has been selected as the MCM/S<sup>TM</sup> foundry's strategic substrate design package. The foundry prefers to accept design files in Mentor format.

# 9.0 CAD Interface Specifications

# 9.1 Technology Files

- 9.1.1 Cadence Technology Files See Appendix A
- 9.1.2 Mentor Technology Files See Appendix B

# 9.2 Mask Transfer

- 9.2.1 Gerber Data
- 9.2.2 GDSII Data
- 9.2.3 DXF Data

# 10.0 CAM Interface Specifications

10.1 Die Bond

10.1.1 TBD\*.

10.2 Wire Bond

10.2.1 TBD\*.

10.2.2 TBD\*.

10.3 Epoxy Dispense

10.3.1 TBD\*.

## 10.4 Test Data Requirements

## 10.4.1 Boundary Scan Data Requirements

The data flow requirements to support Boundary Scan interconnect testing are shown in Figure 10.4.A. For most common Boundary Scan parts, ASCII BSDL files are available from vendors, whereas for custom parts incorporating Boundary Scan, the files must be developed by the test Engineer. In either case, the BSDL must conform to specification IEEE 11491. Using Boundary Scan Description Language (BSDL) files for each digital part type, the tester will automatically generate a program to test MCM interconnectivity using the Boundary Scan "EXTEST" instruction.

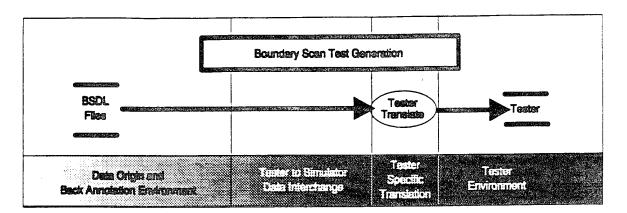
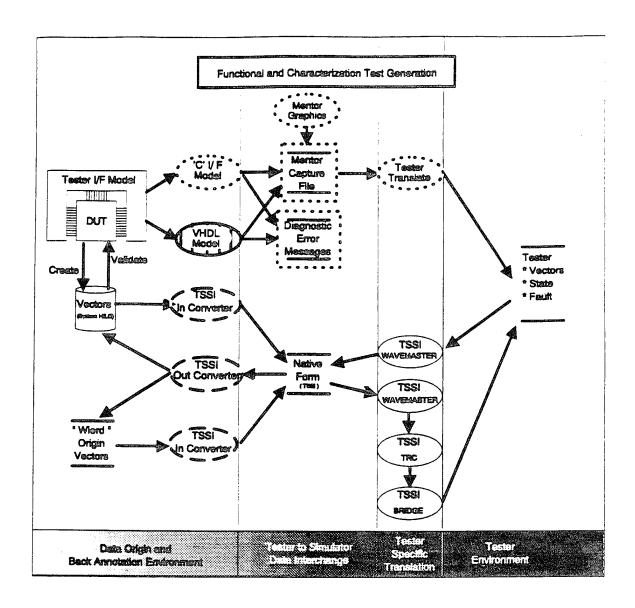


Figure 10.4.A Boundary Scan Test Data Flow

# 10.4.2 Functional and Characterization Test Data Requirements

The data flow required for functional/characterization testing is more complex, due to the large number of simulators available and the lack of a single simulator-to-tester data format. The top half of Figure 10.4.B shows a path from Mentor QuickSim to the tester. QuickSim is able to incorporate a model of the tester pin electronics into the simulation, as either a VHDL model or as a "C" interface model. Since most MCM testers directly support QuickSim, simulation results, including the effects of the tester, are then loaded directly into the tester through proprietary tester translation packages.



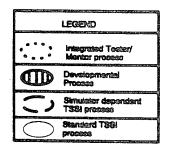


Figure 10.4.B Functional and Characterization Test Data Flow

The bottom half of Figure 10.4.B shows the more general case, where a tester does not directly support the output of a simulator, i.e. where the vectors are of a "wierd origin". To resolve this issue, simulation data is typically translated into a "neutral" format, and then translated into a tester specific format. The TSSI translation software performs this task. It can accept vectors from a wide variety of simulation packages, including System HILO4, and Mentor QuickSim/QuickFault. It then translates these into a TSSI "Native" format through a TSSI In-Converter software package, after which the data is sent through a Test Rules Checker and sent to the tester. Simulation results can be updated, as a result of timing problems uncovered during debug and checkout, by going back to the TSSI "Native" format, through a TSSI Out-Converter software package, and into the simulation data file.

# 11.0 Preferred Magnetic Media Formats

When furnishing design information to MCM/S<sup>TM</sup>, customers need to consider the compatibility of their magnetic media formats with the design tools used by the MCM/S<sup>TM</sup> foundry. MCM/S<sup>TM</sup> can accept electronic data in a variety of magnetic media formats, but the preferred formats are listed below (in order of most preferred to least).

## 0.25 inch QIC-150 (or higher) Tape Cartridge:

This tape format has been popular in the UNIX workstation market for some time now, and most workstations have access to a tape drive of this type. The preferred data format to be used on these tapes is UNIX TAR Format.

# 8mm Tape Cartridge:

The newer 8mm tape cartridges offer higher density than the older 0.25 inch cartridges but are not as common. The preferred data format to be used on these tapes is UNIX TAR Format.

#### 9-Track Tape Reel:

The older 9-Track tape formats are very common, although not as common on modern workstations. Data on these tapes should be furnished in IBM unlabeled format.

# 5.25 or 3.5 inch Floppy Diskettes:

The foundry can also accept high-density IBM-formatted floppy diskettes.

APPENDIX A

# CADENCE CAE DESIGN KIT/TECHNOLOGY FILES

MCM DESIGN KIT SUBSTRATE TYPE LYR			
TECHNOLOGY	NAME	SUBSTRATE TYPE	LYRS
MCM-L	LOFP 160	COMM/POLY	6.8
MCM-L	LQFP 160	MIL/POLY	6.8
MCM-L	LQFP 160	COMM/BT EPOXY	6.8
MCM-L	LQFP 160	MIL/BT EPOXY	6.8
MCM-L	LQFP 194	COMM/POLY	6.8
MCM-L	LQFP 194	MIL/POLY	6,8
MCM-L	LQFP 194	COMM/BT EPOXY	6,8
MCM-L	LQFP 194	MIL/BT EPOXY	6.8
MCM-L	LQFP 228	COMM/POLY	6,8
MCM-L	LQFP 228	MIL/POLY	6,8
MCM-L	LQFP 228	COMM/BT EPOXY	6,8
MCM-L	LQFP 228	MIL/BT EPOXY	6.8
MCM-L	LLCC 76	COMM/POLY	6,8
MCM-L	LLCC 76	MIL/POLY	6,8
MCM-L	LLCC 76	COMM/BT EPOXY	6,8
MCM-L	LLCC 76	MIL/BT EPOXY	6.8
MCM-L	LLCC 92	COMM/POLY	6,8
MCM-L	LLCC 92	MIL/POLY	6,8
MCM-L	LLCC 92	COMM/BT EPOXY	6,8
MCM-L	LLCC 92	MIL/BT EPOXY	6,8
MCM-L	LEC	COMM/POLY	6,8
MCM-L	LEC	MIL/POLY	6,8
MCM-C	PGA 241	MIL/COMM	NA .
MCM-C	CQFP 344	MIL/COMM	NA
MCM-C TFM	MCM TFM	TFM	5.7.9
MCM-C HTCC	MCM HTCC	HTCC	6,8.10

APPENDIX B

MENTOR CAE DESIGN KIT/TECHNOLOGY FILES

MCM	DESIGN KIT   SUBSTRATE TYPE   LYRS		
TECHNOLOGY	NAME	SOSSITURIE ITE	
MCM-L	LQFP 160	COMM/POLY	6,8
MCM-L	LQFP 160	MIL/POLY	6,8
MCM-L	LQFP 160	COMM/BT EPOXY	6,8
MCM-L	LQFP 160	MIL/BT EPOXY	6,8
MCM-L	LQFP 194	COMM/POLY	6,8
MCM-L	LQFP 194	MIL/POLY	6,8
MCM-L	LOFP 194	COMM/BT EPOXY	6,8
MCM-L	LOFP 194	MIL/BT EPOXY	6.8
MCM-L	LQFP 228	COMMPOLY	6,8
MCM-L	LQFP 228	MIL/POLY	6,8
MCM-L	LQFP 228	COMM/BT EPOXY	6,8
MCM-L	LQFP 228	MIL/BT EPOXY	6,8
MCM-L	LLCC 76	COMM/POLY	6.8
MCM-L	LLCC 76	MIL/POLY	6.8
MCM-L	LLCC 76	COMM/BT EPOXY	6,8
MCM-L	LLCC 76	MIL/BT EPOXY	6,8
MCM-L	LLCC 92	COMM/POLY	6,8
MCM-L	LLCC 92	MIL/POLY	6,8
MCM-L	LLCC 92	SOMWBT EPOXY	5. <b>8</b>
MCM-L	LLCC 92	MIL/BT EPOXY	5. <b>8</b>
MCM-L	LEC	COMM/POLY	6,8
MCM-L	LEC	MIL/POLY	6,8
MCM-C	PGA 241	MIL/COMM	NA
MCM-C	CQFP 344	MIL/COMM	NA
MCM-C TFM	MCM TFM	TFM	5,7.9
MCM-C HTCC	MCM HTCC	нтсс	6.8.10

# APPENDIX C

# CADENCE PHYSICAL SYMBOL REFERENCE

PHYSICAL SYMBOLS AVAILABLE UPON REQUEST

# APPENDIX D

# CADENCE LOGIC SYMBOL REFERENCE

LOGIC SYMBOLS AVAILABLE UPON REQUEST

## APPENDIX E MCM DESIGN PREPARATION CHECKLIST

MOTOROLA	Page 1	No.	ASEM/MCM
	Date issued:	Rev	•
Design Kit for the Application Specific Electronic Module (ASEM) Merchant Foundry	Supersedes:		
	Prepared By:		
APPENDIX D	Mike Greene		
Subject:	Approved By:		
MULTICHIP MODULE DESIGN CHECKLIST			

#### 1.0 PURPOSE

The purpose of the Multichip Module Design Checklist is to verify that all information is available so that a timely and efficient Multichip Module layout can be accomplished. Completion of the checklist supports concurrent engineering and helps prevent excessive layout cycle times due to late breaking requirements or incomplete designs.

#### 2.0 SCOPE

This SOI applies to all modules developed either as contract or commercial deliverables or under IRAD. It does not apply to breadboard circuits.

#### 3.0 REQUIREMENTS

A completed and signed off checklist is required before Multichip Module layout will begin. Activities required to support the completion of the checklist, such as, area studies and schematic capture, will necessarily start prior to the completion of the checklist.

#### **Checklist Instructions**

- 1) It is the responsibility of the Project Mechanical Task Leader or MCM Task Leader to have this form issued and completed prior to Module Design Review (MDR).
- 2) Items on this Checklist are to be reviewed by specific Team Members as indicated.
- 3) During the MDR missing or significant data shall be recorded on an action item list. These action items shall be completed prior to initiation of MCM layout.
- Once completed the Checklist shall be signed (on the last sheet of the Checklist) by the cognizant individual and all supporting data shall then be forwarded to the Pesign Supervisor or assigned MCM Designer to initiate design activities.
- 5) Changes or deviations from the initial design package require a completed Change Approval Form (See Attachment B).
- 6) Schematic entry and area study may begin prior to completion of this checklist.
- Prior to generation of Check Plots, items marked CMPL shall be reviewed and checked off by the MCM Designer, and a batch DRC must be run against the design file. All DRC errors must be resolved prior to generation of the check plots. The Designer may sign in item 34 only when the above tasks are complete.

The following checklist is to be completed, signed-off and approved prior to beginning multichip module design.

		Date		
			(MDR)	
PIA No	Work Order No	Project Name		
MCM Directory	Name			<del></del>
SCHEMATIC I	Directory Name			
DOCUMENT N	NUMBERS/DRAWING TITLES		SIZE	CLASSIF
Title				
Fab Nu	umber (84) (86)			
Artwor	rk Number (89) (90) (92)		***************************************	
Schem	atic/Logic Number (63)			
Assem	bly Number (51)			
System	n Reference Designation	(i.e., 1A1A3A, N/A	)	
PERSONNEL:		Phone	Area	
Circuit	t Designer (EE)			
MFG 7	Team Member			
RPE T	eam Member			
Test E	ngineer			
МСМ	Designer			,
Mech	Task Leader (ME)			
Config	guration Mgr	· ·		
Mater	ial Team Member			
Projec	ct Leader			
MCM	Coordinator			

(X)	<b>INPUT</b>	REQUESTED	BY
-----	--------------	-----------	----

1)	Review appropriate supplier or project MCM design guidelines.	Mfg X	EE X	ME X	Des X	[]CMPL
	Specify Guidelines:	-				
2)	What is Circuit Type:	Mfg	EE X	ME	Des	[ ]CMPL
	RF Digital Analog Highspeed Tempest Other, define					
3)	Define MCM Technology:	Mfg X	EE X	· ME X	Des X	[ ]CMPL
	MCM Laminate COB  MCM Laminate DCA  MCM Ceramic Thk Film  MCM Ceramic HTCC  MCM Ceramic LTCC  MCM Deposited  MCM C/D  MCM Silicon  Other, define					
4)	Define substrate material (s):	Mfg X	EE X	ME X	Des	[ ]CMPL
	Alumina Al Nitride Silicon Epoxy Glass (GF) Polyimide (GI) Duroid (GR) Other, define					
5)	Define Layer Structure: Define in Table 1, Sheet 14	Mfg X	EE X	ME X	Des X	[]CMPL

6)	Define integrated components:	Mfg EE ME Des []CMPL X X X X						
	778 1 1 C11							
	Thick-film resistors	(define design rules)						
	Thin-film resistors	(define design rules)						
	Thick-film capacitors	(define design rules)(define design rules)						
	Other, define	(define design rules)						
7)	Define Die/Component attach method(s):	Mfg EE ME Des [] CMPL						
	Specify by component in Table II, Sheet 15	X X						
	Wirebond Al Au Wire Size	(define method)						
	C4	(define method)						
	DCA	(define method)						
	TAB	(define method)						
	Eutectic	(define method)						
	Silverglass, Conductive	(define method)						
	Silverglass, Non-cond.	(define method)						
	Thermoplastic Non-conductive epoxy	(define method)						
	Non-conductive epoxy	(define method)						
	Conductive epoxy Non-conductive preform	(define method)						
	Non-conductive preform	(define method)						
	Conductive preform	(define method)						
	Other	(define method)						
	Other	(define method)						
8)	Supply Mechanical Definition:	Mfg EE ME Des [] CMPL						
		$\mathbf{X}  \mathbf{X}  \mathbf{X}$						
	Substrate/Module Outline	(Attach definition)						
	Substrate Camber	(define)						
	Layer Thickness <u>See Table I. Sheet 14</u>							
	Conductor Thickness See Table I. Sheet 14							
	Special Thermal Consideration Yes_ No_	(Attach definition)						
	Keep Outs Yes_ No_	(Attach definition)						
	Connector I/O	(1-6)						
	Lead Frame	(define)						
	Land Grid Array	(define)						
	Pin Grid Array	(define)						
	Other, Yes No	(define)						
		(define)						
	Seal Ring height Seal Ring thickness	(define)						
		(define)						
	Seal Ring radii	(define)						
	Seal Ring metallization Post (s) Yes No	(Attach definition)						
	Tooling holes Yes_ No_	(Attach definition)						
	Substrate Cavity Yes_ No_	(Attach definition)						
	Package Yes_ No_	(Attach definition)						
	Lid/Cover Yes_ No_	(Attach definition)						
		\						

9)	Component Placement			Mfg X	EE X	ME X	Des X	[]CMPL
	Density Analysis	Yes_ No_	N/A	(Analy area st		be perfor	med on a	all MCM's)-attach
	Dictated by Eng Determined by System (autoplace) Determined by Design		No			on)		
10)	Has Complete Technical	Data Been Suppl	lied?	RPE X	EE X	ME X	Des X	[] CMPL
	Schematic	Yes_ No_	N/A	(Schen		ered into ecked scl		ymbols)
	Symbols Checked	Yes No	N/A	Define	in Table	e II, Shee	t 15.	
		Yes_ No_	N/A	(Will s	chemati	c have an	alysis fu	nctions?)
	Parts List	Yes_ No_	N/A	(EE re	sponsibl	e for upda	ating P/L	to match design)
	Define in Table II, Sheet	15.						
	RPE Appvd.	Yes_ No_	N/A	•				ed ALL parts?)
	Physical Models Checke	d Yes_ No_	N/A	Define	in Tabl	e II, Shee	t 15.	
11)	Data Sheets supplied fro	m RPE Yes _	_ No	Define	in Tabl	e II, Shee	et 15.	
12)	Are Component Pins pre	-assigned?		Mfg	EE X	ME	Des	[]CMPL
	Connectors IC's Headers Gate Assignment	Yes No Yes No Yes No Yes No	N/A N/A N/A N/A	(defin				
	Other	Yes_ No_	N/A					
13)	Discrete Components			Mfg	EE X	ME	Des	[]CMPL
	Pull Up/Down Defined	Yes No		(defin	e)			
	Decoupling Defined	Yes_ No_		(defin	e)			
14)	Define Unused IC Conn	ections		Mfg	EE X	ME	Des	[] CMPL
	Tie High	Yes N/A						
	Tie Low	Yes_ N/A_						
	Float N/C	Yes N/A						
	Other	Yes N/A		(defin	ie)			

(X)	<b>INPU</b>	T REQ	<b>UESTED</b>	BY
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Reference Designations w	ill be assigned:		Mfg X	EE X	ME X		s []	CMPL	
Per Schematic Per Layout Exceptions	Yes N/A Yes N/A		(define	)				•	
MCM Marking		Mfg F	Œ	ME X	Des X	[](	CMPL		
Type of Application Fab No. Assy No. MFG Serial No. Date Code Tri-Graph (NSA) Trace Indent (I&T) ESDS Symbol Rev Back Ref Design Part Outlines Bar Code Bar Code Location/Type Min. Text Height Additional Marking	Yes No N/A	[ ]   [ ]   [ ]   [ ]   [ ]   [ ]   [ ]   [ ]   (define) _   (define) _	[	]				[]	Label [ ] [ ] [ ] [ ] [ ] [ ] [ ] [ ] [ ] [ ]
Specify Drawing Format  Motorola Sanitized DOD	CAGE CODE								
	Per Schematic Per Layout Exceptions  MCM Marking  Type of Application Fab No. Assy No. MFG Serial No. Date Code Tri-Graph (NSA) Trace Indent (I&T) ESDS Symbol Rev Back Ref Design Part Outlines Bar Code Bar Code Location/Type Min. Text Height Additional Marking  Specify Drawing Format  Motorola Sanitized	Per Layout Exceptions  MCM Marking  Type of Application Fab No. Assy No. MFG Serial No. Date Code Tri-Graph (NSA) Trace Indent (I&T) ESDS Symbol Rev Back Ref Design Part Outlines Bar Code Yes No Bar Code Location/Type N/A Min. Text Height Additional Marking  CAGE CODE  Motorola Sanitized DOD  MCM Marking	Per Schematic         Yes N/A	Per Schematic	NA	No.	No.	Note	No.

18)	Identify Specific Features			Mfg X	EE X	ME X	Des X	[]CMPL
	Are Thermal vias required?	Vec	No	(define)		^	Λ	,
	Plane Definition		No			I Shee	et 14)	
	Design Track Width	1 65	. 110		Outer_			ner
	Design Track Width  Design Track Spacing			(define)	Outer			nner
	Critical Signal Paths	Vac	No					
	Critical Line Length		No					
	Can track be on the outer surfaces							
	Min. Edge Clearance	: 1 CS	. 110	(define)	Outer_		Ir	ner
	Pad/Hole Size per what guidelines	:7		(define)	<b>,</b>			
	Annular Rings	,.		(define	Outer		Ir	nner
	Etchback	Yes	No	(define	Outer		Ir	nner
	Smear Removal only?		No					
	Thermal Relief required?	Yes	No	(define	)			
	Via Location Restrictions	Yes	No	(define	)			
	Via Pad DIA							
	Via Hole DIA							
	Via Thermal Relief	Yes	_ No					
	Via Distance from SM Pad							
	Via Maximum Stack							
	Via Stagger	Yes	_ No					
	Via Spiral		No					
	Via Spiral Via Staircase		_ No					
	Via Through		No					
	Via Timough Via Tenting		No	•				
	Can Via Holes be filled		No					
	or partially filled with plating?		_ No	•				
	Special Plating requirements	Yes	_ No	(define	:)(:			
	Are plating bars required?		_ No					
	Panelization	Yes	_ No	(define	:)		· ·	
	Fiducials			(define	:)(:			
	Global	Yes	_ No	•	,			
	Die Bond	Yes	_ No	(define	:)(:			
	Wire Bond	Yes	_ No	(define	;)			
	C5	Yes	No	(define	:)			
	Other	Yes	No	(define	e)(e			
	Uncovered by Dielectric mask?	Yes	No	(define	e)(e			
	Number of Fiducials			(define	e)			
	Class O ESD Parts	Yes	_ N/A	(defin	e)			
	Test Points		_ N/A	(defin	e)			
	Motorola Logo	Yes						

19)	Define Part Orio	entation (consider shadowing)	Mfg X	EE	ME X	Des X	[]CMPL
	IC's						
	Capacitors		•				
	Resistor		•	,			
	Diodes						
	Transistors		•				
	Others		(define		CH NEC	ESSAR	Y INFORMATION
20)	PAD Configura	tion for Pin 1, Polarization of	Mfg	EE	ME	Des	[] CMPL
20)	Components, D		X	X		X	• •
21)		cation Specifications Imposed	Spec. Spec. Spec. Spec.	Rev Rev Rev Rev	ME X		[]CMPL
	Mil-M-38510	Yes No					
	Mil-H-38534	Yes No	Spec.	Rev		<del></del>	
22)	Assembly Sold	Assembly Solder Techniques Required		EE X	ME X	Des	[]CMPL
	Hand	Yes No					
	Wave	Yes No					
	Vapor Phase	Yes No					
	Infrared	Yes No					
	Other	Yes No	(defin	ie)			

23)	Dielectric Mask Required - Define i	n Table I, Sheet 14	. Mfg X	EE	ME X	Des	[]CMPL
	Тор	Yes No					
	Bottom	YesNo					
	Туре	<del></del>	Liquid_				Dry
	Selective	Yes No					
24)	Solder Paste/Epoxy Mask Require		Mfg X	EE	ME X	Des	[] CMPL
	Selective	Yes No	(define	)			
25)	Allower Con Continue Managinto	Van Na	Mfg X	EE X	X	Des X	[]CMPL
25)	Allowance for Staking Materials	1 es No	(derme	)			
26)	Conformal Coating Defined		Mfg X	EE X			[] CMPL
	Тор	Yes N/A					
	Bottom	Yes N/A					
	Selective	Yes N/A	(define	)			
	Masking	Yes N/A	(define	)			
	Other	Yes N/A	(define	)		<u> </u>	
27)	Assy & Test Requirements Defin	ed	Mfg X	EE X	ME X	Des X	[]CMPL
	Tuning/Adjust	Yes No					
	Assy Heatsink	Yes No					
	Tooling Provisions	Yes No	(tool c	lamping	clear-ou	ts)	
	Alignmt. Holes	Yes No	(define	:)			
	Test Pad (ICT)	Yes No					
	Break out on all SM Pads	YesNo					

Items 28 through 33 are non-mandatory but must be considered for effect on physical design.

28)	Post Assembly							
	Acceleration	<del></del>	Mfg	EE	ME	Des	[]CMPL	
	Fixturing Available?	Yes No	X	X	X			
	Temp Cycle	Yes No	Specify	Method				
	Fine Leak	Yes No	Specify	Method				
	Gross Leak	Yes No						
	Stab Bake	Yes No						
	Burn-In	Yes No	Specify	y Method				
	BI Fixturing Available?	Yes No	Tray Id	lent or Pl	an			
29)	Manufacturing Repair Allowed?	Yes No	Mfg X	EE X	ME X	Des	[] CMPL	
							•	
	Pre Seal		•	-				
	Post Seal		Spec #	or Comn	nent			
			Mfg	EE	ME	Des	[] CMPL	
			X	X	X			
30)	Test System Identified?	Yes No	Spec #	or Plan				
,	Test Fixturing Designed &							
	Fabricated?	Yes No	Spec #	or Plan				
	Test Software In Place?	Yes No	Spec #	or Plan				
	Test Procedures In Place?	Yes No	Spec #	or Plan				
31)	Other Assembly Issues		Mfg	EE	ME	Des	[] CMPL	
31)	In Process Inspection GSI_	CSI	х	X	X		•	
	Location Kit Pre Cap							
	Other		Specif	у				
	MIL-STD-1772 Certification			-				
	Required?	Yes No						
	Qualify/Mfg to MIL-M-38510	YesNo						
	or MIL-H-38534	Yes No						
	<del></del>					_	'a	
			Mfg	EE	ME	Des	[]CMPL	
32)	Pre Seal Electrical		X	X	X			
	Test Fixtures	Yes No	_					
	Test Procedures	Yes No	Plan _					

33)	Seal Method		Mfg X	EE X	ME X	Des	[] CMPL	
	Seam Weld Solder Glass Frit Seal Preform Used Standard Process	Yes No Yes No	(define (define (define Specifi	e)	rial			
34)	DESIGNER ONLY Design Rule Check		S	IGNAT	URE/DA	TE		-

Your signature below means that, from your viewpoint, all information necessary for initiation of MCM design has been supplied. The purpose of this requirement is to minimize subsequent design changes and their impact on cost and schedule.

GN-OFF APPROVAL: Circuit Designer (EE)	DATE:
Mfg. Team Member	
Rel. Project Engineer	
Test Engineer	
MCM Designer	
MCM Coordinator	
Project Leader	
Mech. Task Leader	

# MODULE DESIGN REVIEW MULTICHIP MODULE CHECKLIST TABLE I

LAYER IDENTIFICATION

CONDUCTOR (See Note Below)  ELECT. THERMAL COND. COND TYPE (MILS) mbo/cm w/cm -					DIELECTRIC (See Note Below)						
			TYPE	FUNCTION				CONSTANT	THICK (MILS)	ELECT COND mbo/cm	THERMAI COND w/ cm - deg C
		deg C				<del></del>					
				(FRONT)							
				LAYER 2							
				LAYER 3			45				
			<u> </u>	LAYER 4			-				
				LAYER 5							
			<u> </u>	LAYER 6							
				LAYER 7							
				LAYER S							
				LAYER 9							
				LAYER 10							
				LAYER 11							
		,		LAYER 12				•			
				LAYER 13							
				LAYER 14							
· · · · · · · · · · · · · · · · · · ·			1	LAYER 15							
				LAYER 16							<u> </u>
				LAYER 17							
				LAYER 18							
				LAYER 19							
				LAYER 20							
				LAYER 21							
				LAYER 22							
				LAYER 23							
				LAYER 24							
						YES	NO	_]		,	
				LAYER 91	SOLDER PASTE (FRONT)						
				LAYER 92	SOLDER PASTE (BACK)						
				LAYER 93	EPOXY MASK (FRONT)						
				LAYER 94	EPOXY MASK (BACK)			_			
				LAYER 95	DIELECTRIC MASK (FRONT)			_			
				LAYER %	DIELECTRIC MASK (BACK)			4			
				LAYER 97	SILKSCREEN (FRONT)			_			
				LAYER 96	SILKSCREEN (BACK)						

NOTE: All ITEMS MUST BE COMPLETED IF THERMAL OR SIGNOISE ANALYSIS IS TO BE PERFORMED.								
COMMENTS:								

TABLE II COMPONENT IDENTIFICATION

<del></del>	_	_	_	_	-	_	-	_	 	T	_	_	 _	-	-	-	 	7	 _	 -	-	ı
DATA SHEET																						
BACK BIAS																						
ATTACHMENT METHOD																						
PIN 1 IDENTIFIED																						
MIN PAD PTTCH																						
PAD SIZE (MILS)																						
MASK																						
VENDOR																						
DIE SIZE AND THICKNESS (MILS)																						
PHYSICAL MODEL																						
LOGIC																						

## MULTICHIP MODULE CHANGE APPROVAL

## ASEM/MCM

		IDR app To be	roval. complete	part placement or routing by Circuit Design Engle to MCM Designer			Issue Date: Rev Attachment: Page	00-00-00 00-00-00 B 1 of 1
PROGR	AM _					_ PIA	NO	
PREPARED BY DATE Print Name								
MODU	LE NA	ME AND	NO.					_
DESCR	IPTIO!	N OF CH	ANGE(S	)		Chec	k if marked print at	tached
Impact	of Char	nge(s) on	Circuit 1	Performance, Layout, C	cycle Time	and Pro	ducibility, etc.	
Key	0 1 2		No im Minor Major	impact (layout can pro- impact (layout on hold	until revisi	elect	made (check boxes) rical/mechanical sir rical/mechanical me	nulation
DESCR	UBE IN	/PACT:						
						Esti	mate Days Held	

To be completed by MCM Designe	<b>:</b>	1	Key
IMPACT OF CHANGE(S):			
SCHEDULE			
Estimated time to make change	· · · · · · · · · · · · · · · · · · ·		
Impact on Schedule		-	
			Signature
APPROVAL			
The change(s) described above has	(have) been reviewe	ed and approved.	
Project Leader	Date	Mechanical Task Leader	Date

## Appendix D

**Reliability Testing** 

for

Liquid Epoxy Encapsulation

#### Qualification history of Dexter Liquid Encapsulation

The following report is in response to interest in Dexter Liquid Epoxy Encapsulation (LEE) for MCM's. This report outlines the testing and use history at various Motorola facilities.

#### Motorola MMTG, APAM:

APAM is a Motorola center for excellence in advanced packaging. In this capacity they have a KME automated Chip on Board (COB) assembly line. As part of this capacity APAM has developed the use of Liquid Epoxy Encapsulation using Dexter FP4451 dam material with Dexter FP4450 encapsulation. The primary aspects of the development test vehicle are:

- Substrate is .020" and .040" thick single layer BT epoxy resin.
- Devices contained nine .300" by .750" die, with a total of 2016 wires daisy chained together.
- Epoxy die bond with Ablestik 84-1 LMI SR4 silver filled conductive epoxy.
- Wirebonding is accomplished using Gold Ball Bonding with 1.3 mil gold wire.
- Encapsulation is accomplished using the liquid epoxy encapsulant dispensed over the individual die surfaces. The epoxy dam is dispensed through a capalary, heated to 35°C, to limit the flow of the liquid epoxy. The substrate is raised in temperature to 70°C during the dispensing operation. The device cure is accomplished at 125°C for 20 minutes and finished at 160°C for 2 hours.

Due to the non-hermetic nature of these devices the primary reliability concerns for the packaging technology are thermal mismatch and moisture related mechanisms. The reliability testing performed to date has been to accelerate these associated mechanisms. Eight devices were subjected to initial test. These devices were test as follows:

- Thermal cycled from -55°C to 125°C for 2000 cycles with no failures.
- Autoclave at 2 atmosphere, 121°C, with 100% RH for 144 hours with 0 failures.

Follow up tests were performed on four devices at higher thermal cycle levels and the Dexter FP648-48 was added to the test with 4 devices:

- Thermal cycled from -65°C to 150°C for 2560 cycles with the first failure at 1776 cycles for FP4450 and no failures for the FP648-48 devices
- Autoclave at 2 atmosphere, 121°C, with 100% RH for 144 hours, 2 devices each with 0 failures.

These tests are impressive for the resistance of the overmolding compound to thermally induced failure mechanisms. The autoclave test gives an indication of the resistance of the technology to corrosion. The limitation of this test is the lack of electrical bias which will greatly accelerate corrosion and with some metal/electrolyte combinations bias is absolutely necessary to induce corrosion.

#### MCC RwoH

MCC, for their Reliability without Hermeticity program (RwoH) has been testing the Dexter materials. The standard test vehicle is a ceramic quad flatpack with a Sandia test chip mounted internally. The package is then filled with the encapsulating material and placed on test. The most important testing that was done in the RwoH studies was moisture resistance testing. The tests consisted of the following:

- 85°C/85%rh testing with the chip biased to 40 volts. Last report there were no failures on the 200 devices after 6000 hours.
- Autoclave at 4 atmosphere, 140°C, with 85% RH. This test has determined a MTTF of 350 hours.

#### ASIC Division

ASIC Division of SPS has been looking into the use of Dexter FP648-48 for encapsulation of their Pad Array Carriers. Reliability evaluation of the devices has been accomplished using the H4C123 die, which is approximately .400" on a side and uses 225 wires. The reliability evaluation used 84 devices which were baked at 125°C for 24 hours, stored at 30°C and 70% rh for 48 hours. The devices were then sent twice through the solder reflow process on the belt furnace. three equal groups were formed of the original 84 devices to be subjected to the following tests:

- Temperature Cycle (air to air), -65°C to 150°C, 500 cycles
- Thermal Shock (liquid to liquid), -65°C to 150°C, 500 cycles
- Presure, Temperature, Humidity, Bias, 2 atm, 121°C, 85% RH, Static Bias for 96 hours

During these tests there was one open wire experienced during thermal shock.

#### **Boynton Beach**

Paging Division at the Boynton Beach facility is presently using Dexter FP4450 in volume production of components. They are producing 20,000 devices a week of 143 pin, .300" X .314" CMOS die on BT substrates. The LEE devices were initially qualified by testing the following regimen of tests with 100 devices per subgroup.

- Temperature Cycle (air to air), -55°C to 125°C, 1000 cycles
- Thermal Shock (liquid to liquid), -65°C to 150°C, 500 cycles
- Presure, Temperature, Humidity, 2 atm, 121°C, 85% RH, for 144 hours
- Temperature, Humidity, Bias, 85°C, 85% RH, Static Bias for 1000 hours
- Popcorn testing, storage at 130°C, 85% RH for 50 hours followed by 2 reflow cycles

No failures were noted.

## Appendix E

**Selected Suppliers List** 

for

**Known Good Die** 

# ASEM FOUNDRY LIST OF SELECTED SUPPLIERS

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#### 1.0 Introduction

This report covers major die suppliers and third party die suppliers who provide additional die testing such as lot acceptance test and hot chuck probing not often available from the original die suppliers. Also, this report provides current and updated status of suppliers in the areas of dies, standard packages and substrates. An assessment about the current and future methods of obtaining Known Good Dies is provided.

### 2.0 Summary

This report lists the selected suppliers who are providing dies, packages and substrates to build Multichip Modules (MCMs) within the Motorola ASEM Foundry. The methodology of selection of suppliers will be discussed including a current list of available die and their quality level. Also, a list of suppliers of packages and substrates will be provided along with their products. One of the major issues for MCM manufacturers is the lack of participation from major semiconductor suppliers to produce known tested dies or known good dies (KGDs). Only a very large demand in KGD will drive the major semiconductor suppliers to build a KGD infrastructure. Intel and National are the two current producers of known tested dies. Micron/Chip Supply is now the only supplier of known good SRAM die. Known tested dies are considered fully AC/DC tested dies at hot temperatures. Known good dies are currently defined as known tested dies plus die level burn-in.

## 3.0 Methodology of Selection

## 3.1 Die Suppliers

The following is a description of the attributes required of a supplier for the ASEM Foundry.

1) Vendors (from the Semiconductor Supplier List).

The Supplier List is composed of Semiconductor Suppliers and Distributors utilized by Motorola GSTG. They have been evaluated for the procurement of material, processes, and/or services. The list also includes suppliers that offer special products and particular services that are not available from major Semiconductor Suppliers.

2) Leaders in Product Technology and Process Experience

Semiconductor dies will be selected from:

- Suppliers with leading product technology demonstrated by performance and versatility
- Suppliers with proven semiconductor process technology
- 3) Technical Capabilities to provide additional testing on bare dies at temperature and at speed.

The suppliers need to have state of the art digital and memory testers that are capable of testing high lead count I/Os devices (where necessary) at high speed and at all temperatures. The tester programs need to be supported by Test Engineers who have knowledge and experience in the hardware and the software of the equipment as well as knowledge of the electrical interface issues between bare dies and testers. Test Engineers need to be supported by Application Engineers that are knowledgeable in device applications and Device Engineers that know device design and fabrication.

## 4) Availability of Physical Data

Physical data describing the die is necessary for the layout of the MCM substrates: the routing of metal lines between devices, the positioning of pins of all the devices, and the MCM partitioning of electrical and functional blocks with respect to signal layers, VCC layers and GND layers. Typical physical data are: die dimensions, bond pad location, die thickness, list of I/O pins, backside surface finish, substrate voltage (float, GND, VCC) etc. This data must be available before a supplier can be selected.

### 5) Electrical Test Data

It is not practical and economical for the ASEM Foundry to develop test vectors for complex devices such as MPUs, MCUs, DSPs. Non Disclosure Agreements between the ASEM Foundry and Suppliers will be used to protect the proprietary nature of the test vectors supplied by the die supplier and used by an outside test service.

## 6) Quality Assurance Provisions

For applications that require MIL Specifications, the Suppliers will comply with the requirements of MIL Specifications such as MIL-STD-883, MIL-H-38534.

## 7) Reliability Provisions

Reliability data such as PDA, Lifetest Data, Long Term Failure Rate, SPC Data, Historical Yield Data is used to determine whether additional testing is required to ensure Known Good Die. No further testing is needed if Reliability data show a mature product and a robust process.

## 8) Packaging and Shipping Provisions

The Suppliers will have packaging provisions to prevent damage to wafers and dies in the containers. Markings on the outside of the containers need to indicate at least the following information: supplier name, device type, quality level, wafer ID number or wafer run/lot number. Provisions against Electrostatic Damage (ESD) at workbenches and at work areas are required and need to be observed. Workers handling die must be trained and certified in ESD prevention and awareness.

## 9) Storage and Handling Requirements

The Suppliers must have procedures in place to protect wafers and bare dies from physical damage. Wafers and die must be stored in a manner, such as nitrogen, that will not cause oxidation to the bond pads. Provisions against ESD damage at storage areas are similar to provisions required at packaging and shipping areas.

## 3.2 Substrate suppliers

The following is a description of the attributes required of a substrate supplier for the ASEM Foundry.

## 1) Vendors are from the GSTG Supplier List

The Supplier List is composed of substrate and package suppliers utilized by Motorola GSTG and other Motorola sites that will be used by the ASEM Foundry. They have been evaluated for the procurement of material, processes, and/or services.

2) Leaders in Product Technology and Process Experience

Substrates and packages will be selected from:

- Suppliers with leading product technology in MCM-C and MCM-D and MCM-L Substrates.
- Suppliers with qualified and repeatable process technology.
- 3) Design Capabilities
  - Design Parameters Guidelines
  - Layout/Design Capabilities supported by CAD/CAM tools and substrates design kit to perform automated design and artwork preparation. They often include auto router, design rule checker, schematic capture, software, electronic simulation software and engineering modeling system for mechanical and thermal analysis.
  - Design transfer system for GDSII, ASCII, DXF, EDIF, GERBER files and others.
  - Product line Portfolio
  - Technology Roadmap: processes, material, improved design parameters and updated/compatible CAD/CAM tools.
- 4) Manufacturing Capabilities
  - Number of substrates or wafers produced per week
  - Process capabilities controlled and driven by CAD tools
  - Design for manufacturablility
  - Manufacturing/Assembling sites in the U.S.
- 5) Product Testing
  - System testing of substrates for surface leakage, interlayer short and open, capacitance and resistance
  - Evaluation and analysis capabilities for Material Evaluation, Material Development and Failure Analysis

 Test and qualification processes applicable to commercial, industrial and military requirements

## 6) Quality Assurance

- Processes controlled and driven by SPC
- Certification of operators and calibration of equipment
- Documentation of material, products and processes.
- Qualification test and acceptance test
- Final inspection
- Statistical data base to control design parameters using processing parameters, operator parameters and equipment parameters

## 7) Cost and Cycle Time Reduction Plans

- Continuous cost reduction plan through elimination of rejects and defects
- Cycle time reduction through consistent, repeatable and defect-free processing steps
- Cycle time reduction through tuned and standardized processes
- 8) Additional Information if required.

## 3.3 Package Suppliers

Package Vendor Selection Plan

- 1) Vendors are from the supplier list. The supplier list is composed of package suppliers utilized by Motorola GSTG. They have been evaluated for the procurement of material, processes and/or services. The list includes suppliers that offer special products and particular services that are not available form major package suppliers.
- 2) Leaders in Production Technology and Process Experience. Packages will be selected from:

- Suppliers with leading product technology in packages
- Suppliers with qualified and repeatable processes.

## 3) Design Capabilities

- Design Parameters Guidelines
- Tight control of design parameters and dimensions
- Layout/Design Capabilities supported by CAD/CAM tools. They often include auto router, design rule checker, schematic capture software, electronic simulation software and engineering modeling system for mechanical and thermal analysis.
- Design transfer system for DWG, IGES, GERBER files and others with high speed modems.
- Product line Portfolio: PGAs, high lead count packages, PACs, ceramic MCM packages, high power dissipation packages.
- Technology Roadmap: processes, material, improved design parameters and updated/compatible CAD/CAM tools, high destiny ceramic and low cost plastic.

## 4) Manufacturing Capabilities

- Number of packages of each type produced per week
- Process capabilities controlled and driven by CAD tools
- Integrated processes from start to finish
- · Design for manufacturablility for easy electrical test and assembly
- Manufacturing/Assembling sites in the U.S.

## 5) Product Testing

- System testing of packages for surface leakage, short, inductance, capacitance and resistance
- Evaluation and analysis capabilities for Material Evaluation, Material Development and Failure Analysis

 Test and qualification processes applicable to commercial, industrial and military requirements

## 6) Quality Assurance

- Processes controlled and driven by SPC
- Certification of operators and calibration of equipment
- Documentation of material, products and processes.
- Qualification test and acceptance test
- Final inspection
- Statistical data base to control design parameters using processing parameters, operator parameters and equipment parameters

## 7) Cost and Cycle Time Reduction Plans

- Continuous cost reduction plan through elimination of rejects and defects
- Cycle time reduction through consistent, repeatable and defect-free processing steps
- Cycle time reduction through tuned and standardized processes

## 4.0 List of suppliers

## 4.1 Die Suppliers

Most of the following suppliers sell commercial or bare dies that are DC tested at wafer level and at room temperature. Only IBM has a long history and experience with known good dies as flip-chips for the C4 (Controlled Collapse Chip Connection) technology and has sold them within their company. Micron supplied military SRAM and DRAM dies as KGDs (M3 level) but recently sold this business to Chip Supply. Intel supplies flash EPROMs, Microcontrollers and Microprocessors as known tested dies. National just announced its Known Good Die business at the International Conference on Multichip Modules in Denver, CO April 14 - 16, 1993. Most successful users of MCMs that used KGDs have been mainframe computer companies (IBM, UNISYS, DEC, Honeywell/NEC, Hitachi and Fujitsu) and high production telecommunications

companies (AT&T) that are vertically integrated. Other companies such as Hughes and Rockwell used KGDs in their hi-rel MCMs. Through full DC and AC testing of bare dies as flip-chips or TAB (tape automated bonding) chips, these companies obtain Known Good Dies and achieve reliable commercial and military MCMs. The following semiconductor suppliers and third party die suppliers provide dies for various applications of MCMs.

#### **AMD**

AMD supplies flash memory dies:

Am28F256-XC/3	32K X 8	200ns	12 V ERASE VOLTAGE
Am28F512-XC/1	64K X 8	200ns	11
Am28F010-XC/4	1M(128K X 8)	200ns	H
Am28F010A-XC/5	1M(128K X 8)	200ns	11
Am28F020-XC/1	2M(256K X 8)	200ns	11
Am28F020A-XC/2	2M(256K X 8)	200ns	
Am29F010-XC/3	1M(128K X 8)	120ns	5 V ERASE VOLTAGE

Die are AC/DC tested at wafer sort to guarantee full device functionality over commercial or military temperature ranges. All the AMD dies listed above will be available by 1Q 94.

#### AMI

AMI supplies ASIC gate array, standard cell and Programmable Logic Devices (PLD) dies and performs Lot Acceptance Test on packaged dies from the same wafer lot. Dies are DC and function tested at wafer level and at room temperature.

#### **Analog Devices**

Analog Devices (AD) supplies flash A/D, A/D converters, D/A converters, Sample/Hold, and DSP dies:

8-bit 20 MHz Flash A/D	AD9002,AD9012,AD9048
8-bit lo-cost A/D	AD570,AD571,AD670
8-bit lo-cost DAC	AD9700,AD9701,AD9703
	AD557,AD558,DAC08,DAC1408,DAC8888
16-bit lo-cost A/D	AD7703BCHIPS
16-bit lo-cost DAC	AD1861,AD7846ACHIPS
8-bit Sample/Hold	AD9100,AD9101
<del>-</del>	AD582SCHIPS,AD585SCHIPS

16-bit Sample/Hold DSPs

SMP10NBC,SMP11NBC AD1154 ADSP2101K-40,ADSP2100AJ, ADSP2103K-40,ADSP2111K-52, ADSP2115K-40

AD will provide physical information such as die size, backside, glassivation and special handling. Device electrical characteristics such as junction temperature and substrate voltage are available. Spice Models are available on individual cases. Access to GDS II files is pending. Wafer yield on each device type will not be available but large quantity orders will motivate AD to change position. Most of the dies are DC tested at wafer level and at room temperature. Some dies will be DC tested at high temperature with additional NRE cost of \$ 10K minimum. For DSP devices, AC testing (speed sorting) will be at room temperature.

#### Atmel

Atmel supplies bare FPGA and EEPROM dies. EEPROM dies are 100% tested in wafer form. Atmel's EEPROM sort testing incorporates functional and parametric tests. A typical test flow consists of basic DC parameters such as ICC and input leakage, and AC switching parameters. Data pattern testing is included to guarantee the functionality of each bit and to guard against pattern sensitivity. Several oxide stress tests are introduced to reduce the likelihood of infant mortality failures. The data retention bake is included to ensure the integrity of the core cell oxide. A final quality assurance test is performed on each assembly lot and consists of subjecting a sample of the dies ready to ship to electrical tests.

AT29C040 die as 512K X 8 will be available by third quarter 1994

#### The list of EEPROM dies are:

AT28C16	2K X 8	
AT28C64	8K X 8	
AT28PC64	8K X 8	PAGE MODE
AT28HC64L	8K X 8	HIGH SPEED
AT28C256	32K X 8	150ns
AT28HC256L	32K X 8	70ns
AT28C010	128K X 8	120ns
AT29C040	512K X 8	150ns

## Chip Supply

Chip Supply is a third party die supplier. Dies are in TAB, CoDc (Chip on Device carrier), bumped dies, Softab and Softool. CoDc or chip on substrate consists of permanently attaching a die to a ceramic substrate that extends 30 mils on each side of the die; the die is then wire bonded to the substrate which is temporarily attached and wire bonded to a test carrier. Softab uses a new process to temporarily bond the lead tape to the gold bumped pad. The Softool KGDPlus process was obtained from Micron through a licensing agreement. It consists of assembling the die in a ceramic package with temporary die attach and temporary wire bond. The unit will go through standard testing and burnin using existing equipment. All the four carrier methods allow 100% DC/Functional/AC (speed) tested, over temperature tested and 100% burned-in but require NRE costs. Lot acceptance test is also available.

Chip Supply does not offer Intel dies.

Chip Supply offers dies or dies attached to TAB or SofTAB. The list is updated in our list of dies.

## **Cypress**

Cypress offers commercial and military dies: SRAMs, PROMs, PLDs, FIFOs, Sparc Processor, VME Interface chips and Programmable clock buffers. Dies are DC and function tested at wafer level and at room temperature. They are either bumped dies or TAB dies. Lot acceptance test is available.

#### Elmo

Elmo is a third party die supplier. Elmo is performing AC hot chuck probed at wafer. Elmo is also developing a die carrier similar to the CoDc process of Chip Supply; The die carrier is temporarily attached and wire bonded inside a ceramic package which can be sealed. The unit will go through standard testing and burn-in using existing equipment. Another process is being experimented and consists of depositing a proprietary layer of about 2 mils thick on top of the chip. This layer allows Elmo to enlarge and reinforce the bonding pads without causing chemical and physical damage to the die itself. Again, the die is temporarily attached and wire bonded to a ceramic package that will go through standard testing and burn-in using existing equipment. Lot acceptance test is also available.

Elmo does not offer Intel and National dies.

Elmo offers five(5) levels of tested dies(KGD) with following main features: standard, hot chuck probed and burnt-in.

#### **EPI**

EPI is another new third party supplier and supplies KGDs with a process called EPIK.

#### Harris

Harris offers KGDs as Intelligent Power Products(IPP). They are fully AC/DC tested at speed. Dies are DC at probed at multiple temperatures. DSP and ASIC dies are in tape carriers. They are AC/DC tested at speed and temperature, and burnt-in. Harris also does lot acceptance test.

#### **IBM**

IBM had a long history and successful experience with Know Good Dies using the C4 process. Current list of KGDs is pending.

#### IDT

IDT offers ECL, FIFO, LOGIC, RISC(32-bit and 64-bit), SRAM, dual port RAM, complex logic, and Speciality Memory KGD dies. Options are: commercial, industrial and military flows.

IDT used a temporary packaging method to produce KGDs. The method consists of the following main steps:

\_deposit a layer of gold (Au) on the bonding pads. The wire bonds will be temporarily bonded and will be removed with low stress according to IDT after completion of electrical test and burn-in test

\_temporarily bond the die to the package with thermo-plastic and it will be removed after final electrical test.

IDT can perform electrical test on dies over military temperature range.

#### Intel

Any Intel Product is a candidate for bare die. Known Tested Die is sorted with full AC/DC testing between 0 to 85 degrees C junction temperature and has a new name as SmartDie. Data package of Intel SmartDies are available and includes physical and mechanical information. Test vectors are available for a fee and a non-disclosure agreement must be signed. A Product Assessment that includes infant mortality (DPM data) and long term reliability (FIT rate) information is available upon request for KGD products with a non-disclosure agreement.

#### Flash EPROM dies are:

28F010/90ns

1M (128 K X 8)

28F020/90ns

2M

28F200BX

2M (256K X 8 or 128K X 16)

28F008SA/120ns

8M (1M X 8)

28F400BX/90ns

4M (256K X 16 or 512K X 8)

### Microprocessor dies are:

80386SX/33MHz 80386CXSA/33mHz 80486SX/25MHz 80486DX2/40MHz

and **Pentium** processor

#### Microcontroller dies are:

8XC51SLAX/16MHz 80C196NPX/40MHz

#### Lattice

Lattice offers one PLD die : the ISP LSI 1032 is DC and function tested at wafer level and at room temperature.

### Maxim

Any Maxim Product is a candidate for bare die. All dies are 100% electrically probed. Most parameters tested are checked to limits that are more stringent than the data sheet worst case parameters. Generally, the parameter limits listed in the packaged unit data sheets are tested during electrical probe. Some parameters are impossible to test with absolute accuracy on bare die but information regarding any of the parameter limits will be available from Maxim.

#### Micron

The KGDs have 4 quality levels: C1, C2, C3 and C7 and can support commercial and military MCMs. Micron's C1 flow is designed to meet requirements for the lowest cost when a guaranteed speed is not required. The C2 flow allows Micron to guarantee the hot chuck probed access speed ( $t_{AA}$  or  $t_{RAC}$  and  $t_{CAC}$ ) of the die to the speed grade selected by the customer; cell margin and parameter characteristics are probed.

The C3 flow includes speed sort, cell margin and parameter probe and burn-in. The C7 is (C3 + stress test)

#### National

National offers a list of 84 standard KGDs. The dies include FACT logic, SCAN logic families and SRAMs. Five options are offered to fit various customer needs and technology requirements. Option 1 dies see 100 % DC Wafer sort at room temperature and 100% Visual inspection. Option 2 is Option 1 plus Lot Acceptance Test. Option 3 dies see 100% AC/DC Sort at 25 degrees C and 125 degrees C, 100% Visual inspection. Lot Acceptance Test is optional. Options 1,2 and 3 are applicable to products built from mature manufacturing processes. Option 4 offers the highest quality level of National KGD dies; it has 100% die level test at all temperatures and burn-in. NSC recently adds 3 KGDs SRAMs: 128KX8, 256KX4 and 512KX8.

Die Supply Information includes BDSL model, Spice models, GDS II, Device characteristics(i.e., Theta, backside V, etc.), Structural information (i.e. backside metal, passivation, etc.), Radiation tolerance, Vector sets, etc...

# **Quicklogic**

Quicklogic supplies FPGA (Antifuse) wafers built by Cypress and VLSI Technology Inc. Quicklogic has been flexible but a die business has not been announced yet. Should they do so they will be reviewed for inclusion into this list.

## Samsung

Samsung will offer memory bare dies and known good dies with burn-in using gold bumps over bond pads.

### Semi Dice

Semi Dice is a new third party supplier and supplies KGDs

#### TI

TI has just announced its KGD program called FlexS/Die.

This program provides commercial and military processing options such as Standard Wafer Sort(KTD), Commercial Temperature Processing(C-KGD), and Military Temperature Processing(M-KGD). Initial KGD offerings from TI are DSP 320 C40 and 1MX4 DRAM.

### Triquint

Triquint offers ASIC GaAs wafers but a die business has not been announced yet. The will be reviewed again if a die business is announced.

### **UTMC**

UTMC offers ASIC gate array dies and performs Lot Acceptance Test on packaged devices from the same wafer lot. Dies are DC and function tested at wafer level and at room temperature.

#### Vitesse

Vitesse offers ASIC GaAs wafers but die business has not been announced yet. They will be reviewed again if a die business is announced.

#### Xilinx

Xilinx offers FPGA dies: XC2064, XC3020, XC3090, XC4005, XC4008, XC4010 and XC4013. Third party die suppliers will perform frequency testing and lot acceptance test to meet customer requirements.

# Chip Capacitor and resistor suppliers

1) Capacitor: ATC, AVX and MURATA

2) Resistor: Mini-Systems, Semi-Films and State of the Art

# 4.2 Package Suppliers

The package suppliers are: Kyocera, Coors and General Ceramics. The ceramic packages are: PGA, and QFP. Coors, General Ceramics and Kyocera build custom Pad Array Carriers (PAC), high lead count packages such Ceramics Quad Flat Package (CQFP) with 344 leads and Pin Grid Arrays (PGA) with 351 leads. They all have modeling capabilities and on-site design centers in US. Kyocera built Ceramic QFP and Ceramic PGA packages for Motorola. Motorola ASEM offers laminate QFP and leaded chip carrier laminate(LLCC). LLCC is

comprised of J-bend leads on four edges of the MCM-L substrates.

## 4.3 Substrate Suppliers

The available substrates for MCM in this report are:

- 1. MCM-C low temperature cofired ceramic (LTCC)
- 2. MCM-D deposited organic thin film
- 3. MCM-L high density laminated substrate

Standard laminate substrates with 6 and 8 layers are offered with various sizes from 1.7"X1.7" to 3.1"x3.1". The supplier of these substrates is ACSIST

### 4.3.1. MCM-C

The suppliers of MCM-C substrates are Kyocera, Coors and General Ceramics. They are the same suppliers as described in section 4.2. MCM-C is a cofired ceramic substrate technology which is an extension of single chip ceramic packages.

Main characteristics of ceramic substrates are:

- Mature and proven technology
- High dielectric constant and high signal line resistance due to the tungsten metal line
- Strong and inert to environment exposure
- High number of interconnect layers

The substrate can be easily designed as a hermetic package using a seal ring around the periphery.

#### Coors

Coors Electronic Package entered the multilayer ceramic business in the mid to late 1960s. Coors manufactures finished cofired ceramic substrates as well as base ceramic substrates for thin film deposition. Hermetic packages are also available. The substrate materials are: alumina, aluminum nitride, low K glass/ceramic. The substrate size is  $130 \times 160$  mm. The conductor material uses refractory metal: tungsten (W) or Mo and Au and barrier metallization uses Ni + Au. Conductor width is  $100 \ \mu m$  minimum, thickness is  $18 \ microns$ 

and pitch is 200 microns minimum. Via spacing is 0.2 mm but .6 mm is preferred. The I/O capacity is 50,000 + vias per layer.

### **Kyocera**

Kyocera America, Inc. was founded in 1959 as the world's largest manufacture of ceramic IC packages. In 1969, Kyocera entered the cofired ceramic business. Since 1982, Kyocera has been supplying finished substrates for thin film multichip modules. Kyocera has supplied alumina and aluminum nitride since 1990. In the past two years, Kyocera offered glass ceramic substrates. Kyocera also offers design assistance, substrate testing, and enclosures. The substrate materials are: alumina, mullite, aluminum nitride, LTCC. Substrate size is  $225 \times 225 \text{ mm}$  (alumina) and  $102 \times 102 \text{ mm}$  (other materials). The conductor material is Tungsten (W) Barrier metallization uses Cr. Number of layers is about 30 microns, thickness is about 3-5 microns and pitch is about 75 microns. Via spacing is about 152 microns.

#### **General Ceramics**

General Ceramics built HTCC substrates for KOV5 program at GSTG. The design rules for the above substrate are:

- -92% minimum aluminum oxide with dielectric constant of 8.9.
- -4 mil diameter vias
- -8.9 mil via centerline spacing
- -5 mil circuit lines
- -5 mil circuit isolation
- -5 mil power/ground plane grid
- -4 mil minimum tape layer thickness
- -circuit metallization will be refractory tungsten

General Ceramics also performs 100% electrical verification of all circuit elements.

#### 4.3.2. MCM-D

The suppliers of MCM-D substrates are identified as MMS, nChip and IBM. As of this date no supplier has selected. Selection and qualification are expected to occur by 4Q93.

#### **MMS**

Micro Module Systems built copper/polyimide high-density interconnect on low-cost 150 mm aluminum, silicon or ceramic wafers using semiconductor photolithography, plating, and a sputtering process.

Substrate material is depended upon customer requirements. Typically, aluminum is used for wire bond and TAB assembly. Silicon is used for flip chip and ceramic for hermetic applications. Substrate products are MMS-D200, MMS-D300 and MMS-D500. For example, the MMS-D500 is a four metal layer substrates consisting of four copper/polyimide layers on aluminum on five copper/polyimide layers on silicon or ceramic.

In a RISC workstation, MMS increased clock speed from 40 MHz to 55 MHz using silicon substrate. A MCM-D Design kit is available and works with Mentor Graphics tools. According to MMS, its MCM-D substrates offer high density lines and VIAS, low inductance power distribution, built-in power bypass capacitance, excellent signal integrity and choice of substrate starting materials.

### nChip

n Chip offers three substrates also described as silicon circuit board nC1000 series, nC2000 series and nC3000 series. According to nChip, the silicon base substrate has good characteristics such as high thermal conductivity, good thermal expansion match and good manufacturability. A typical nC1000 series has two sputtered aluminum layers of about 2 micron thick each. The silicon dioxide insulator is 7 micron thick and has characteristics such as good thermal conductivity. It is also a low expansion and stress controlled material with negligible moisture absorption. The chip is attached to the silicon substrate with re-workable and thermally conductive adhesive. The target application of nChip products is from less than 100 MHz to about 500 MHz. The metallization system can be either sputtered aluminum or electroplated copper. The other characteristics of nchip substrates are: low permeability to gases and ionic contaminants, chemical inertness and controlled fabrication processes.

#### **IBM**

IBM has built and used multi-layer thin film (MLTF) in its midrange and mainframe computers which operate at clock rates of 50 to 125 MHz. Recently, IBM has developed a high wiring density MCM-D substrate. It consists of one plane pair of copper/polyimide thin films (two signal planes, and two

power/ground planes) on silicon, alumina or glass ceramic substrates. The copper/polyimide interconnect uses a non-planar conformal via process. The vias are defined by photosensitive polyimide photolithography and the conductors are defined by pattern electroplating, The wiring pitch and width are approximately 25 microns and 10 microns. According to IBM, this MCM-D thin film will be used in computer systems, telecommunication products, avionics and other applications both within IBM and outside. The improvements over the old MCM-D substrates by IBM are: options for alumina or glass ceramic carriers, copper for improved resistivity and photosensitive polyimide for process simplification of via definition. This substrate can be used with device interconnection technologies such as C4, TAB, wire bond, and industry card level interconnections.

### 4.3.3. MCM-L

The list of selected substrate suppliers and their key design rules includes:

### ACI

Currently is supplying MCM-L with .005 line width / .006 spacing and projecting .003 line width / .004 spacing in the near future. They are drilling .012 holes with .010 holes in the development stages with aspect ratios of 6:1 and 10:1 projected. ACI is on our ASL as an approved supplier and has supplied the MCM-L on the KOV5 program in both Kevlar and Thermount materials.

### **ACSIST**

They are currently supplying MCM-L to various customers utilizing blind and buried vias and buried resistors on advanced laminates. They are fabricating with .003 line width and spacing, and drilling at .010 with .008 studies inprocess. They are doing 10:1 aspect ratios with bondable gold capabilities. ACSIST is also on our ASL on a restricted basis because of limited orders at this time.

### DAISHO DENSHI

They are supplying MCM-L substrates to Motorola's Austin APDPL facility; also, they are building for Codex and Automotive Systems in Chicago. They are drilling .010 via holes and can achieve up to a 20:1 aspect ratio. They can produce .004 line widths and .005 spacing on Polyimide and BT materials. They also provide a wire bondable gold surface finish. All product is

manufactured in Japan.

#### **IBIDEN**

Supplies MCM-L with .004 line width and spacing and can drill up to an aspect ratio of 20:1. They can drill a .012 finished hole size and have the capability of multilayer, stepped cavity construction. Boards are manufactured in Japan; Motorola Austin has been experiencing delivery problems with MCM-L.

### CHARACTERISTICS OF MCM-L SUBSTRATES

Substrates used in current MCM-L assemblies are mainly in the Polyimide family. FR4 is used but is frequency restricted; BT/Epoxy is also used. Some of the new materials being mentioned in the industry are Thermount and Kevlar.

 Polyimide (GI) material is currently the most used material in the fabrication of MCM-L because of its low cost and ability to achieve wire bonding or flip-chip bonding. Conductors are almost always copper and can be deposited additively or are part of the printed board subtractive process. MCMs made of this material are readily available from PWB suppliers and can be manufactured by established processes and procedures.

There are limitations imposed by the dielectric constant of the material as well as the availability of thin dielectric's for impedance control. MCM-L on GI material is currently being done on a production basis at 4 mil lines and 5 mil spaces.

- 2) Epoxy substrates (FR4) are also used frequently in fabricating MCM-Ls and have basically the same properties as Polyimide as far as being readily available and made using established processes and procedures. They are limited as to frequency application and have Dk values in the range of 3.5 to 5.2. Woven Glass can result in dimensional repeatability problems and thickness limitations. This substrate is very sensitive to both deformation in glass weave and changes in resin content which causes variation in Dk values across the board. FR4 has a poor TCE match to silicon and has poor to fair wire bond ability performance but is the lowest in cost.
- 3) BT/Epoxy substrates have good dimensional stability that offers consistent repeatability in registration of layer count from panel to panel and lot to lot. Low Z-axis expansion of B/T Epoxy provides for better plated-through reliability, especially during temperature fluctuations at systems levels. Although not as good as GI material for Tg, it is superior

to the standard FR4 epoxy system. It has an improved Dk compared with GI material that allows printed circuits with higher speeds to be built on thinner boards. B/T has good thermal resistance to aid in repair and shows good resistance to copper plate cracking in plated-through, blind and buried via holes. It also has low moisture absorption characteristics; whereas Polyimide has high moisture absorption. B/T is cheaper than the GI material and is in the cost range of standard FR4 material.

- 4) Thermount is a relatively new material made from short, random Kevlar fibers with an aramid binder using a multifunctional epoxy or Polyimide resin system among others. It is available in 3 mil thicknesses with good dimensional stability. Thermount has a lower dielectric than GI substrates and has a smoother surface for finer line applications. It also is reduced in weight for aerospace and avionics applications and has drill wear equal to or better than FR4. Cost of the Thermount is substantially less than Kevlar but is only slightly more than Polyimide / E glass and is currently available on a limited basis.
- 5) Cyanate Ester is rated by some as the substrate material of choice for high complexity, high layer count where its low dielectric constant is of value. Lower Dk materials permit impedance requirements to be met with thinner individual spacings than possible with substrates like FR4 or GI, it also helps reduce crosstalk if lines are closely spaced. With a Dk of 2.8, Cyanate Ester will meet all these needs. Nothing is free; Cyanate Ester products exhibit low melt viscosity and require detailed process controls for consistent manufacturability. This substrate resin system is very sensitive to moisture. It has a predictable dimensional stability low Z axis expansion as well as resistance to degradation when subjected to thermal changes.

# 5.0 Supplier Data Summary

The following tables highlight the key features of dies, packages, and substrates that have been discussed in the main report.

# **DIES**

FAMILY	VENDOR	PART NUMBER	BARE DIE <sup>1</sup>	KNOWN TESTED DIE2	KNOWN GOOD DIE <sup>3</sup>
Logic					
	Motorola	FACT	X		
	National	FACT	х	Х	X
	11	FACT Quiet	Х	X	Х
	TI	FACT	х	X	
	11	BCT	X	x	
	National	SCAN 18245T	X	x	X
	**	SCAN 18373T	X	X	X
	11	SCAN 18374T	X	x	X
	11	SCAN 18540T	X	X	X
	11	SCAN 18541T	X	x	X
	11	SCAN PSC100F	X	X	X
		SCAN PSC110F			
	National	100K 300 Series ECL	X	X	X
Memories					**************************************
1MEG SRAM	Micron	MT5C1008	x	x	Х
128K x 8		12-20ns	:		3
		*4 types of 1MEG	х	X	X
		SRAM	,		
		*17 types of memory configurations			1
`		*Byte Write and Read			
		Control	-		
		*5V and 3.3V Power			
		Supply			
	National	NS41024	х	X	Х
	11001101	15-35ns	-1	43.	-1
256Kx4	National	NS41028	х	х	X
		15-35ns			
	Motorola	MCM6226A	х	3Q94	

4MEG SRAM	Mot/Chip	MCM6246	X	х	x
512Kx8	Supply	in TAB and			
		SOFTTAB			
		20-30ns			
	National	NS41096	Х	X	X
32Kx9	Motorola	MCM62110		3 <b>Q</b> 94	
1MEG	IDT	IDT71024	X	х	

256K	IDT/Chip	IDT71256	Х	Х	Х
20011	Supply	also in TAB and			
	Juppey	SOFTAB			
4MEG	Micron/	MT4C16257	Х	х	X
DRAM	Chip	SOFT and SOFTTAB			
256Kx16	Supply	60-70ns			
4Mx1	Micron/	MT4C1004	х	X	Х
	Chip	60-80ns			
	Supply				
1M x 4	Micron/	MT4C4001J	X	х	X
DRAM	Chip	60-80ns			
	Supply				-
Flash	Intel	28F010	x	x	
EPROM		/90ns			
		28F400BX/80ns	X	X	
		28F008SA/120ns	x	X	
		28F020/90ns	x	x	
		28F001BX/70-120ns	x	x	
		28F400BX/80ns	х	X	
EEPROM	ATMEL	AT28C16	X		
		AT28C64	Х		
	11	AT28PC64	X		
	11	AT28HC64L	X		
	11	AT28C256	X		
,	11	AT28HC256L	X		
	11	AT28C010	X		
Digital					
Signal				1	
Processor					
	Motorola	DSP56156	х	3Q94	
	11	DSP96002	х	3Q94	
	TI	TMS320C30	х	х	x
	ft.	TMS320C40	X	х	X
	Analog	ADSP21xx	х		
	Devices	Series			

Micro- processor					
	Intel	80386SX/33MHz	х	х	
	"	80386SCXSA/MHz	x	x	
		80486SX/25MHz	x	х	
	11	80486DX2/40MHz	X	X	
	Motorola	MC68020	Х	4 <b>Q</b> 94	

	11	MC68040	х	4 <b>Q</b> 94	
Microcontroll					
er					
	Intel	8XC51SLAX/16MHz	X	X	
		80C196NPX/40MHz	x	X	
RISC					
Processor					
	AMD/ Chip Supply	CSAM29050-A 25MHz	х	<b>X</b>	x
	Motorola	MC88100/88200	X	4Q93	3 <b>Q</b> 94
ASIC					
	Motorola	H4C	х	1 <b>Q</b> 94	4 <b>Q</b> 95
FPGA					
	ATMEL	SRAM	X		
	Xilinx	XC2064	X		
	11	XC3020	x		
		XC3090	X		
		XC4003	X		
·		XC4005	X		
		XC4006	X		
		XC4008	X		
	Xilinx/ Chip Supply	CSXC4010-A 507x496.5mils	х	х	х
		XC4013	X		
		XC2018	X		
PLD			•		
	Lattice	ISP LSI 1032	X		

### **PASSIVES**

CAPACITOR: Values range between 0.1pf and 0.33uf. RESISTOR: Values range between 1 ohm and 2.5M ohm.

#### Notes:

1. Bare Die: 100% die probe at 25°C to full functional and DC limits.

2. Known Tested Die: 100% die probe over a temperature range of 0°C to 25°C o full functional, AC, and DC limits.

3. Known Good Die: 100% die probe over a temperature range of 0°C to 125°C to full functional, AC, and DC limits. In addition a die level burn-in is performed.4. Die of different types and quality levels can be purchased from the following list of suppliers: AMD, AMI, Analog Devices, ATMEL, Chip Supply (3rd party), Cypress, ELMO (3rd party), Harris, IDT, Intel, Lattice, Maxim, Micron, Motorola MPO, National, TI, Triquint, Vitesse and Xilinx.

# **PACKAGES**

STANDARD PACKAGE O.D.	MATERIAL	PACKAGE ATTACH	PITCH (MILS)	LEAD COUNT
LLLC 29.5X29.5mm 35.3X35.3mm  JEDEC Outline MO-047	Laminate	Surface	1.27mm 1.27mm	76 92
CQFP  40X40mm 52X52mm 60X60mm  JEDEC Outline MO-148	Ceramic	Surface	.65mm .65mm .65mm	224 296 344
LQFP  40X40mm 50.2X50.2mm 58.7X58.7mm 70.5x70.5mm  JEDEC Outline MO-089	Laminate	Surface	1.27mm 1.27mm 1.27mm 1.27mm	108 140 160 204

Custom packages can be developed for additional NRE charges

# **SUBSTRATES**

SUBSTRATE TYPE	SUBSTRATE SIZE (INCHES)	MINIMUM METAL WIDTH/ SPACE (MILS)	MINIMUM VIA DIAMETER (MILS)	MAXIMUM NUMBER OF INTER- CONNECT	DIELECTRIC CONSTANT
MCM-L	1 by 1 (min.) 12.4 by 16.4 (max.)	3/4	8	LAYERS 20	3.5 - 4.5
MCM-C	2 by 2.4 (min.) 5.5 by 6 (max.)	3/5	3	50	9.5
MCM-D	1 by 1 (min.) 5 by 5 (max.)	1/2	1-2	6	3.0 - 3.5

### 6.0 Conclusion

More major semiconductor suppliers such as IBM(C4), IDT, Intel, Micron, Motorola, National, Samsung and TI are supporting the Known Good Die business. More new probe card technologies and materials have been developed (MMS, Hughes and others) to support electrical testing and burn-in of die at high temperature. There is interaction between die users and die suppliers through EIA, MCC, SEMATEC meetings and technical conferences. Membrane probe card, temporary die carrier, Softool, Softab, chip on substrate, and TAB methods are being used to produce Known Good Die. These methods allow to test and burn-in dies and adapt to high volume by using existing equipment. Wafer level burn-in method is the future method to obtain high quantity of Known Good Dies but one of the technical obstacles is the ability to establish and maintain electrical contact between the bond pads of the wafer and the terminals of the test system probe.

The Microelectronics and Computer Technology Corporation (MCC) and SEMATEC have been funded by the Advanced Research Project Agency (ARPA) to accelerate the availability and promote the quality of bare die for Multi-chip Module (MCM) applications.

The cost of KGD is still high due to the low volume demand and high NRE cost. The infrastructure for KGD is building up slowly. Die users and die suppliers should work more closely to determine what level of testing is required to guarantee good die for the intended MCM application.

New processes have been developed in MCM-D at IBM4 and materials in MCM-L such as Dupont's Thermount, Hercules Sycar, GE's Getek and Cyanate Ester substrates. There are still cost issues with MCM-D except for high volume application and technical issues with MCM-L with regard to via size/via pitch, limited I/O fan-out capability and contamination due to electrolytic Ni/Au plating. According to Jim Trent from Motorola, MCM-L substrates with wire bondable die housed in a plastic molded package provide the MCM user with the least expensive MCM substrate technology. MCM-L is being pursued as the most likely broad application candidate in the future of MCM's and is expected to be the predominant substrate in this industry for both prototype and volume product. There is also a current development of MCM-L/D substrates<sup>3</sup> based on glass reinforced polyimide multilayer printed circuit board base substrate and a copper/benzocyclobutene (BCB) deposited thin This development is aimed at producing high performance and costsensitive applications. These new developments will be followed for inclusion into the ASEM Foundry offerings when they are sufficiently mature.

### References

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- 2. M. Freda and C. Reynolds, "MCM-L Enabling Technologies ICE MM Proceedings '93.
- 3. T.G. Tessier and E.G. Myska, "High Performance MCM-L/D Substrate Approaches for Cost-Sensitive Packaging Applications. ICE MM Proceedings '93.
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# Appendix F

# **Bench Mark Data Comparisons**

for

Mentor and Cadence MCM Design Stations

### Mentor MCM Station

## **Executive Summary**

Early on in the ASEM Merchant Foundry Program, a team of two individuals (Lucius Lockwood and Mike Greene) performed bench marks of MCM design tools; Cadence Allegro MCM, Harris Finesse MCM, Intergraph MCM and Mentor MCM Station were the tools bench marked. During the bench marking, a rating table was utilized for scoring each tool's performance in various areas. The purpose of this effort was to select the best available tool(s) for Foundry MCM design applications. The bench marking efforts resulted in the Team's recommendation for purchase and implementation of Mentor MCM Station as the "golden" tool for MCM design. The purpose of this report is to provide a post bench mark experiential analysis of Mentor MCM Station's performance on a real world MCM design application.

### **General Comments**

For purposes of consistency, the same rating table (less non-applicable categories) was used to rate Mentor's performance (Refer to Table I). Cadence Allegro is GSTG's standard tool for general PWB and MCM design; Cadence's scores are shown as reference to Mentor's scores. Cadence's scores are unchanged from original bench mark rating and are representative of the bench mark effort (Version 8.x) and experience with the current of the day release 6.x.

Following are general comments about the Mentor MCM Design Experience. Refer to the following Rating Table for detailed scoring:

# Support Infrastructure

Local applications engineers were an excellent source of assistance. They were very proficient with the tools and available most of the time for support both by telephone and site visits. The hot-line returned calls sometimes same day, usually within twenty-four hours.

# Physical and Logical Symbols

Both the physical and logical symbol editing environments were very flexible. I had no difficulty in creating or modifying symbols to support the design.

# Automatic Routing

The standard Mentor router performed very poorly. Yields were very low -- in the 70 and 80 % ranges -- and this took nearly a week . Furthermore, the router ignored pre-routes either ripping them up (despite being locked) or adding routes that already existed. One especially annoying habit of the router was that it randomly ripped-up wire bond traces -- these too were locked. Mentor eventually assisted by performing the routing at their offices on their shape-based router. Even then I was forced to hand route over a hundred traces to complete the design.

# Interactive Routing/Editing

In general I was not impressed with the ease of use of the interactive routing tools. Adding routes was very difficult and the system was very sensitive to picks and guide locations. Layers that were invisible were selectable -- this was incredibly annoying -- it was very difficult in dense areas to select the desired track for editing. During interactive editing it is not practical to constantly toggle selectability -- a not visible/not selectable feature would help. Also, the system is very sensitive to guide origins, limiting the ability to easily add a connection without first adding a new guide and deleting the old one. Z-axis guides at vias, while advertised as a feature, turned out to be very annoying and hard to get rid of, even though the physical connection to the via was achieved -- again, overly sensitive to process.

# • Shape Editing

This was an excellent area of capability! All environments had the ability to create polygonal features. This was especially helpful in creating physical symbols, board geometrys, and circuit plane layers. MCMs and PWBs are often irregular in shape and the ability to support this requirement is very necessary.

# Factory/Manufacturing Interfaces

Very easy to use and reliable interfaces for setup of artwork and NC drill output. The symbol and geometry building environments of Librarian allow input of mounting holes, and special vias, etc., that directly flows through to the output. One disappoint was in getting the NC milling data generated. The board had an irregular outline with small groves extending inward at four locations and I was unsuccessful (even with AE support) to get the program to properly handle the grooves.

# Design Manager

One of the best features of MCM Station! It was a little difficult to understand all the environmental relationships at first, but afterward, it became evident that this concept is an excellent way of controlling design libraries and entire designs and projects. Designs are easily kept in synchronization and under configuration control with this tool. The logical to physical interface (both directions) was excellent.

## Layout Clean-up

There is basically no (external to the router) provision for manufacturing clean-up of the routed traces. No conductor balancing, line smoothing or jog elimination features exist -- I was required to spend considerable time in modifying the conductor patterns interactively to enhance manufacturability or eliminate potential solutions traps in the pattern.

### Summary

Overall Mentor is a very strong tool set. Mentor still rates higher than Cadence in the Rating Table. The rating and number of available features and quality of features that support MCM design still exceeds what Cadence provides. Some ratings were increased and some were decreased with respect to the actual performance versus the bench mark. Despite the problems encountered on this design I still support MCM Station as the tool of development for MCM design applications. This design was the first MCM design performed by the Foundry on the system and some allowance should be made for learning curve. I encountered many bugs in the 8.2\_5 software but there were also many features that performed very well. Performance in the areas of design management, physical to logical control/interface, schematic capture through Design Architect, factory/manufacturing interfaces, and many other areas were strong or superior as compared to other benchmarked tools. Still, router performance, interactive editing of traces, and the lack of what I consider a real MCM environment are three vital areas for improvement.

CATEGORY/FEATURE	WGT	ALLE	GRO	MEN.	TOR
(MCM SPECIFIC FEATURES)					
(Support Infrastructure)		sc	tot	sc	tot
-Local Product Support	10	6	60	10	100
-Telephone Support Hours/Day Available Total	4	2	8	8	32
-Telephone Support Hours/Day Available MST	4	2	8	8	32
-Support During Evaluation Test	10	7		9	90
-Bugfix Turnaround Time	10	5	50	8	80
-Mean Response Time for Telephone Queries	4	2		8	32
Subtotal			204		366
Maximum Score	420		204		- 555
Waxinan Good	720				
(Physical Models)		sc	tot	sc	tot
-Wirebond Element	10	5		5	
-Bondpad Element	10	ō			
-Ability to Apply BBvia in Library Model	10	3			
-Pin Mapping .	10	Ö	<del></del>		
-Ability to receive text input for pins	10	6		9	
- Data extracton from model	10	10	<del> </del>	<del>                                     </del>	70
Dara extractor from model	10	10	100		
Subtotal			240		330
. Maximum Score	600				
(Automatic Routing)		sc	tot	sc	tot
-Management and Application of MCM style vias	10	3		9	<del></del>
-Rip-up of unused via segments (during route)	10	. 0	<del></del>		
-Metallization Balancing	10	7			
-Interlocking Vias	10	9			
-Ability to control via stack by rules	10	3			
-Evaluation Results	10	3			
Subtotal			250		400
Maximum Score	600		<del> </del>	<u> </u>	ļ
(Interactive Editing)		sc	tot	sc	tot
-Wirebond Methodology	10	6		<del> </del>	
-Definition of MCM Vias	10				
-Via Containment Within a Pin	10	3			
-General Ease of Use	10	8		<del></del>	
			200		300
Subtotal	100		230		300
Maximum Score	400	<u> </u>			
(Shape Editing)		sc	tot	sc	tot
-What You See is What You Get	10	3	30	7	
-Less than 4-mil filling capability	10	0	Ö	10	
-Plane merging Capability with Cross-Hatch Matchup	10	6	60	10	100
-Plow-through Planes	4	С	0	0	
-True Smooth Taper Capability	10				(
-Taper Through Curves	10	+			(
-General ease of use and reliability	10				80
0.1.1.1			100		250
Subtotal Maximum Score		-	180		350
iviaximum score	010	<u> </u>	<u> </u>	<u> </u>	

CATEGORY/FEATURE	WGT	ALLE	GRO	MEN	TOR
(Eggton) (Manufacturing late 4				ļ	
(Factory/Manufacturing Interfaces)		sc_	tot	sc	tot
-Drill Data Supports Sequential Lamination (Cofired		<del>                                     </del>		-	
Technology)	10	3	30	10	100
-GDSII in/out to Physical Model Editor	10		<del>+</del>	<del></del>	+
-Ability to View GDSII Data	10			+	
-Ability to View Gerber Data	10	10			
, , , , , , , , , , , , , , , , , , ,	10	10	100	3	30
Subtotal			230		350
Maximum Score	340				
(Think/Thin Film Company) Net But (B. 144)					
(Thick/Thin Film Component) Not Part of Post Mortem		SC	tot	sc	tot
(General)		sc	tot	sc	tot
-Technology Files/Design Kit Support	10	10		10	100
-Minimum Dimension Granularity	10		100		100
-Submil Capability	10				100
-Metric Capability	10	10			100
-Ability to handle Mixed Units	10	10	100		
-Automatic Unit Conversion			100		100
-Documentation Within Tool Environment	10	10			100
-Push and Shove Models and Pins (to adjacent Layers)	10	6	60		100
-Ability to handle High Pin Count Devices	10	3	30		30
-Interactive DRC Violation Checking	10	3	30		100
-Batch violation checking of design	10	10	100		50
-Ability to accept violations and proceed	10	10	100		50
-Ability to Turn Off Interactive DRC entirely	10	10	100		100
Ability to Turn Off Interactive DRC entirely	10	10	100		100
-Ability to Turn Off Interactive DRC for one instance	10	10	100	10	100
Subtotal			1220		1230
Maximum Score	1400	•			
(Thermal Analysis) Not part of Post Mortem			4-4		4-4
(Monthal y that your part of 1 ost Montelli		sc	tot	sc	tot
(CFI/Inter-Tool Interfaces) Not part of Post Mortem		sc	tot	sċ	tot
(Ease of Use)					
-Time Spent in Shells/Vi Editing			tot	sc	tot 000
-True MCM Environment	10	6	60	9	90
	10	0	0	5	50
-User-programmable Stroke Recognition -On-Line Context-Sensitive Help	4	4	16	8	32
-OTF-LINE COMEXI-Sensitive Help	4	4	16	10	40
-Ease of moving from one module to the other	4	4	16	10	40
-case of moving from one module to the other	10	6	60	8	80
Subtotal			168		332
Maximum Score	348				
GENERAL FEATURES (NOT MCM SPECIFIC)					
(PHYSICAL SYMBOL GENERATION)		sc	tot	sc	tot
-Graphical data entry of physical symbol	1	1	. 1	1	1
count	<u>i</u>	1	1	i	i
	11			, , ,	

CATEGORY/FEATURE	WGT	ALLE	GRO	MEN	TOR	
-Flexibility when adding new data classes to symbols						
(fidicuals, manufacturing details, etc.)	1	1	1	1	1	1
-Format symbol generation	1	1	1	ī		1
-Ability to modify pin location and body contours	1	ī	1	1		1
-Plot output of graphical devices	1	1	1	1		
-Adjustable placement extents	1	1	]	1		1
-Command 'undo' during symbol build	1	1	1	1	<u> </u>	•
-Addition of holes on the symbol	1	1	1	1	İ	1
-Ability to add multiple height parameters to same symbol	1	1	1	1		1
-Ability to create special symbols	1	1	1	1		
Subtotal			12			12
Maximum Score	12				ļ.,	
(PADSTACK BUILDING/EDITING)		sc	tot	sc	tot	
-Assignment of hole size	1	1	1	1		1
-Pad stack assignment to the component	1	i	<del>  i</del>	i		1
-Ability to generate pad stacks with flash, antipads, null and	·	<u>'</u>	<u> </u>	<u> </u>	<b>-</b>	
isothermal pads	1	1	1	1	<u> </u>	_1
-Contour pad editor and pin assign	1	1	1	1	ļ	
-Custom build of isotherm shape	1	1	1	1 1		_
-Pad rotation	1	1	1	0	ļ	_(
				<u> </u>		
Subtotal	<u> </u>		6		ļ	
Maximum Score	6			-	ļ	
FORWARD ANNOTATION OF SCHEMATIC TO		sc	tot	sc	tot	
PWB ENVIRONMENT		-	1		1	
-Assign one schematic symbol to many physical packages				<del>                                     </del>		
or discrete values	1	1	۱ ۱	1	ł	1
-Transfer of room, ecl, electrical, and thermal properties into			<u> </u>			
		1	1	1	ł	1
	1	1	1	1	1	
the MCM system	1	1	1	1		
-Assign user power source at the schematic level and	1	1	1	]		1
the MCM system -Assign user power source at the schematic level and transfer into the MCM system		1	]	1		
-Assign user power source at the schematic level and		1	]	1 1		1
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data		1 1	]	1 1 1		1
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and	1	1	]	1 1		1
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and	1	1 1 1	]	1 1 1		1
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and	1	1 1 1	]	1 1 1		] - - - -
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation	1	1 1 1	1 1	1 1 1 1		ן ן ן
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward	1 1	1 1	1 1	1 1 1		ן ן ן
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation  -Option to change or add components during forward annotation	1 1	1 1	1 1 1	1 1 1		1
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation  -Option to change or add components during forward annotation	1 1	1 1	1 1 1	1 1 1		] ] ] ]
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation  -Option to change or add components during forward annotation  -Option to change and update signal connectivity	1 1 1	1 1 1	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1 1 1		ן ן ן
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation  -Option to change or add components during forward annotation  -Option to change and update signal connectivity environment	1 1 1 1 1	1 1 1	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1 1 1 1 1		]
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation  -Option to change or add components during forward annotation  -Option to change and update signal connectivity environment	1 1 1 1 1	1 1 1	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1 1 1 1 1		10
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation  -Option to change or add components during forward annotation  -Option to change and update signal connectivity environment	1 1 1 1 1	1 1 1	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1 1 1 1 1		]             
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation  -Option to change or add components during forward annotation  -Option to change and update signal connectivity environment  Subtotal Maximum Score	1 1 1 1 1 1	1 1 1	]   1   1   1   1   1   1   1   1   1   1	1 1 1 1 1	tot	10
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation  -Option to change or add components during forward annotation  -Option to change and update signal connectivity environment  Subtotal Maximum Score  (MCM TO SCHEMATIC INTEGRATION)  -Third party netlist input and device file support	1 1 1 1 1 1	1 1 1 1 1		1 1 1 1 1 1 1		100
the MCM system  -Assign user power source at the schematic level and transfer into the MCM system  -Synchronization manager to guide the schematic and MCM into synchronization  -Difference file creation of forward annotated data -Interface would maintain directory path for schematic and MCM directories for future transfers  -Option to remove previously existing etch during forward annotation  -Option to change or add components during forward annotation  -Option to change and update signal connectivity environment  Subtotal Maximum Score	1 1 1 1 1 1	1 1 1 1 1		1 1 1 1 1 1 1		100

CATEGORY/FEATURE	WGT	ALLE	GRO	MEN	TOR	
-Difference report between MCM and schematic						
ndependent of annotation	1	1		1 1		
			ļ. <u></u> .		<u> </u>	
Subtotal			ļ;	3		_
Maximum Score	3		-	<u> </u>		_
(BACKWARD ANNOTATION OF MCM TO			1-4		1-4	_
SCHEMATIC ENVIRONMENT)		sc	tot	sc	tot	-
-Interface between MCM and schematic is executed from			<del>                                     </del>	<u> </u>	<del> </del>	-
MCM environment	1	ן		, .	1	
-Interface would maintain directory path for schematic and	<u> </u>		<del> </del>	1	<u> </u>	-
MCM directories for future transfers	1	1		, .	ı	
-Error log file creation during back annotation and a		<u>'</u>			-	-
difference listing	1	1		, .	ı	
amoremes listing		<del>  '</del>	<del> </del>	+	<u>'</u>	_
Subtotal			<del>                                     </del>	3	+	-
Maximum Score	3	<u> </u>	<del>  '</del>	1 -	+	-
ividaii ildiri scole				+	+	-
(BOARD GEOMETRIES)		sc	tot	sc	tot	-
-Arc capability for board outline	1	1	101	1 30		-
-Arc capability for routes and package work area	1	1	ļ · · · · · ·	<u>'</u>	<del>   </del>	-
-Arc capability for plane features	<del>-</del>	<del>                                     </del>		,		_
-Add radius or chamfer to specified corners without	<u> </u>	<del> </del>	<del>                                     </del>	+	<u> </u>	-
start/stop point	1	1		1 1		
-Ability to add mounting holes at the substrate level	1	i		<u> </u>	1	-
-Three point and two point arc generation	1	i		i -	il	-
- Ability to define restrict areas	1	<del></del>	<del></del>	il i		-
-Ability to adjust substrate origin	1	1				_
					ļ	_
Subtotal				3	ļ	
Maximum Score	8		<del> </del>	<del> </del>	<del> </del>	_
(SUBSTRATE PREPARATION)		sc	tot	sc	tot	_
design		1	1.0.	1 .	1	-
-Ability to add different track and spacing rules for each	•	<u>'</u>	<del> </del>	<u>'</u>	<u> </u>	-
individual net in the design	1	1	.	1 1	ı	
tool	i	ī	<del> </del>	1		_
-Dynamic layer addition	1	1	+		ŀ	-
-Different grid setting on each layer for both tracks and vias	1	1	<u> </u>	1		-
- Produce user defined functional layer types	1	1		il		-
-Dynamic layer deletion	1	1	T	1		
-Pad stack substitution on components or on individual pins	1	1		1	ı	-
-Pad stack substitution on individual vias	1	ī		1		•
-Layer swapping	1	1		1	1	-
-Plane Swapping	1	0	) (	)		•
Subtotal			10			1
Maximum Score	11					-
(DI A CEMENT)				1	<del>  -</del>	_
(PLACEMENT)		sc	tot	SC	tot	-
-Option change physical packages with a version switch	1	1	<u> </u>	]	Ц	_
-Switch to place components by body center or pin 1	_				}	
regardless of data base coding	1	1 1	1	H	1	

CATEGORY/FEATURE	WGT	ALL	EGRO	MEN	TOR
-Rotation of components and/or mirror of components					
during interactive placement	1		1 1	1	1
-Customize placement grid by area	1		1	1	1
-Any number of placement grid positions	1		1	1	1
-Automatic placement in schematic defined rooms	1		1	i i	1
-Ratnest jog to avoid density areas	1		1	1	1
-Different autoplacement grid on top and bottom layers	1		1	1	1
-Automatic grid calculation based on components and			1	1	
board geometries	1 1		1 1	1 1	1
-User defined placement grid origin	i		1 1	1	1
-Autoplace weight definition on nets and components	1	<del>                                     </del>	11 1	1	1
-Room placement of components will be influenced by				1	1
weighted components or externally placed components	1		ı  ı	1	1
-Placement log and error files	i		1 1	1	1
-Graphically watch autoplace	1		1 1		1
-Automatic rotation of components at 0, 90, 180, 270				<u> </u>	
degree positions during autoplace	1		լ  յ	1	1
-Direction indicator from seed component (i.e. North, South,	'	1	<del>` </del>	<del>                                     </del>	<u> </u>
etc.) during autoplace	1	1	ו ון	1	1
-Placement keepout areas	Ť	<del>                                     </del>	<u> </u>	<u> </u>	1 1
-Logic length statistics placement	i	1	1 1	i	1
-Interactive autoplace features	1		1 1	1	l i
who do no displaced realistics	'	<del>                                     </del>	1	<del>'</del>	<del>                                     </del>
Subtotal			19	,	18
Maximum Score	19	<del> </del>	+	<del>                                     </del>	'
Widali Idiri occio	- ''	$\vdash$	+		
(PIN AND GATE SWAP) Not Part of Post Mortem		sc	tot	sc	tot
			<del>                                      </del>		
(BREAKOUT ADDITION)		sc	tot	sc	tot
-Snap of Ratnest to breakout pad on SMD devices	1		1	1	1
-Interactive addition of breakout segments and copy to			1		
other components	1	1	1 1	1	1
autorouter	1		1 1	1	1
-Automatic change the pin status of power pins from					
repartment change the pin status of power pins from	•	1		<u> </u>	
isothermal to full connection to plane	1		1	1	1
	1		] 1	1	1
	1		1 1	1	1
isothermal to full connection to plane	1		1 1	1	1 4
isothermal to full connection to plane Subtotal Maximum Score			1 1	1	1
isothermal to full connection to plane Subtotal		sc	1 1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	sc	1 4
isothermal to full connection to plane Subtotal Maximum Score					
isothermal to full connection to plane Subtotal Maximum Score  (PLANE ADDITION)					
isothermal to full connection to plane  Subtotal  Maximum Score  (PLANE ADDITION)  -Buried plane capability					
isothermal to full connection to plane  Subtotal  Maximum Score  (PLANE ADDITION)  -Buried plane capability  -Display isothermal connections on buried layers  -Split buried plane addition					
isothermal to full connection to plane  Subtotal  Maximum Score  (PLANE ADDITION)  -Buried plane capability  -Display isothermal connections on buried layers					
Subtotal  Subtotal  Maximum Score  (PLANE ADDITION)  -Buried plane capability  -Display isothermal connections on buried layers  -Split buried plane addition  -Automatic plane fill routine that will separate around all conductive objects on the substrate		sc	tot		
Subtotal  Maximum Score  (PLANE ADDITION)  -Buried plane capability  -Display isothermal connections on buried layers  -Split buried plane addition  -Automatic plane fill routine that will separate around all conductive objects on the substrate  -Automatic plane fill obstacle space settings	1 1	sc	tot		
Subtotal  Maximum Score  (PLANE ADDITION)  -Buried plane capability  -Display isothermal connections on buried layers -Split buried plane addition  -Automatic plane fill routine that will separate around all conductive objects on the substrate  -Automatic plane fill obstacle space settings  -Automatic artwork fill check after plane fill	1 1	sc	tot 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	sc	
Subtotal Maximum Score  (PLANE ADDITION)  -Buried plane capability -Display isothermal connections on buried layers -Split buried plane addition -Automatic plane fill routine that will separate around all conductive objects on the substrate -Automatic plane fill obstacle space settings -Automatic artwork fill check after plane fill -Creation of any angle lattice network for a plane	1 1	sc	tot	sc	
Subtotal Maximum Score  (PLANE ADDITION)  -Buried plane capability  -Display isothermal connections on buried layers -Split buried plane addition  -Automatic plane fill routine that will separate around all conductive objects on the substrate  -Automatic plane fill obstacle space settings  -Automatic artwork fill check after plane fill  -Creation of any angle lattice network for a plane  -Modification of plane shape features	1 1 1 1 1 1 1	SC	tot  1  1  1  1  1  1  1  1  1  1  1  1  1	sc	
Subtotal  Maximum Score  (PLANE ADDITION)  -Buried plane capability  -Display isothermal connections on buried layers  -Split buried plane addition  -Automatic plane fill routine that will separate around all conductive objects on the substrate  -Automatic plane fill obstacle space settings  -Automatic artwork fill check after plane fill  -Creation of any angle lattice network for a plane  -Modification of plane shape features  -Interactive addition of plane void areas	1 1 1 1 1 1 1 1 1 1 1 1	sc	tot  1  1  1  1  1  1  1  1  1  1  1  1  1	sc	
Subtotal  Maximum Score  (PLANE ADDITION)  -Buried plane capability  -Display isothermal connections on buried layers  -Split buried plane addition  -Automatic plane fill routine that will separate around all conductive objects on the substrate  -Automatic plane fill obstacle space settings  -Automatic artwork fill check after plane fill  -Creation of any angle lattice network for a plane  -Modification of plane shape features  -Interactive addition of plane void areas  -Arc resolution definition for plane contours	1 1 1 1 1 1 1	sc	tot	sc	
Subtotal  Maximum Score  (PLANE ADDITION)  -Buried plane capability  -Display isothermal connections on buried layers  -Split buried plane addition  -Automatic plane fill routine that will separate around all conductive objects on the substrate  -Automatic plane fill obstacle space settings  -Automatic artwork fill check after plane fill  -Creation of any angle lattice network for a plane  -Modification of plane shape features  -Interactive addition of plane void areas	1 1 1 1 1 1 1 1 1 1 1 1	sc	tot	sc	

CATEGORY/FEATURE	WGT ALLEG		ALLEGRO I		TOR
Maximum Score	11				
					<b>†</b>
(INTERACTIVE ROUTING)		sc	tot	sc	tot
-Highlight component nets or individual signal nets	]		+	1	+
-Auto completion of interactive digitized nets	1		1	1	1
-Arc generation for line traces	1		i	1	1
-Automatic bubble of nets around any copper feature on			<del>-</del>	<del></del>	<u> </u>
board during interactive routing to avoid spacing violations	1	1	1	1	
-Automatic slide of adjacent nets during interactive routing	•	·	<u> </u>	<u> </u>	
to avoid spacing violations	1	1	1	1	
-Area copy of substrate elements	<u></u>	1	1	<del>                                     </del>	<del>                                     </del>
-Area move, rotate, delete or mirror	1	1	1	1	<del></del>
-Addition of thru hole vias or blind and/or buried vias during	<u>.</u>	<u> </u>	<u> </u>	<del></del>	<del> </del>
interactive routing	1	1	1 1	۱ ۱	
-Layer color code bar for interactive routing	<del>'</del>	<u> </u>	<del>                                     </del>	1	<del> </del>
-Toggle width adjustment during interactive routing to any		<u> </u>	<u> </u>	<u>'</u>	<del> </del>
track width	1	1	1	1	
-Toggle adjustment of track grids during interactive routing	<u>-</u>			1	
-Selection of different via sizes during routing	1	1	1	1	
s and the size of defining rodning		<u> </u>	<del>                                     </del>	<u> </u>	
Subtotal	-	<u> </u>	12		12
Maximum Score	12	<del></del>	12		
Widainiditi ocole	12				
(AUTOMATIC ROUTING)		sc	tot	sc	tot
-Automatic strategy file generation based on MCM		30	101	<u> </u>	101
technology and user input (i.e. device size, technology, etc.)	1	. ,	١,	,	
-Different grid settings on separate routing layers	1	1	+	1	
design	1	1	1	1	<del> </del>
-Separate track width settings for each signal on the design	1	1	1	1	<del>                                     </del>
-Net property attachment	1	1	1	1	<del> </del>
-Autorouting channel precedence (high, low)	1	1		1	<del>                                     </del>
-Auto Ripup routing	<u>-</u>	<del>- '</del>	1 1	1	<u> </u>
-Auto Offgrid routing (track and via)	1	1	1	1	<del>                                     </del>
environment		1	1		
-Batch autorouting	1	<u>'</u>	<u> </u>	1	<u> </u>
-Autorouting and 0, 45 and 90 degrees		1	1	1	-
-Greater than 20 layer autorouting		1	1	1	<del> </del>
-Customization of breakout pattern for autorouter		1	1	1	
-Autorouter keepout areas	- 1		+	<u>'</u>	-
-Maximum length setting per net	1	1	1		
-Maximum via setting per net	1	1	1	<u>'</u>	-
-Content and usefulness of autorouter log file	1	1	'	1	-
-Automatic continuation of routing after defined number of	<u>-</u>		<u>'</u>		
passes, if routing is not 100% complete	,	1	١,	1	
-Autorouting in a window area	1	1	1		ļ
-Autorouting of blind and buried vias	<u>'</u>	1	ļ <u>'</u>	1	<del>                                     </del>
-Via type setting on a pass by pass basis	1	1		1	<del>                                     </del>
-Entry and exit settings for pads during autorouting		1	<del>                                     </del>	<u> </u>	<del> </del> -
-Automatic shove of tracks during autorouting		1			-
-Automatic shove of tracks during routing -Pause routing and restart					<b>_</b>
		1	<u> </u>	1	<u> </u>
-Fine grid routing capability	1	1	1		<u> </u>
-Different grid setting in the X and Y directions	]	1		1	<u> </u>
Subtotal			26		20

CATEGORY/FEATURE	WGT	ALLE	GRO	MEN	ITOR
Maximum Score					
(DESIGN RULE CHECKING)		sc	tot	sc	tot
process	1	1		1 1	
-Adjustment of violation symbol size and color or fill symbol	1	1		1 (	)
-Pick violation symbol and receive detailed description of					
violation	1	1	1	1 (	
-Violation listing of actual spacing separation	]	С	) (	) ]	
Subtotal Subtotal			<u> </u>	3	
Maximum Score	4		<u> </u>		ļ
// AVOUT OF FAMILY A	ļ			.	<u> </u>
(LAYOUT CLEANUP)		SC	tot	sc	tot
-Automatic line smoothing after autorouting	1	1			) (
-Automatic renumbering of device designators by row and			1		
column	1	1	ļ	]	
-Suffix addition to renumbered device designators		_			
encompassed between grid lines	1			<u> </u>	1
-Replace unused pads with null shapes on internal layers	1	1		1 1	
-Clean-up 45 degree bends to 90 degree	1	1		1 1	<u> </u>
degree angles on round, square, rectangular, and oblong	_	_			
pads Fillet to a limetic paradic pad and a limetic pad a l	1	]		1 0	) (
-Fillet tee junctions and pad entry	1	1		]	<u> </u>
-Automatic via eliminate	1	1		] ]	+
-Remove unused breakout segment	1			] ]	<del></del>
-Detailed clean-up log file creation	1	!	ļ		) (
Cultababal			1		<b>.</b>
Subtotal Maximum Score	10		10	<del>'</del>	<del>  '</del>
ividximum score	10			-	<del> </del>
(MISCELLANEOUS FEATURES)	<u> </u>	sc	tot	sc	tot
-Multiple color definition	1	1	101	1 1	101
-Setting color priority for color overlay	<del>- </del>	1	<del>                                     </del>	1	
-Load plot files to verify accuracy	<u> </u>	1	<del>                                     </del>	1 1	
-Command undo for substrate layout	1	1	<del>                                     </del>	1	
	1	<del></del> ;	<del> </del>	1	<u> </u>
process	1				
process	1		<del> </del>		
process -Automatic generation of list files to effectively perform	1	1			
process  -Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etc.	1	1			
process  -Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data		1		1 1	
process  -Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability	1	1			
process  -Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads	1	1			
process  -Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability	1	1			
-Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads -Multiple via shape capability	1	1			10
process  -Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads	1	1			10
process -Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads -Multiple via shape capability  Subtotal	1 1	1			10
-Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads -Multiple via shape capability  Subtotal Maximum Score	1 1	1		1 1 1	10
-Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads -Multiple via shape capability  Subtotal Maximum Score  (SILKSCREEN AND TESTPAD GENERATION)	1 1	1			10
-Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads -Multiple via shape capability  Subtotal Maximum Score  (SILKSCREEN AND TESTPAD GENERATION) -Automatic silkscreen generation with auto clearance from	1 1	1 1 1	10		
-Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads -Multiple via shape capability  Subtotal Maximum Score  (SILKSCREEN AND TESTPAD GENERATION) -Automatic silkscreen generation with auto clearance from holes and data editing	1 1	1 1 1	10		
-Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads -Multiple via shape capability  Subtotal Maximum Score  (SILKSCREEN AND TESTPAD GENERATION) -Automatic silkscreen generation with auto clearance from holes and data editing	10	1 1 1 1 sc	10		
-Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads -Multiple via shape capability  Subtotal Maximum Score  (SILKSCREEN AND TESTPAD GENERATION) -Automatic silkscreen generation with auto clearance from	10	1 1 1 1 sc	10		
-Automatic generation of list files to effectively perform unique autoplace, autoroute, analysis, etcAccuracy of displayed data -Vision target capability -Addition of miscellaneous pads -Multiple via shape capability  Subtotal Maximum Score  (SILKSCREEN AND TESTPAD GENERATION) -Automatic silkscreen generation with auto clearance from holes and data editing -Automatic text placement during silkscreen generation	10	1 1 1 1 sc	tot		tot

CATEGORY/FEATURE	WGT	ALLEGRO		ST ALLEGRO ME		MEN	NTOR	
-Log file for testpad generation	1	-	1	1				
-Multiple physical testpad sizes	<del>                                     </del>	<del> </del>	1	1	† -			
-Batch testpad generation	<del>                                     </del>		1	1				
-Test Pad X-Y Location File Generated		-	1					
-Test Pad Size Data and Net Information Generated	- ;	- '		+	<del> </del>			
-Physical test pads added automatically and option to not			<u> </u>		-			
probe under devices	١,	١,	Ι,	J ,	١,			
-Isocontour density display of probe points	1 1		!	<u> </u>				
-Filter for board elements				ļ				
-Silkscreen and testpad edit	1	-		<del>  ,</del>				
onworker and resipad edit	<del>                                     </del>	1	1	1	<u> </u>			
0.164-4-1			1	<b>ļ</b>	ļ			
Subtotal			13	<del> </del>	11			
Maximum Score	13	<del>                                     </del>	ļ					
(ARTWORK GENERATION)		sc	tot	sc	tot			
-Aperture editor	1	1	1	1	1			
-Automatic aperture generator	1	1	1	1	i			
-Graphically display any design data and produce a Gerber	· · · · · ·	<u> </u>	<u> </u>	İ	<u> </u>			
file for that data	1	1	1	1	l 1			
-Identify the Gerber layer with a user defined name	i	1	1	1				
-Define multiple Gerber wheels via an editor	i	i	<del>                                     </del>	Hi	<del>'</del>			
-Define each Gerber layer as a negative or positive, format			<u> </u>	<del>                                     </del>	<del>'</del>			
type, XY origin, area, rotation, mirror, and removal of G		i	İ					
codes within PWB environment	1	,	1	١,	١,			
-Metric or English aperture units and coordinates		1	+	<del> </del>	<u> </u>			
-Batch generation of Gerber files	1	1	<del> </del>	<del>                                     </del>	<del>                                     </del>			
-Aperture rotation listed in Gerber File	1	<del>                                     </del>	<del>                                     </del>	1				
-Photoplot log file	1	1	<del>                                     </del>	1	1			
-Error checking of problem fill areas	1	1	1	1	1			
etc.)	1	1	<del>                                     </del>	<del>                                     </del>	<del> </del>			
-Load multiple design data layers into one session	<u>'</u>	1	+ +	-	0			
-Graphically step and repeat Gerber data	1	1	1	1	1			
-Add manufacturing elements to the stepped and			1	'	· · · · · ·			
repeated Gerber file	,	1	,	1	١,			
- Production in the second sec		1	-	1	·			
Subtotal			15		13			
Maximum Score	15		13		13			
MidAiridiri Score	13		<del> </del>					
(DRILL/ROUTE DATA)		sc	tot	sc	tot			
-Automatic generation of stepped and repeated drill and			101	30	101			
route data	1	1	1 ,	1	1			
-Define drill format in the pcb editor	1	i	<del>                                     </del>	1	1			
-English or metric drill output	1	<u>;</u>	1	1	1			
-Customize drill/route data		<u>'</u>	1	1	<u>'</u>			
-Offset drill/route starting point from board origin	<u>_</u>		<del>                                     </del>	1	<u>'</u>			
-Generate drill tapes based on graphical displayed holes	1	1	1	<del>                                     </del>	1			
-Create drill tapes for blind, buried, and thru hole vias	1	1						
-Drill/route error log generation	1			1				
overlay	1	1			<del></del>			
position	1				0			
- Control 1		1						
Subtotal			10		8			
Maximum Score	10							

CATEGORY/FEATURE	WGT	ALLEGRO		MEN	OR
(SYSTEM INTERFACES) Not Part of Post Mortem		sc	tot	sc	tot
(PLOTTER OUTPUT) Not Part of Post Mortem		sc	tot	sc	tot
			1		
(USER FRIENDLINESS)		sc	tot	sc	tot
-Ability to display system information without leaving MCM					
session	1	1	ן ן	1	1
-File manager to control all files and external processes	1	0	0	1	1
-Query facility to view directory files and pick files for input					
into the MCM environment	1	1	1	1	1 1
-Peripheral manager to define peripheral equipment such					
as printers and plotters	1	1	1	Ιo	Ιo
-Load local or directory environment files	1	1	1	1	
-Modification of environment variables within the MCM			·	<u> </u>	
environment and reexecution	1	1	1	1	1 1
-Define and move any window in the display environment	1		i	i	l i
-Optional use of the display screen	1	i	<b></b>	l i	
-Font size adjustment of graphics	1		i	l i	
-Automatic window manager	1	<del> </del>	1	l i	
-User interface: mouse	1	1	i	1	
-User interface: function keys	<u>-</u>	1	1	Hi	<del></del>
-User interface: menus	1	1	<del> </del>	1	
-Perform find on next element when in auto applications	1	<del>                                     </del>	<u> </u>	<del>                                     </del>	Ö
-Redisplay using world window	1	l i	i	1	
-Playback capability with script files	1	1	1	<del>                                     </del>	
-MCM diagnostic tools for checking, fixing, and	,	<u> </u>	<del>  '</del>	<u> </u>	<u>'</u>
compressing database files	1	1	۱ ۱		0
-Archiving procedures/methods	1	i	<u> </u>	1	
-Operational within 16M memory	1		1	0	
-Response time statistics and performance data reports	1	1	1	1	
-Warning and error messages	1	<del>                                     </del>	1	1	
-User definable library search paths	1	1		1	
see desiriable ibidity sedicti patris	<u> </u>	<del> </del>	<del>- '</del>	<del>                                     </del>	<del>                                     </del>
Subtotal			21		18
Maximum Score	22				
Maximum Score Total	4933		2927		3849
Score Total					
			1		